

$$R = \rho \cdot \frac{l}{A}$$

R → direnç (Ω)
 ρ → öz direnç ($\Omega \cdot \text{cm}$)
 l → uzunluk (cm)
 A → alan (cm^2)



$$\rho_{\text{bakır}} \approx 10^{-6} \Omega \cdot \text{cm} \text{ (iletken)}$$

$$\rho_{\text{germanyum}} \approx 50 \Omega \cdot \text{cm} \text{ (Yarıiletken)}$$

$$\rho_{\text{mika}} \approx 10^{12} \Omega \cdot \text{cm} \text{ (Yalıtkan)}$$

$$\rho_{\text{silisyum}} \approx 50 \cdot 10^3 \Omega \cdot \text{cm} \text{ (Yarıiletken)}$$

Atom → Elektronlar (- yüklü)
 → Çekirdek → Protonlar (+ yüklü)
 → Nötronlar (yüksüz)

Proton sayısı atom numarasını verir.
 Proton ve nötron sayıları toplamı kütle numarasını verir.

Elektronlar çekirdek etrafındaki yörüngelerde dolanırlar. Atomun elektronlarının bulunduğu en dış yörüngesine valans yörünge, bu yörüngede bulunan elektronlara da valans elektronlar denir. Valans elektronlar atomun elektriksel davranışında önem taşırlar.

Valans yörüngesindeki elektron sayısı 4'ten az olan basit maddelere iletken denir. Bütün metaller iletkendir ve elektrik akımını iletirler. İletkenlerin son yörüngesinde bulunan valans elektronlar yörüngelerinden çok kolay bir şekilde ayrılabilirler. Valans elektron sayısı ne kadar az ise iletkenlik o kadar fazladır.

Valans elektron sayısı 4'ten fazla olan basit maddelere yalıtkan denir. Yalıtkanlar, elektrik akımına karşı büyük direnç gösterirler. Cam, Porselen, Plastik, Kaucuk vb. maddeler yalıtkanlardır.

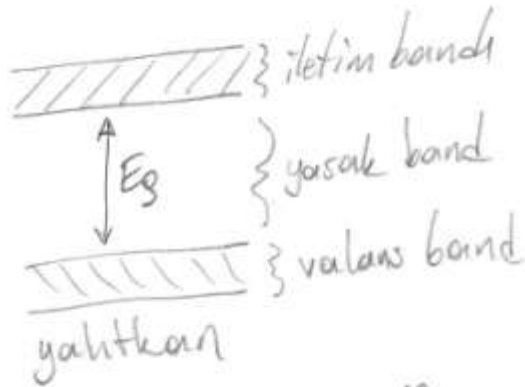
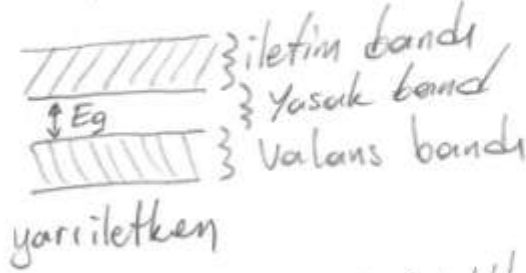
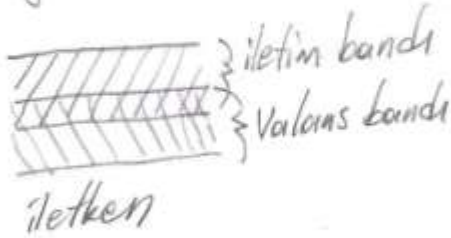
Son yörüngesinde 4 elektron bulunan basit maddelere yarıiletken denir. En çok kullanılanlar: Silisyum, Germanyum, Selenyum, Sülfür, Bakır oksit, Ginko oksit, Kurşun Sülfür, Kadmium sülfürdür.

• 7 7 7 Alüminyum iletkenidir.
13 elektron

• 7 7 18 7 Bakır iletkenidir.
29 elektron

202 formülü

Bir maddeyi iletken hale getirmek için dışarıdan bir enerji uygulanması gerekir. Bu enerji 3 ayrı enerji bandının oluşmasını sağlar. iletim bandı, Yasak band, Valans bandı



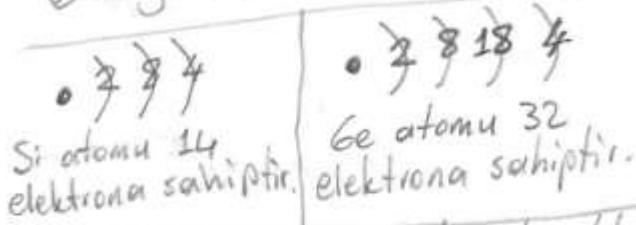
$$E_g > 5 \text{ eV (Yalıtkan)}$$

$$E_g = 1.1 \text{ eV (Si)}$$

$$E_g = 0.67 \text{ eV (Ge)}$$

$$W = QV = \underbrace{(1.6 \times 10^{-19} \text{ C})}_{\substack{\text{1 elektron} \\ \text{yükü}}} \times \underbrace{(1 \text{ V})}_{\substack{\text{1 Volt}}} = 1 \text{ eV} = 1.6 \times 10^{-19} \text{ J}$$

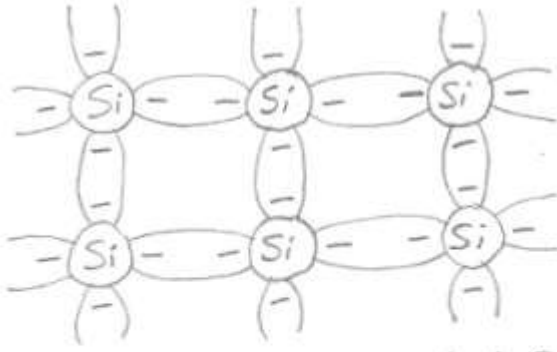
Elektronlar, çekirdekten ne kadar uzak ise, enerji durumları da o derece yüksektir. Ana atomdan ayrılmış bir elektron atomik yapıdaki herhangi bir elektrondan daha yüksek bir enerji durumuna sahiptir.



Si ve Ge atomları dış yörüngelerinde 4 valans elektrona sahip olduklarından yarıiletkenlerdir.

Yarıiletken malzemelerin karakteristikleri, nispeten saf yarıiletken matzeme bazı katkı atomları ilave edilerek önemli ölçüde değiştirilebilir.

Si ve Ge, 10 milyarda 1 gibi, çok yüksek bir saflık düzeyinde üretilebilmektedir. Si ve Ge maddesine milyonda 1 gibi bir katkı ilavesi, onları nispeten iyi bir iletkeneye dönüştürmektedir.



Dış yörüngedeki valans elektronların paylaşımıyla oluşan bağlar kovalent bağ denir.

Dış yörünge 8'e tamamlanmış olur.

Her ne kadar Kovalent Bağ, valans elektronlarıyla ana atomlar arasında daha sağlam bir bağlaşımına sebep olsa da, valans elektronların doğal sebeplerle yeteri kadar kinetik enerji alıp kovalent bağdan koparak serbest hale geçmesi mümkündür.

Oda sıcaklığında, 1 cm^3 öz Si maddesinde yaklaşık 1.5×10^{10} , öz Ge maddesinde ise 2.5×10^{13} serbest taşıyıcı vardır. Öz maddeler, katkılarını çok düşük bir düzeye düşürmek amacıyla modern teknoloji ile mümkün olan en yüksek saflıkta rafine edilmiş yarıiletkenlerdir.

Katkılı Malzeme: Yarıiletken maddeye dışarıdan yabancı bir madde katılırsa iletkenliği katılan maddenin özelliğine göre oldukça değişir. Yarıiletken kristalin her 16 gramına, 1 gramın milyonda biri kadar yabancı madde atomu katılmalıdır.

N tipi malzeme

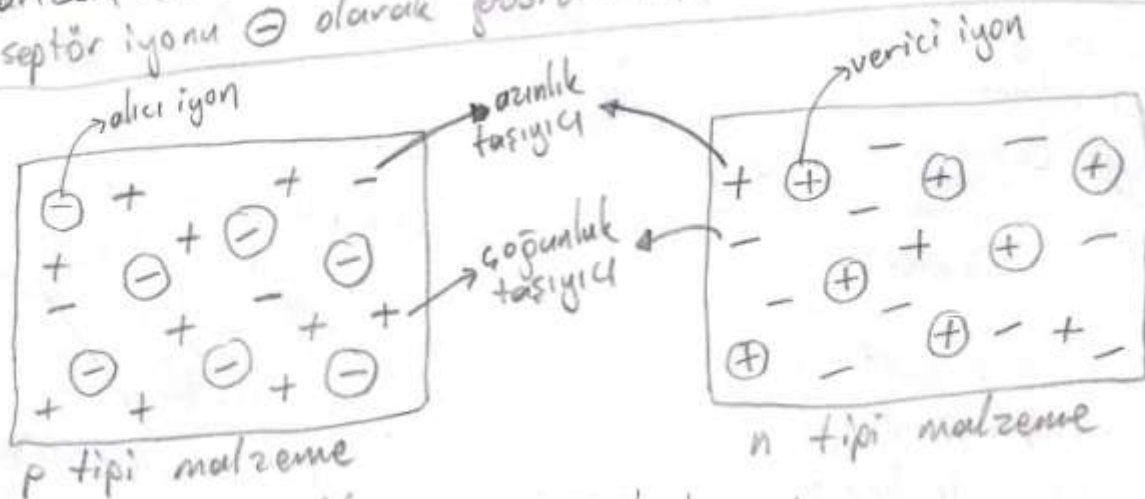
Si ve Ge gibi bir yarıiletken malzemeye 5 valans elektronlu yabancı atomlar eklenmesiyle elde edilir. 4 valans elektron kovalent bağa katılır. 5. elektron serbest haldedir. Bu elektronun atomdan ayrılması kolay olduğundan akım taşıyıcı olarak kullanılır. Bu elektronu koparmak için 0.01 eV enerji yeterlidir. Oda sıcaklığında, bir öz Si malzemede her 10^{12} atoma yaklaşık 1 serbest elektron düşer. Katkı düzeyi 10 milyonda bir olursa $\frac{10^{12}}{10^7} = 10^5$, yani taşıyıcı yoğunluğu 100.000 kez artar. Aynı sıcaklıkta, öz Ge malzemede her 10^9 atoma yaklaşık 1 serbest elektron düşer. Taşıyıcı yoğunluğu ne kadar fazla ise iletkenlik o derece iyidir.

P tipi malzeme

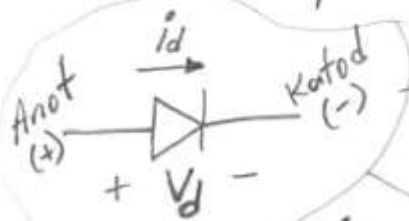
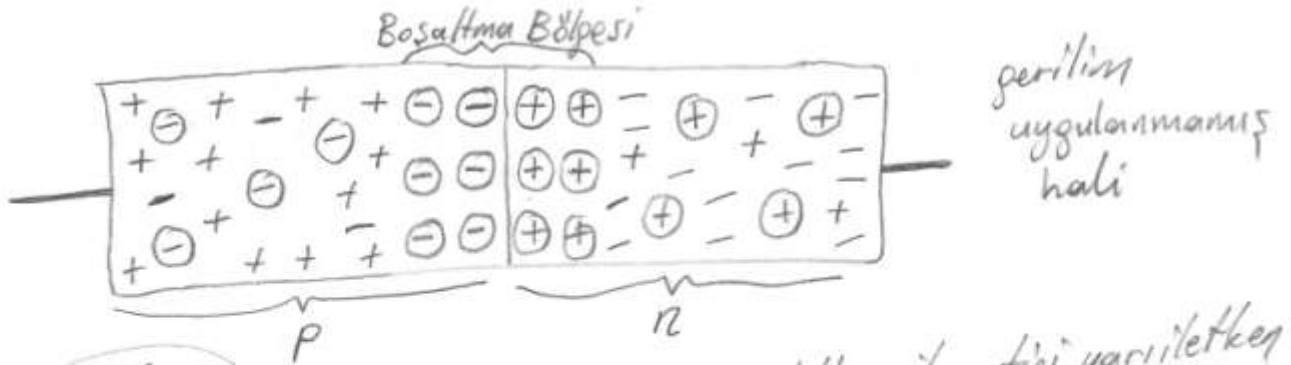
Si ve Ge gibi bir yarıiletken malzemeye 3 valans elektronlu yabancı atomlar eklenmesiyle elde edilir. 3 valans elektronu kovalent bağa katılır. Ancak, yarıiletkenin bir valans elektronu yabancı madde atomu içinde bağ yapacak elektron bulamaz. Burada oyuk meydana gelir. Küçük bir enerji ile bu oyuk, komşu atomdan bir valans elektronu ile doldurulur. Böylece, geride elektron veren atomda bir oyuk meydana gelir. Oyuklar akım taşıyıcı olarak kullanılır. n tipi malzemede elektronlar akım taşıyıcı idi. p tipi malzemeye gerilim uygulanırsa, oyuklar akım geçişini sağlar. Oyuklar serbest elektron gibi elektrik akımını taşıyarak iş görmüş olur. Oyukların hareketi elektronların hareketine zıt yöndedir. Akım taşıma işi pozitif yüklü oyuklar tarafından yapıldığından bu tip yarıiletkenlere p tipi yarıiletkenler denir.

Malzemedeki toplam proton sayısı, toplam elektron sayısına eşit olduğundan n tipi malzeme ve p tipi malzeme elektriksel olarak nötrdür.

Bir donör atomunun 5. elektronu ana atomdan ayrıldığında, geriye kalan atomun net bir pozitif yükü olur. Bundan dolayı donör iyonu \oplus olarak gösterilir. Ekseptör atomunun da bir elektronu eksik olduğundan dışarıdan bir elektron alınca atom negatif yüklü olur. Bundan dolayı ekseptör iyonu \ominus olarak gösterilir.



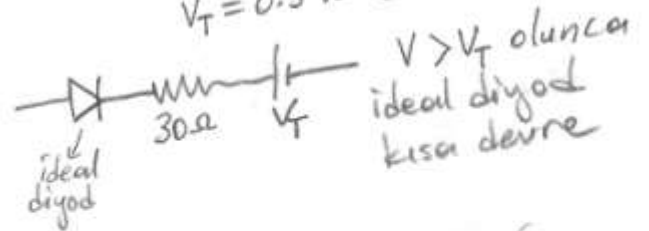
- : Serbest elektron + : serbest oyuk



→ Diyod: p tipi yarıiletken ile n tipi yarıiletken birleştirilerek elde edilir.

ileri öngerilimleme

Boşaltılmış bölge küçük.
akıma karşı küçük direnç.
 $V_T = 0.7 \text{ Volt (Si)}$
 $V_T = 0.3 \text{ Volt (Ge)}$



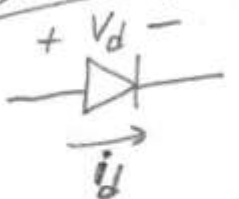
Tersine öngerilimleme



Boşaltılmış bölge genişler. Akıma karşı yüksek direnç.
 $E < V_Z$ için $I = I_S$: Ters doyma akımı
 $I_S \approx 0$ olduğundan kapalı devre
Diyod bu bölgede kullanılmaz.

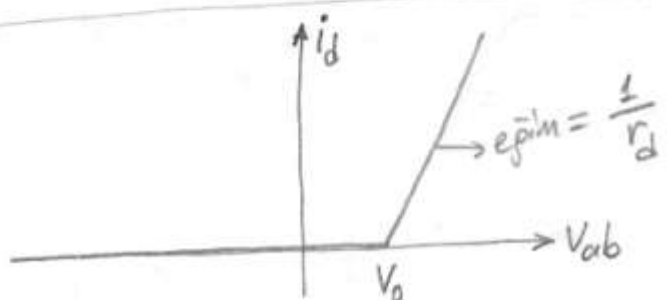
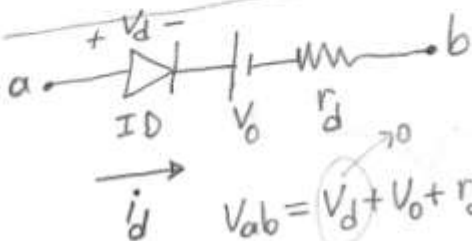
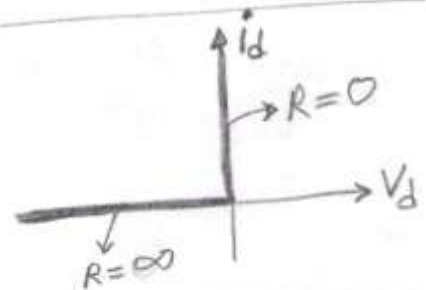
$V_Z = 40 \text{ Volt (Si)}$

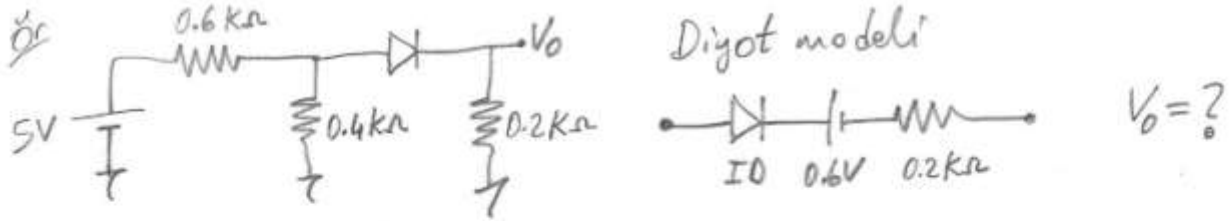
ideal Diyot



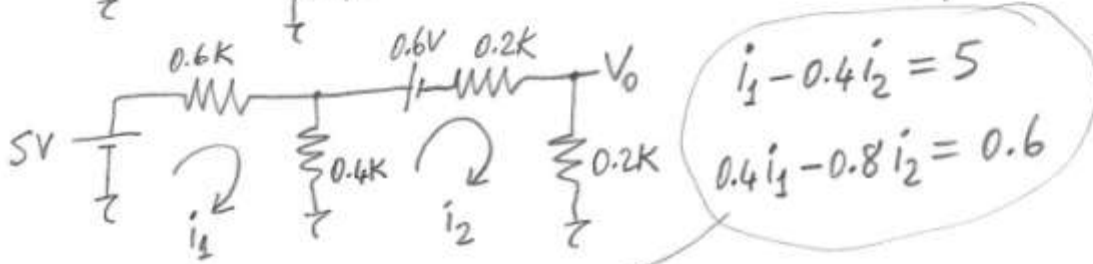
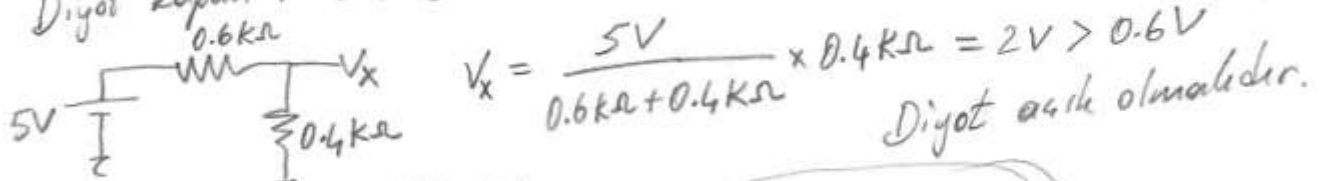
$V_D \geq 0$ için kısa devre

$V_D < 0$ için açık devre





Diğer kapalı kabul edilirse



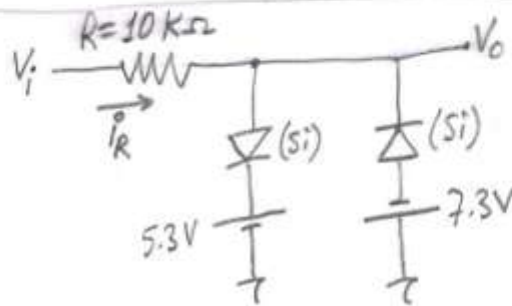
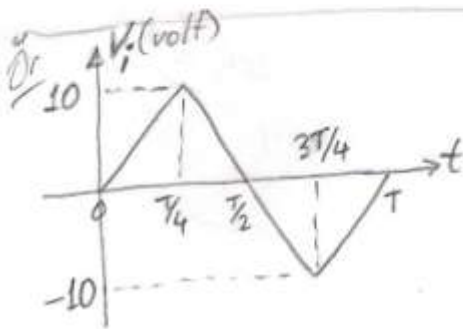
5 ile çarp

$$5i_1 - 2i_2 = 25 \rightarrow i_1 = \frac{25 + 2i_2}{5}$$

$$2i_1 - 4i_2 = 3$$

$$2 \frac{25 + 2i_2}{5} - 4i_2 = 3$$

$$i_2 = \frac{35}{16} \text{ mA}, V_O = 0.2i_2 = \frac{7}{16} \text{ Volt}$$



$\text{Diğer} \equiv \text{Diğer} \text{ } I_D 0.7V$

i_R akımının grafiğini çiziniz.

$$5.3V + 0.7V = 6V$$

$$7.3V + 0.7V = 8V$$

$V_O > 6V$ için 1. diğot açık.

$V_O < -8V$ için 2. diğot açık.

$$i_R = \frac{V_i - V_O}{R} = \frac{V_i - V_O}{10K}$$

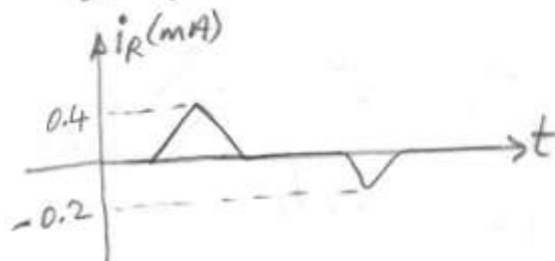
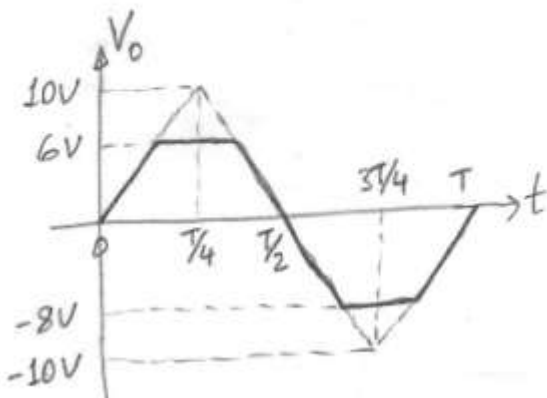
$$-8V < V_O < 6V \rightarrow i_R = 0$$

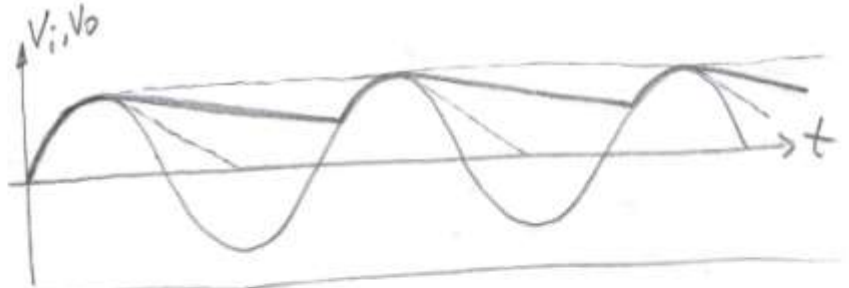
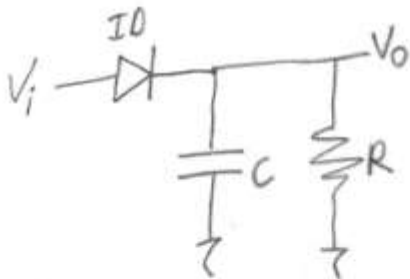
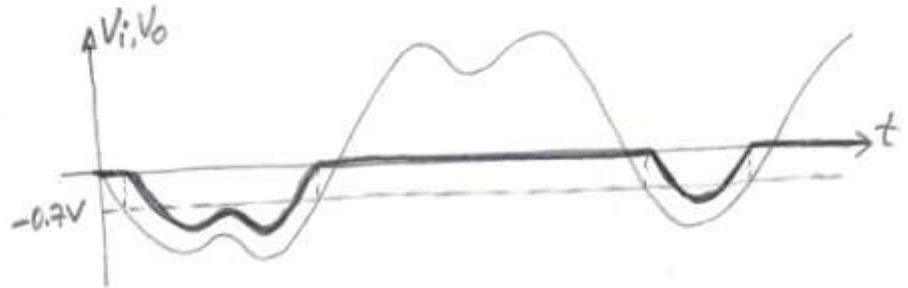
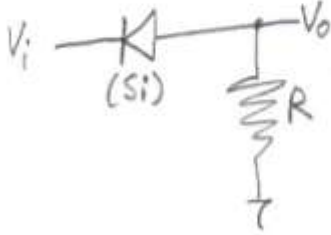
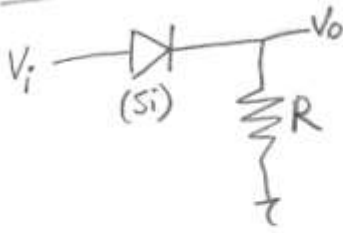
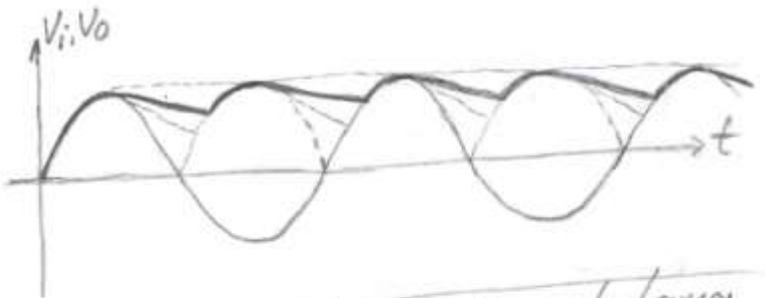
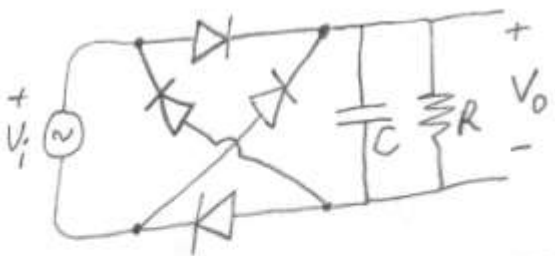
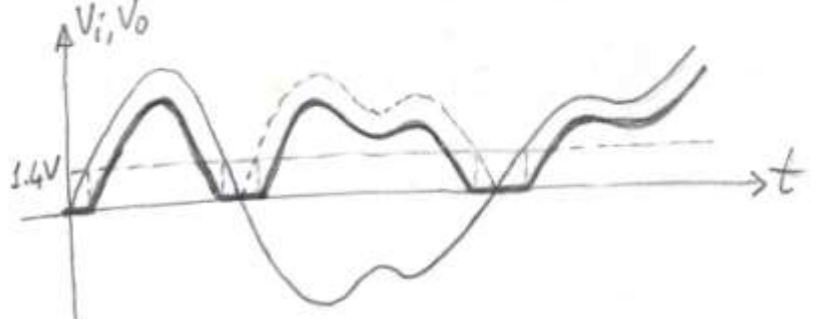
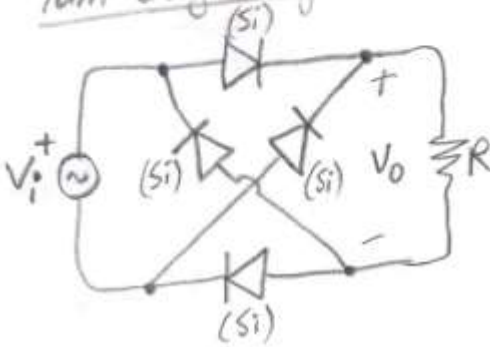
$$V_O = 10V \text{ için}$$

$$i_R = \frac{10 - 6}{10} = 0.4 \text{ mA}$$

$$V_O = -10V \text{ için}$$

$$i_R = \frac{-10 + 8}{10} = -0.2 \text{ mA}$$

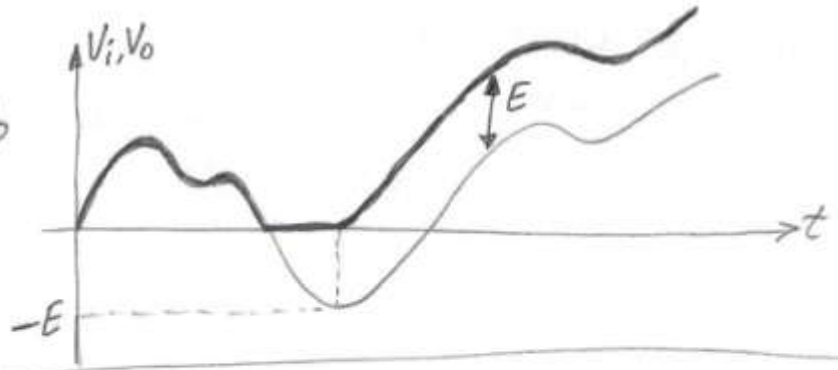
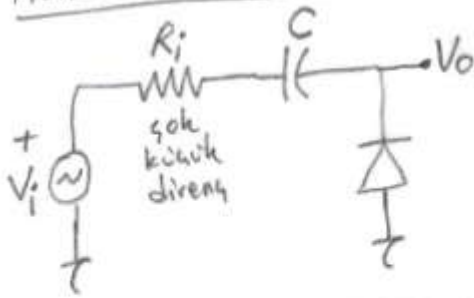
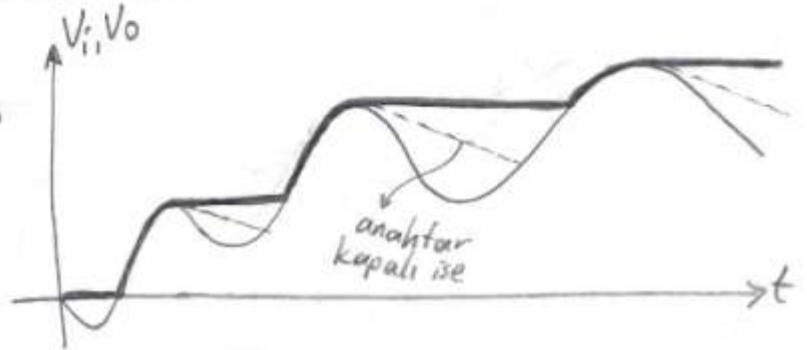
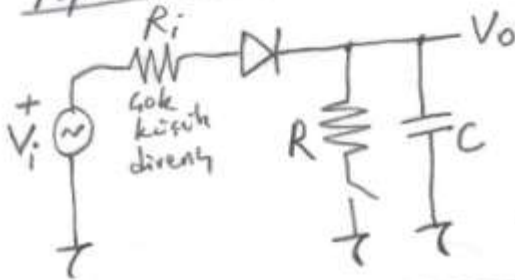
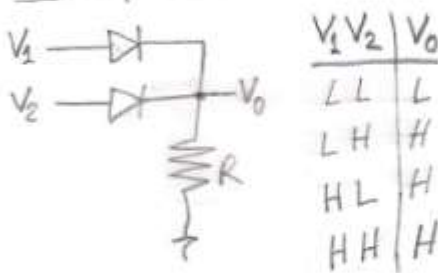


Yarım Dalga DoğrultucuTam Dalga Doğrultucu

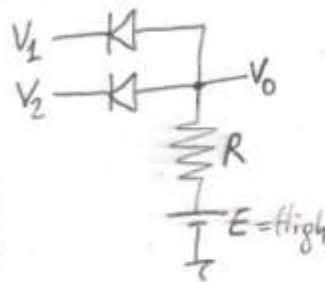
$V_i(t) = V_m \sin \omega t$, $\omega = 2\pi/T$ olsun. Kapasitör yok ise ortalama dc voltaj.

Yarım Dalga Doğrultucusu için $V_{dc} \approx 0.318 (V_m - V_T)$
 $V_T \ll V_m$ ise $V_{dc} \approx 0.318 \cdot V_m$

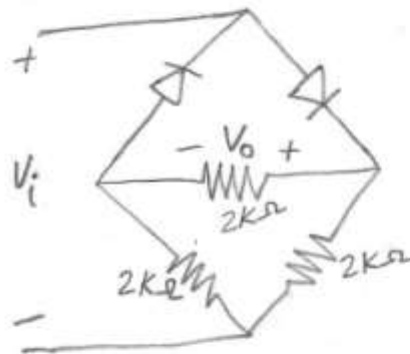
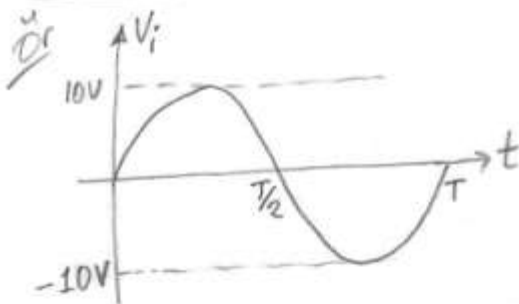
Tam Dalga Doğrultucusu için $V_{dc} \approx 0.636 (V_m - 2V_T)$
 $2V_T \ll V_m$ ise $V_{dc} \approx 0.636 \cdot V_m$

Kenetlenme DevresiTepe DetektörüPozitif Mantık Veya Kapısı

V_1	V_2	V_o
L	L	L
L	H	H
H	L	H
H	H	H

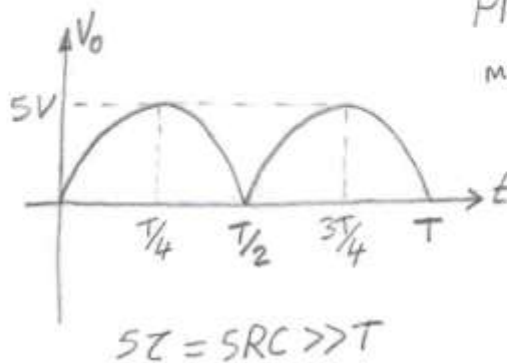
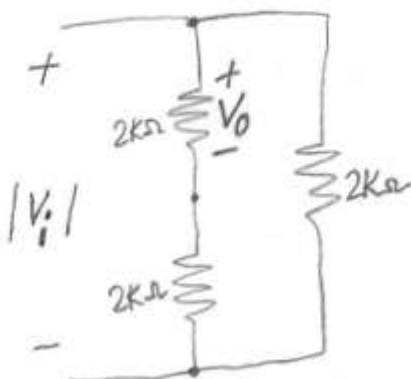
Pozitif Mantık Ve Kapısı

V_1	V_2	V_o
L	L	L
L	H	L
H	L	L
H	H	H



V_o çıkış dalgasını
giziniz.

PIV ve DC düzeyini
hesaplayınız.

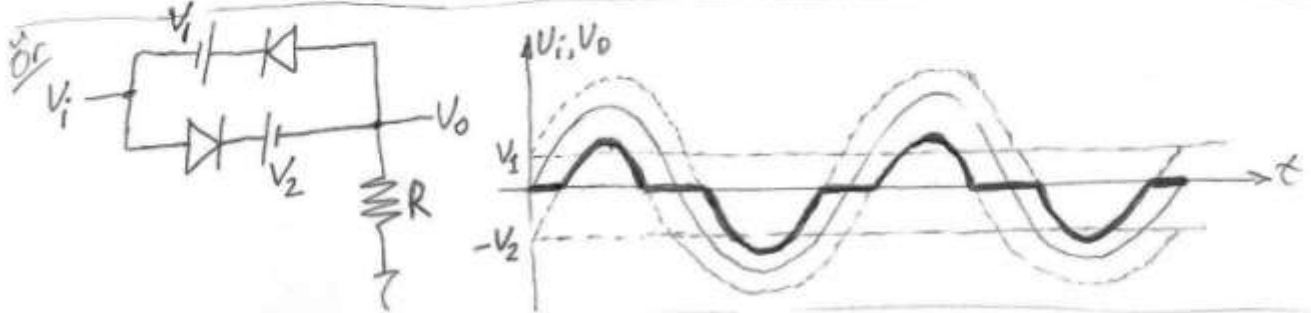
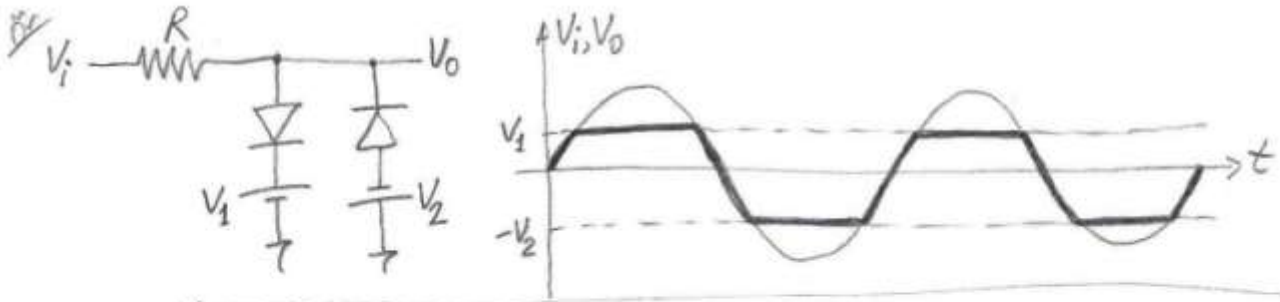


PIV, R üzerindeki
maksimum gerilime eşittir
 $PIV = 5 \text{ Volt}$

$$V_{dc} = 0.636 \times 5V$$

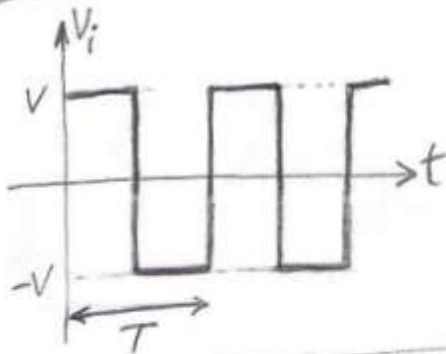
$$= 3.18 V$$

$$5T = 5RC \gg T$$



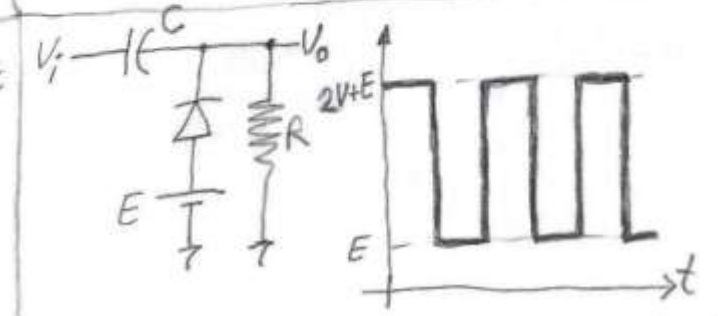
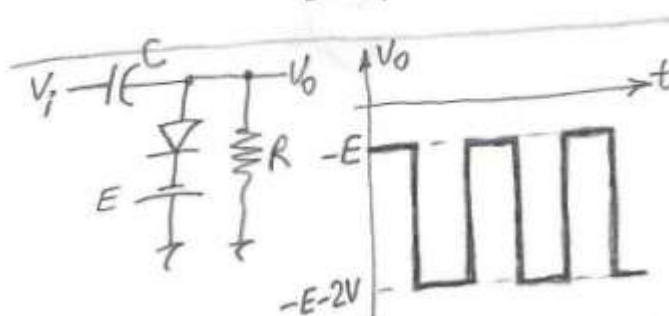
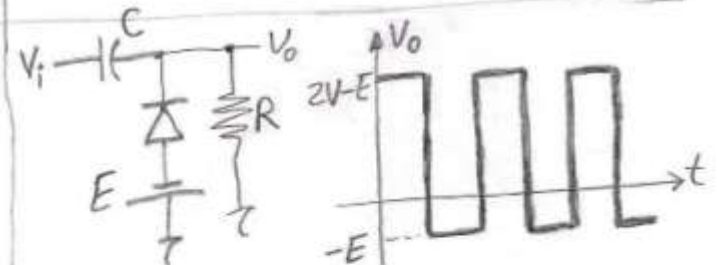
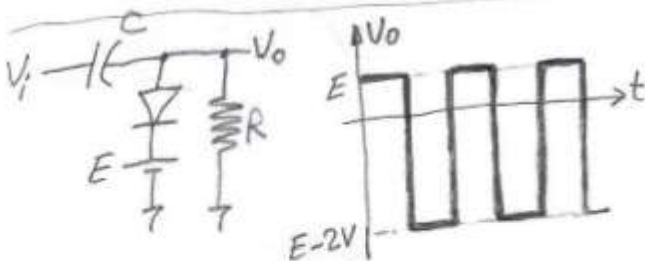
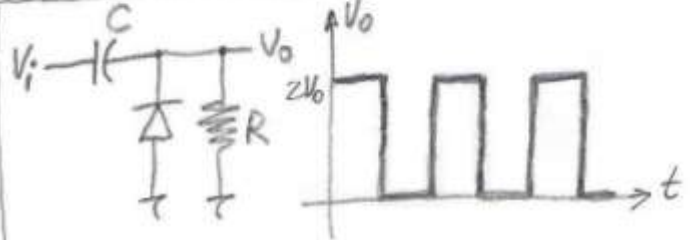
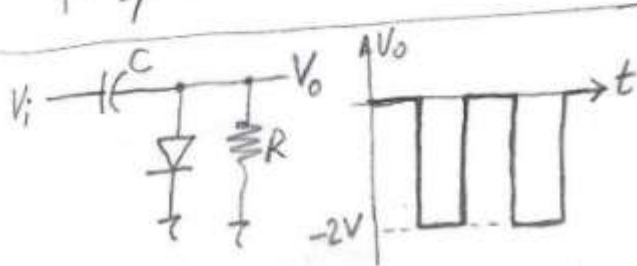
Kenetlenme Devreleri

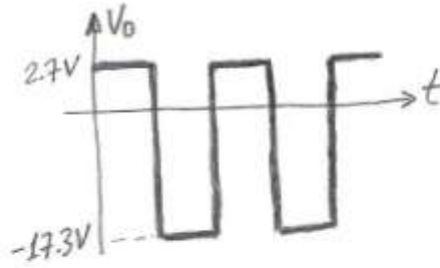
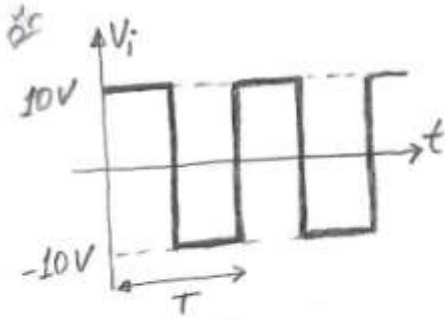
f : frekans (Hz) $T = \frac{1}{f}$: periyot (s)



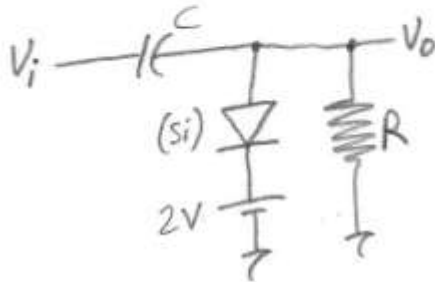
$\tau = RC \rightarrow 5\tau$ (Kapasitörün direnç üzerinden dolması ve boşalması için gerekli süre)

$T \ll 5\tau$ ise kapasitörün dolması ve boşalması için süre çok az.



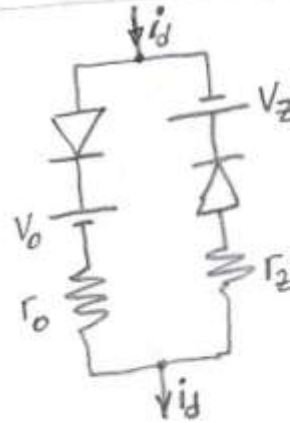
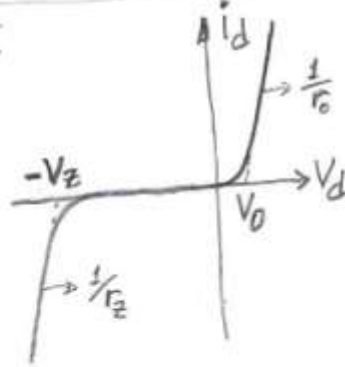
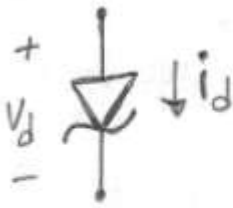


Si Diyot kullanarak devreyi tasarla.
 $5\tau = 5RC \gg T$

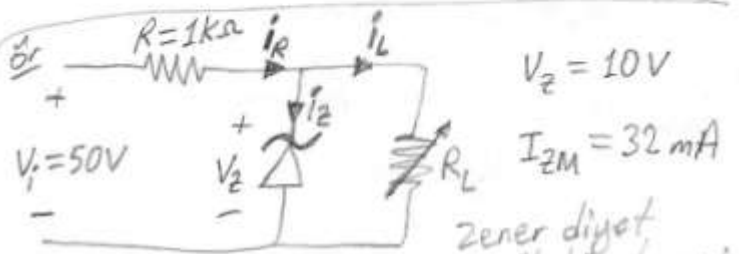
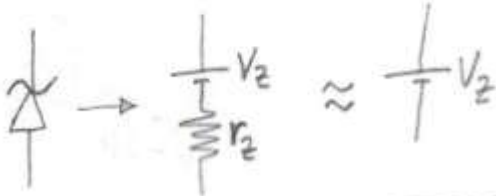


$V_i = 10V$ için diyot açık.
 $V_o = 2V + 0.7V = 2.7V$ $V_C = V_i - V_o = 7.3V$
 $V_i = -10V$ için diyot kapalı.
 $V_o = V_i - V_C = -10V - 7.3V = -17.3V$

Zener Diyot



Zener diyot zener bölgesinde tam anlamıyla faydalanmak için kullanılır.



Zener diyot reglör devresi

a) R_L ve i_L aralığını bulunuz.

b) Zener diyotun harcanan maksimum gücü bulunuz

$i_Z = 0$ için R_L minimum olur.

$$i_R = i_L \rightarrow \frac{V_i - V_z}{R} = \frac{V_z}{R_{Lmin}} \rightarrow R_{Lmin} = \frac{RV_z}{V_i - V_z} = \frac{(1k\Omega) \cdot (10V)}{50V - 10V} = 0.25 K\Omega$$

$$i_{Lmax} = \frac{V_L}{R_{Lmin}} = \frac{V_z}{R_{Lmin}} = \frac{10V}{0.25k\Omega} = 40mA = i_R$$

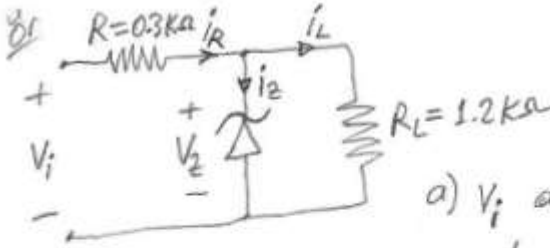
$$i_{Lmin} = i_R - i_{ZM} = 40mA - 32mA = 8mA$$

$$8mA \leq i_L \leq 40mA$$

$$R_{Lmax} = \frac{V_L}{i_{Lmin}} = \frac{V_z}{i_{Lmin}} = \frac{10V}{8mA} = 1.25 K\Omega$$

$$0.25 K\Omega \leq R_L \leq 1.25 K\Omega$$

$$P_{max} = V_z \cdot I_{ZM} = (10V) \cdot (32mA) = 320 mW$$



$$V_Z = 20V \quad I_{ZM} = 60mA$$

Zener diyot
regülâtör devresi

a) V_i aralığını bulunuz. b) Zener diyotta harcanan maksimum güç.

$I_Z = 0$ için V_i minimum olur.

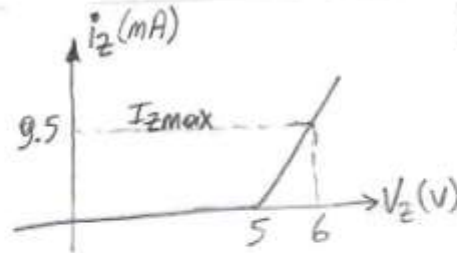
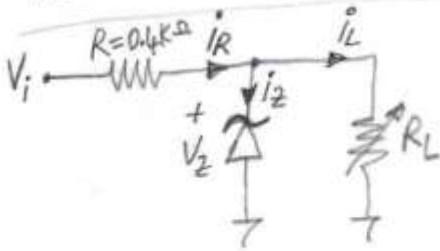
$$I_R = I_L \rightarrow \frac{V_{imin} - V_Z}{R} = \frac{V_Z}{R_L} \rightarrow V_{imin} = \frac{R + R_L}{R_L} V_Z = \frac{0.3k\Omega + 1.2k\Omega}{1.2k\Omega} \times 20V = 25V$$

$$I_L = \frac{V_L}{R_L} = \frac{V_Z}{R_L} = \frac{20V}{1.2k\Omega} = \frac{50}{3}mA = 16\frac{2}{3}mA$$

$$I_{Rmax} = I_{ZM} + I_L = 60mA + 16\frac{2}{3}mA = 76\frac{2}{3}mA$$

$$V_{imax} = R I_{Rmax} + V_Z = (0.3k\Omega) \times (76\frac{2}{3}mA) + 20V = 46V$$

$$P_{max} = V_Z I_{ZM} = (20V) \cdot (60mA) = 1200mW = 1.2W$$



$V_i(t) = 8 + 2\cos\omega t$ için
 R_L direncinin ve I_L akımı
nın sınır değerlerini
bulunuz.
Zener kırılma bölgesinde
çalışıyor.

$$V_i(t) = 8 + 2\cos\omega t \text{ için } V_{imin} = 6V, V_{imax} = 10V$$

V_{imin} ve $I_Z = 0$ için R_L minimum olur.

$$I_R = I_L \rightarrow \frac{V_{imin} - V_{Zmin}}{R} = \frac{V_{Zmin}}{R_{Lmin}} \rightarrow R_{Lmin} = \frac{R V_{Zmin}}{V_{imin} - V_{Zmin}} = \frac{(0.4k\Omega) \times (5V)}{6V - 5V} = 2k\Omega$$

$$I_{Lmax} = \frac{V_{Zmin}}{R_{Lmin}} = \frac{5V}{2k\Omega} = 2.5mA$$

V_{imax} ve $I_Z = 9.5mA$ için R_L maksimum olur.

$$I_R = \frac{V_{imax} - V_{Zmax}}{R} = \frac{10V - 6V}{0.4k\Omega} = 10mA$$

$$I_{Lmin} = I_R - I_{Zmax} = 10mA - 9.5mA = 0.5mA$$

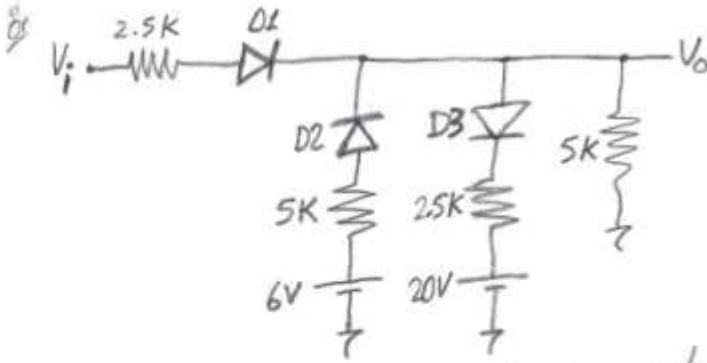
$$R_{Lmax} = \frac{V_{Zmax}}{I_{Lmin}} = \frac{6V}{0.5mA} = 12k\Omega$$

$$2k\Omega \leq R_L \leq 12k\Omega$$

$$0.5mA \leq I_L \leq 2.5mA$$

Zener üzerindeki maksimum güç tüketimini

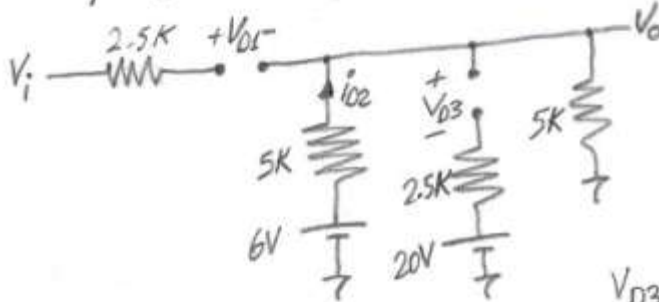
$$P_{max} = V_{Zmax} \cdot I_{Zmax} = (6V) \times (9.5mA) = 57mW$$



Bütün diyotlar idealdır.
 $V_i - V_o$ grafiğini çiziniz.

$-\infty < V_i < ?$ D_1, D_3 kapalı, D_2 açıktır.

$$i_{D2} = \frac{6V}{5K + 5K} = \frac{6V}{10K} = 0.6 \text{ mA} > 0 \checkmark$$

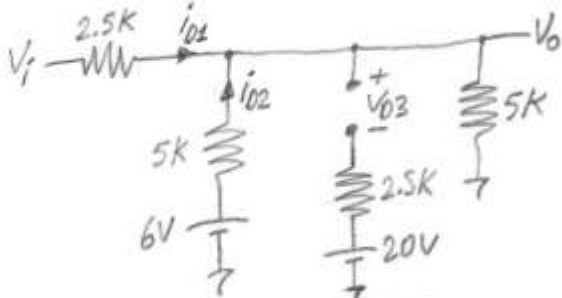


$$V_o = 5K \cdot i_{D2} = 5K \cdot 0.6 \text{ mA} = 3V$$

$$V_{D1} = V_i - V_o = V_i - 3 < 0 \rightarrow V_i < 3V$$

$$V_{D3} = V_o - 20 = 3 - 20 = -17V < 0 \checkmark$$

$3 < V_i < ?$ D_1, D_2 açık, D_3 kapalıdır.



$$V_o = 5K \cdot (i_{D1} + i_{D2}) = 5K \cdot \left(\frac{V_i - V_o}{2.5K} + \frac{6 - V_o}{5K} \right)$$

$$= 2V_i - 2V_o + 6 - V_o = 2V_i + 6 - 3V_o$$

$$4V_o = 2V_i + 6 \rightarrow V_o = \frac{V_i + 3}{2} \text{ olur.}$$

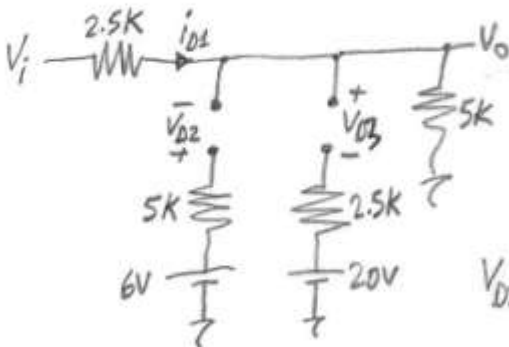
$$i_{D1} = \frac{V_i - V_o}{2.5K} = \frac{V_i - \frac{V_i + 3}{2}}{2.5K} > 0 \rightarrow V_i > 3V \checkmark$$

$$i_{D2} = \frac{6 - V_o}{5K} = \frac{6 - \frac{V_i + 3}{2}}{5K} > 0 \rightarrow V_i < 9V$$

$$V_{D3} = V_o - 20 = \frac{V_i + 3}{2} - 20 < 0$$

$$V_i < 37V$$

$9 < V_i < ?$ D_2, D_3 kapalı, D_1 açık olmalıdır.



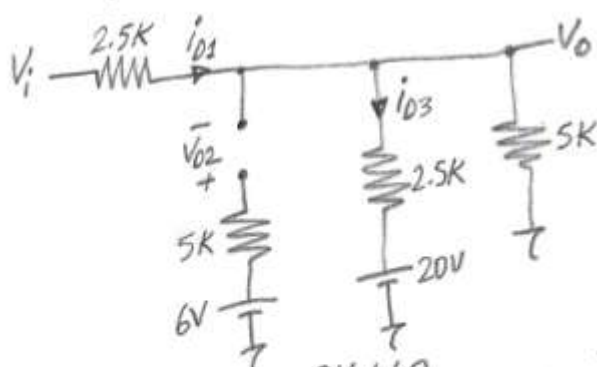
$$V_o = 5K \cdot i_{D1} = 5K \cdot \frac{V_i}{2.5K + 5K} = \frac{2V_i}{3} \text{ olur.}$$

$$i_{D1} = \frac{V_i - V_o}{2.5K} = \frac{V_i - \frac{2V_i}{3}}{2.5K} > 0 \rightarrow V_i > 0V \checkmark$$

$$V_{D2} = 6 - V_o = 6 - \frac{2V_i}{3} < 0 \rightarrow V_i > 9V \checkmark$$

$$V_{D3} = V_o - 20 = \frac{2V_i}{3} - 20 < 0 \rightarrow V_i < 30V$$

$30 \leq V_i < ?$ D1, D3 açık, D2 kapalıdır.



$$V_o = 5K \cdot (i_{D1} - i_{D3})$$

$$= 5K \cdot \left(\frac{V_i - V_o}{2.5} - \frac{V_o - 20}{2.5} \right)$$

$$= 2V_i - 2V_o - 2V_o + 40$$

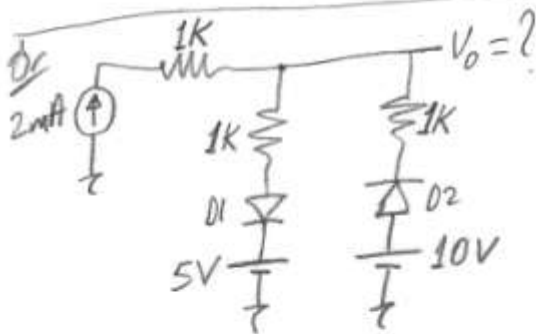
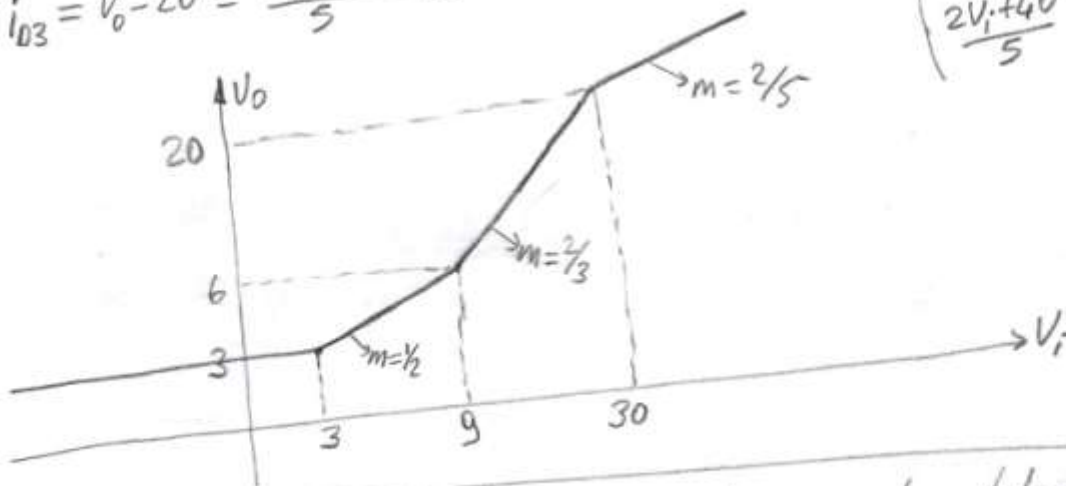
$$5V_o = 2V_i + 40 \rightarrow V_o = \frac{2V_i + 40}{5}$$

$$i_{D1} = \frac{V_i - V_o}{2.5K} = \frac{V_i - \frac{2V_i + 40}{5}}{2.5K} > 0 \rightarrow V_i > \frac{40}{3} V \checkmark$$

$$V_{D2} = 6 - V_o = 6 - \frac{2V_i + 40}{5} < 0 \rightarrow V_i > -5V \checkmark$$

$$i_{D3} = V_o - 20 = \frac{2V_i + 40}{5} - 20 > 0 \rightarrow V_i > 30V \checkmark$$

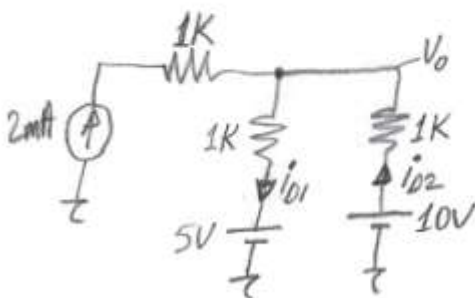
$$V_o = \begin{cases} 3 & V_i < 3 \\ \frac{V_i + 3}{2} & 3 \leq V_i < 9 \\ \frac{2V_i}{3} & 9 \leq V_i < 30 \\ \frac{2V_i + 40}{5} & V_i \geq 30 \end{cases}$$



Akım kaynağından dolayı D1 açık, D2 kapalı kabul ederseniz

$$i_{D1} = \frac{V_o - 5V}{1K} = 2mA \rightarrow V_o = 7V$$

$$V_{D2} = 10 - V_o = 10 - 7 = 3V > 0 \quad \text{D2 açık olmalı.}$$

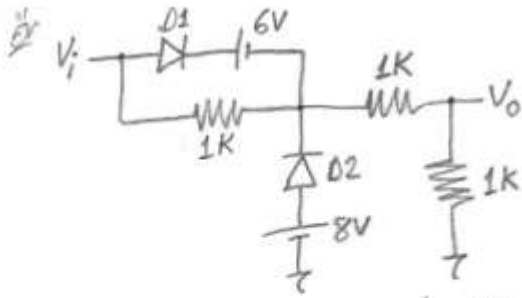


$$i_{D1} = i_{D2} + 2mA$$

$$5V + 1K \cdot i_{D1} = 10V - 1K \cdot i_{D2}$$

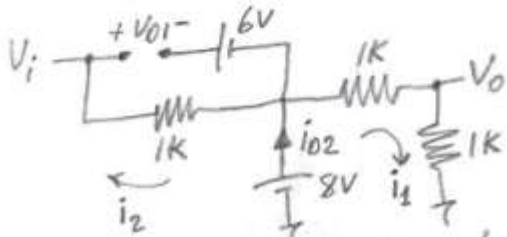
$$5 + i_{D2} + 2 = 10 - i_{D2} \rightarrow i_{D2} = \frac{3}{2} mA$$

$$V_o = 10V - 1K \cdot i_{D2} = 8.5 \text{ Volt}$$



Bütün diyotlar idealdir.
 $V_i - V_o$ grafiğini çiziniz.

$-\infty < V_i < ?$ D1 kapalı, D2 açıktır.

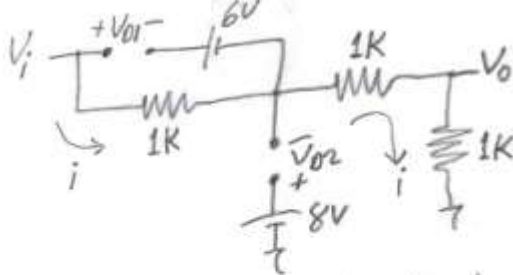


$$i_2 = \frac{8V}{2K} = 4mA, V_o = 1K \cdot i_2 = 1K \cdot 4mA = 4V$$

$$V_{D1} = V_i - 6 - 8 = V_i - 14 < 0 \rightarrow V_i < 14V$$

$$i_{D2} = i_1 + i_2 = 4mA + \frac{8 - V_i}{1K} = 12 - V_i > 0 \rightarrow V_i < 12V$$

$12 \leq V_i < ?$ D1 ve D2 kapalıdır.

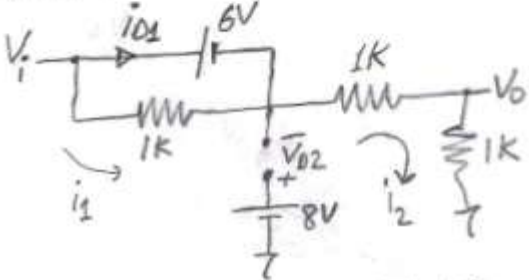


$$i = \frac{V_i}{3K}, V_o = 1K \cdot i = 1K \cdot \frac{V_i}{3K} = \frac{V_i}{3}$$

$$V_{D1} = V_i - 6 - 2i = V_i - 6 - \frac{2V_i}{3} = \frac{V_i}{3} - 6 < 0 \rightarrow V_i < 18V$$

$$V_{D2} = 8 - 2i = 8 - \frac{2V_i}{3} < 0 \rightarrow V_i > 12V \checkmark$$

$18 \leq V_i < ?$ D1 açıktır, D2 kapalıdır.



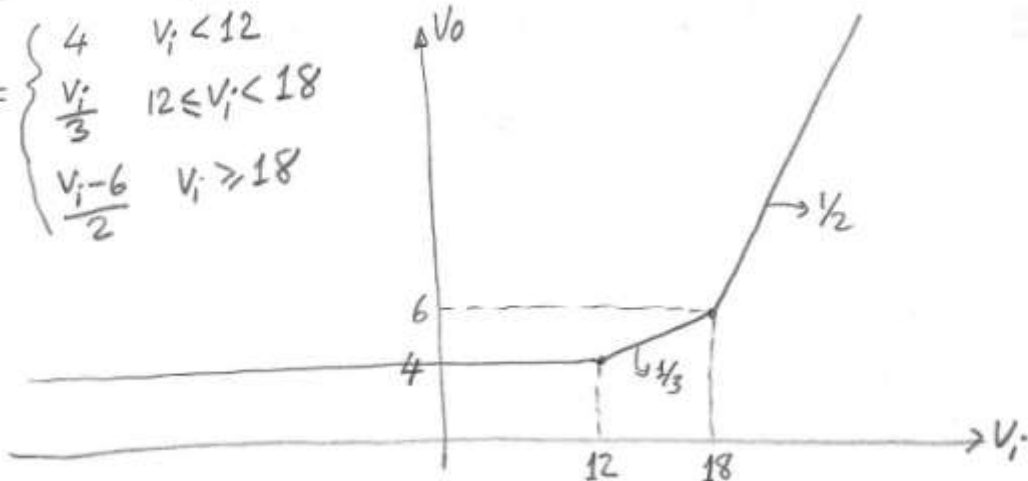
$$i_1 = \frac{6V}{1K} = 6mA, i_2 = \frac{V_i - 6V}{2K} = \frac{V_i - 6}{2}$$

$$V_o = 1K \cdot i_2 = \frac{V_i - 6}{2}$$

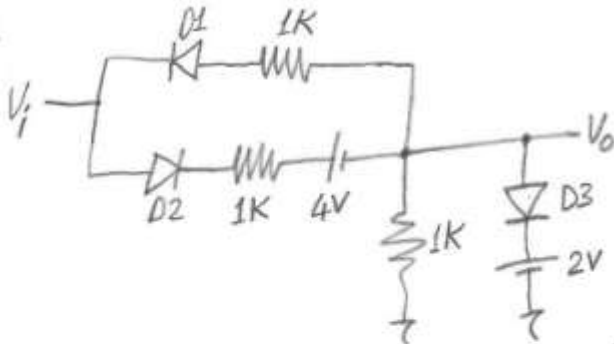
$$i_{D1} = i_2 - i_1 = \frac{V_i - 6}{2} - 6 > 0 \rightarrow V_i > 18V \checkmark$$

$$V_{D2} = 8 + 6 - V_i = 14 - V_i < 0 \rightarrow V_i > 14V \checkmark$$

$$V_o = \begin{cases} 4 & V_i < 12 \\ \frac{V_i}{3} & 12 \leq V_i < 18 \\ \frac{V_i - 6}{2} & V_i \geq 18 \end{cases}$$

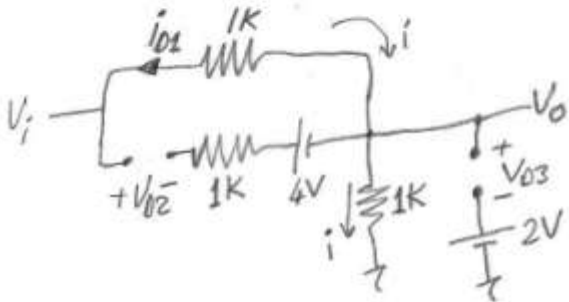


ör



Bütün diyotlar idealdir.
 $V_i - V_o$ grafiğini çiziniz.

$-\infty < V_i < ?$ D1 açık, D2 ve D3 kapalıdır.

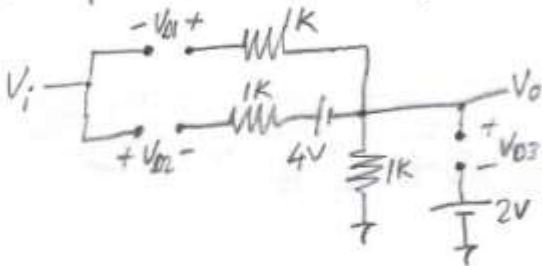


$$V_o = \frac{V_i}{2}, \quad i_{D1} = V_o - V_i = -\frac{V_i}{2} > 0 \rightarrow V_i < 0V$$

$$V_{D2} = V_i - 4 - V_o = V_i - 4 - \frac{V_i}{2} = \frac{V_i}{2} - 4 < 0 \rightarrow V_i < 8V$$

$$V_{D3} = V_o - 2 = \frac{V_i}{2} - 2 < 0 \rightarrow V_i < 4V$$

$0 \leq V_i < ?$ D1, D2, D3 kapalıdır.



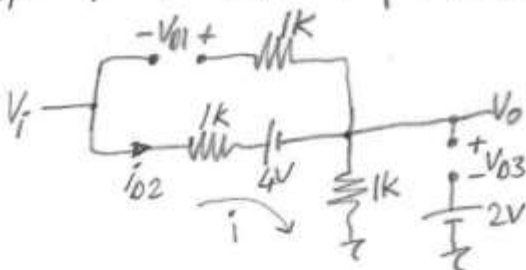
$$V_o = 0$$

$$V_{D1} = V_o - V_i = -V_i < 0 \rightarrow V_i > 0V \checkmark$$

$$V_{D2} = V_i - 4 - V_o = V_i - 4 < 0 \rightarrow V_i < 4V$$

$$V_{D3} = V_o - 2 = -2 < 0 \checkmark$$

$4 \leq V_i < ?$ D1, D3 kapalı, D2 açıktır.



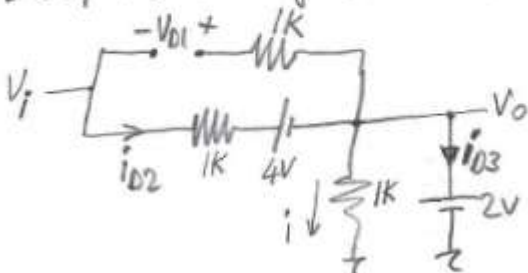
$$V_o = \frac{V_i - 4}{2}$$

$$i_{D2} = V_i - 4 - V_o = V_i - 4 - \frac{V_i - 4}{2} = \frac{V_i - 4}{2} > 0 \rightarrow V_i > 4V \checkmark$$

$$V_{D2} = V_o - V_i = \frac{V_i - 4}{2} - V_i = -\frac{V_i}{2} - 2 < 0 \rightarrow V_i > -4V \checkmark$$

$$V_{D3} = V_o - 2 = \frac{V_i - 4}{2} - 2 = \frac{V_i - 8}{2} < 0 \rightarrow V_i < 8V$$

$8 \leq V_i < ?$ D1 kapalı, D2 ve D3 açık.



$$V_o = 2V$$

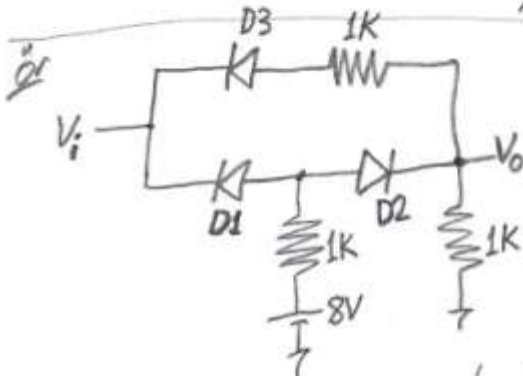
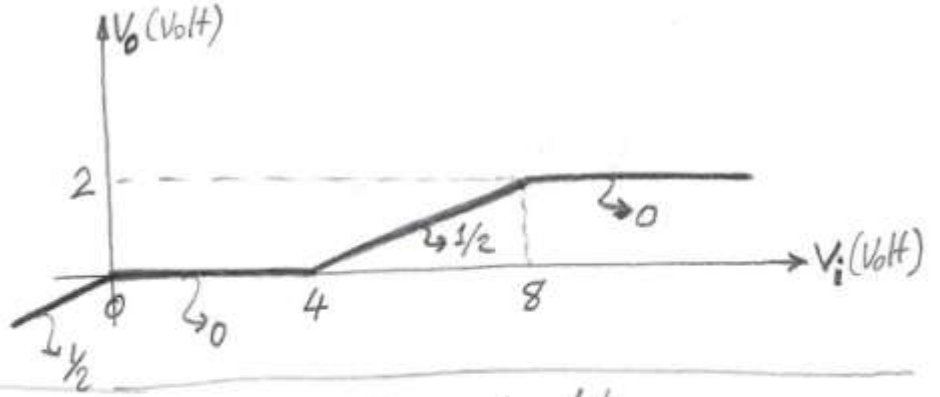
$$i_{D2} = \frac{V_i - 4 - V_o}{1K} = \frac{V_i - 6}{1K} > 0 \rightarrow V_i > 6V \checkmark$$

$$i = \frac{V_o}{1K} = 2mA$$

$$V_{D1} = V_o - V_i = 2 - V_i < 0 \rightarrow V_i > 2V \checkmark$$

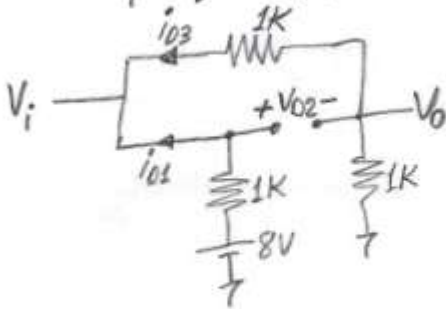
$$i_{D3} = i_{D2} - i = \frac{V_i - 6}{1K} - 2mA > 0 \rightarrow V_i > 8V \checkmark$$

$$V_o = \begin{cases} \frac{V_i}{2} & V_i < 0 \\ 0 & 0 \leq V_i < 4 \\ \frac{V_i - 4}{2} & 4 \leq V_i < 8 \\ 2 & V_i \geq 8 \end{cases}$$



Bütün diyotlar idealdir.
 $V_i - V_o$ grafiğini çiziniz.

$-\infty < V_i < ?$ D1, D3 açık, D2 kapalıdır.



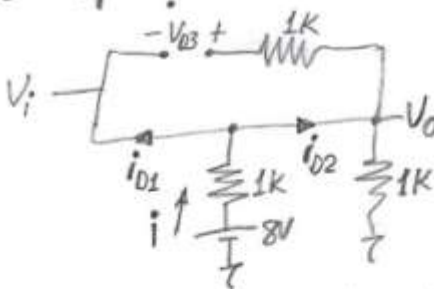
$$\frac{V_i - V_o}{1K} = \frac{V_o}{1K} \rightarrow V_o = \frac{V_i}{2}$$

$$i_{o1} = \frac{8V - V_i}{1K} = 8 - V_i > 0 \rightarrow V_i < 8V$$

$$V_{D2} = V_i - V_o = V_i - \frac{V_i}{2} = \frac{V_i}{2} < 0 \rightarrow V_i < 0V$$

$$i_{o3} = \frac{V_o - V_i}{1K} = V_o - V_i = \frac{V_i}{2} - V_i = -\frac{V_i}{2} > 0 \rightarrow V_i < 0V$$

$0 \leq V_i < ?$ D1, D2 açık, D3 kapalıdır.

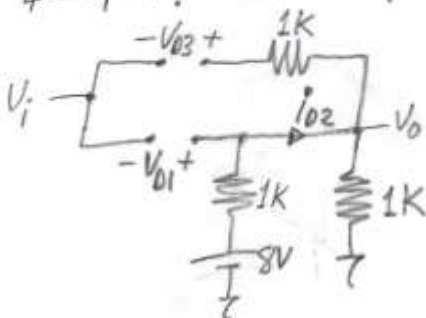


$$V_o = V_i, \quad i_{o2} = \frac{V_o}{1K} = V_i > 0 \checkmark$$

$$i = \frac{8 - V_o}{1K} = 8 - V_i, \quad i_{o1} = i - i_{o2} = 8 - V_i - V_i = 8 - 2V_i > 0 \rightarrow V_i < 4V$$

$$V_{D3} = V_o - V_i = V_i - V_i = 0 \checkmark$$

$4 \leq V_i < ?$ D1, D3 kapalı, D2 açıktır.

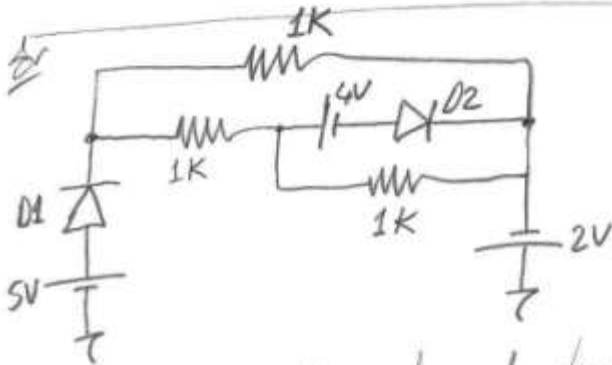
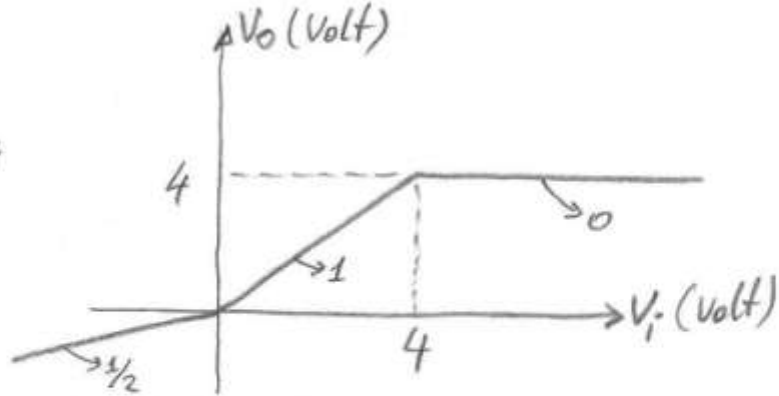


$$i_{o2} = \frac{8V}{2K} = 4mA > 0 \checkmark \quad V_o = 1K \times i_{o2} = 4V$$

$$V_{D1} = V_o - V_i = 4 - V_i < 0 \rightarrow V_i > 4V \checkmark$$

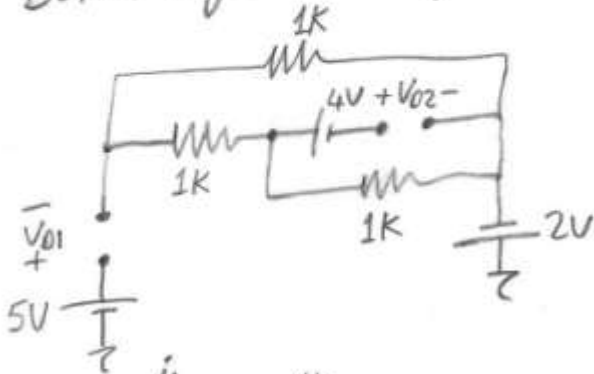
$$V_{D3} = V_o - V_i = 4 - V_i < 0 \rightarrow V_i > 4V \checkmark$$

$$V_o = \begin{cases} \frac{V_i}{2} & V_i < 0 \\ V_i & 0 \leq V_i < 4 \\ 4 & V_i \geq 4 \end{cases}$$



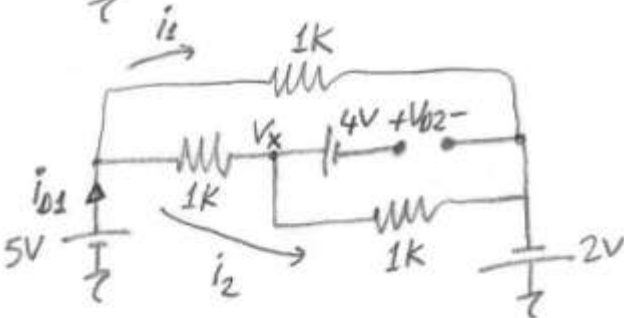
D1 ve D2 diyotlarının durumu nasıldır?

Bütün diyotları kapalı kabul edersek.



$$V_{D1} = 5V + 2V = 7V > 0 \text{ açık olmalı}$$

$$V_{D2} = -4V < 0 \text{ kapalı olmalı}$$



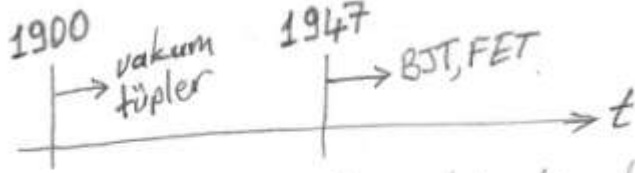
$$i_1 = \frac{5V + 2V}{1K} = 7 \text{ mA}$$

$$i_2 = \frac{5V + 2V}{2K} = 3.5 \text{ mA}$$

$$i_{D1} = i_1 + i_2 = 7 \text{ mA} + 3.5 \text{ mA} = 10.5 \text{ mA} > 0 \checkmark$$

$$V_x = 5V - 1K \times i_2 = 5 - 3.5 = 1.5 \text{ V}$$

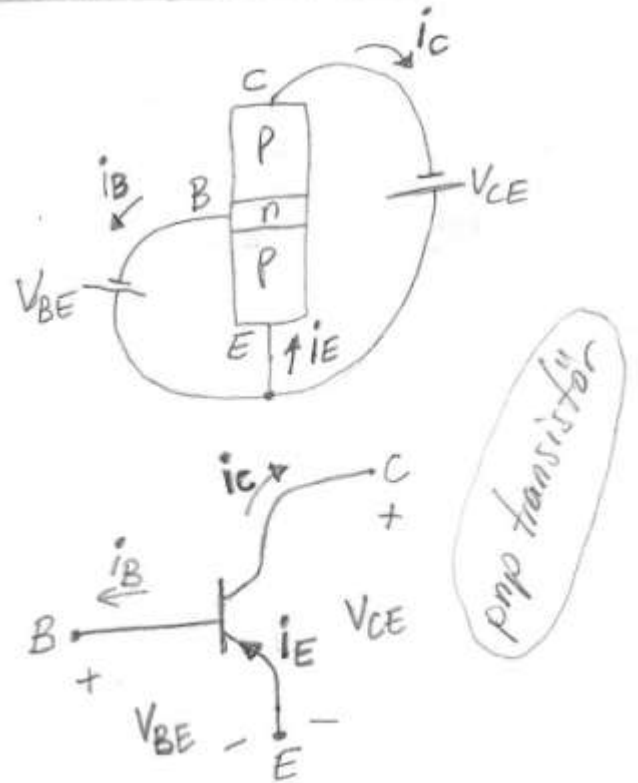
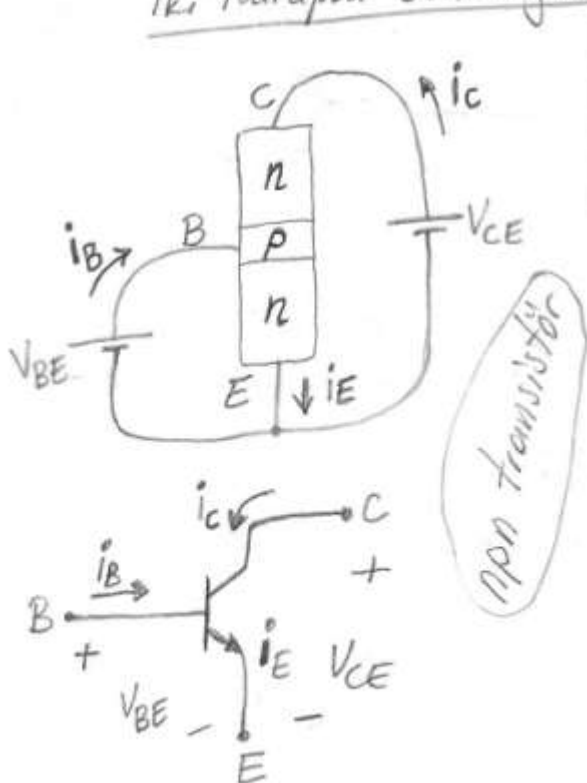
$$V_{D2} = V_x - 4 + 2 = 1.5 - 2 = -0.5 \text{ V} < 0 \checkmark$$

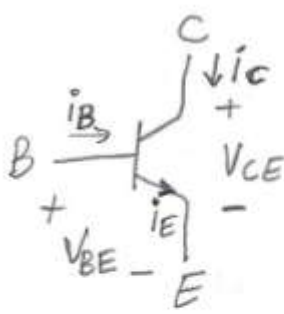
Transistörler

BJT: Bipolar Junction Transistor
FET: Field Effect Transistor

1904'te vakum tüp diyodu J.A.Flemming tarafından bulundu. 1906'da Lee De Forest, kontrol ılgarası denen ve ilk yükselteç sayılan triyodun ortayı çıkmasını sağlayan üçüncü bir elemanı vakum diyodu ekledi. Üretim 1922 yılında 1 milyon tüp iken, 1937'de 100 milyon tüpe yükseldi. 1930'ların ilk yıllarında dört elemanlı tetrot ve beş elemanlı pentot, elektronik tüp endüstrisinde ağırlık korumayı başladı.

1947'de üç uçlu yarıiletken bir eleman olan ilk transistör bulundu. Tüpe göre avantajları çok fazlaydı. Daha küçük ve daha hafifti. Isıtıcıya ve ısıma süresine gereksinimi yoktu. Bu yüzden ısıtıcı kaybı yoktu. Sağlam bir yapıya sahipti. Daha az güç harcadığından daha verimliydi. Daha küçük oranda çalışması perilerine peresinin duymaktaydı.

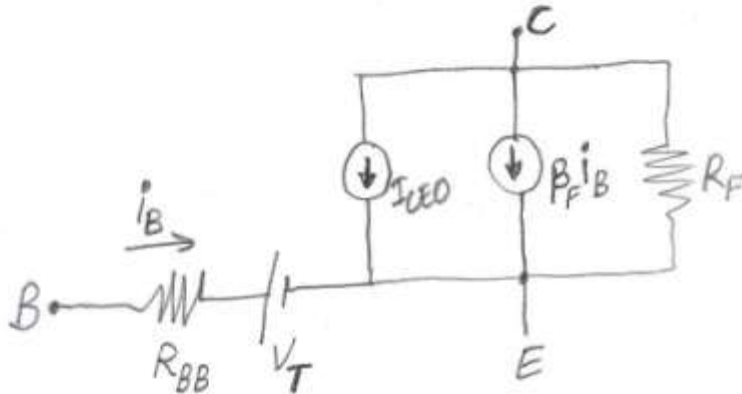
İki Kutuplu Jonksiyon Transistörleri (BJT'ler)



$$i_C = \beta i_B = \alpha i_E$$

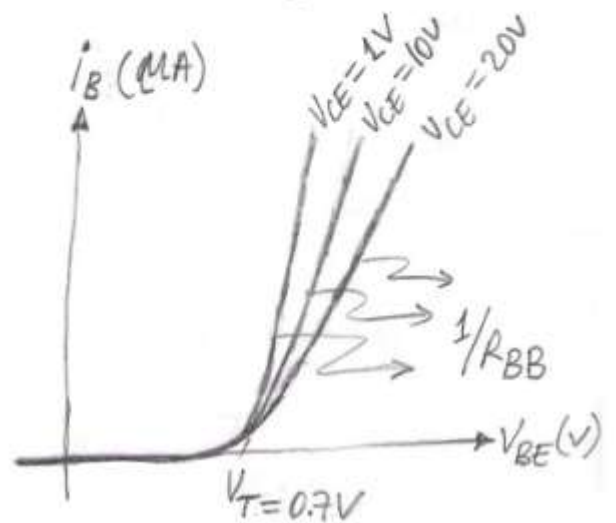
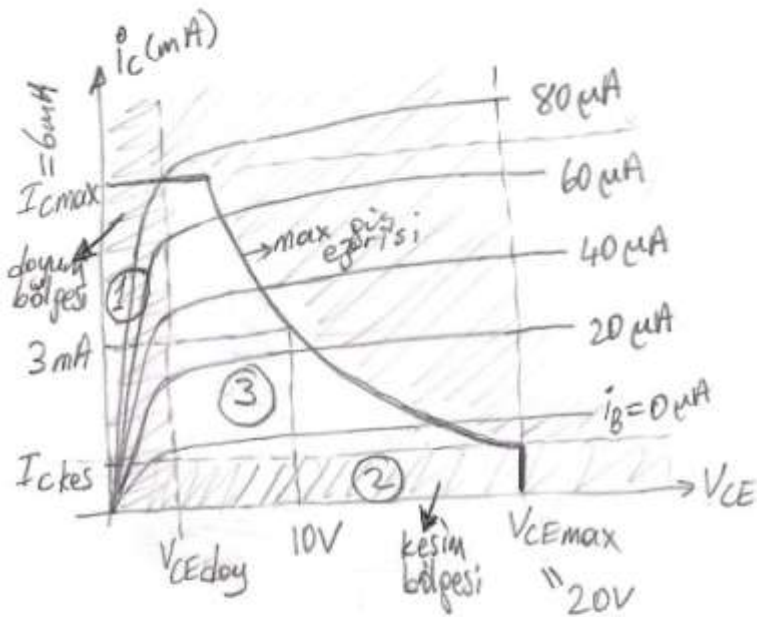
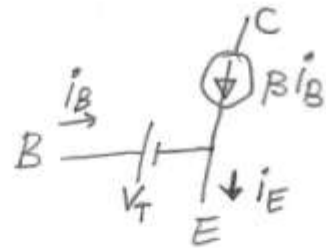
$$i_E = i_C + i_B = \beta i_B + i_B = (\beta + 1) \cdot i_B$$

$$\alpha = \frac{\beta}{\beta + 1} \text{ veya } \beta = \frac{\alpha}{1 - \alpha}$$



$$R_{BB} \rightarrow 0, R_F \rightarrow \infty$$

$$I_{CE0} \rightarrow 0, \beta_F \rightarrow \beta$$



$$I_{Cmax} = 6mA, V_{CEmax} = 20V, P_{Cmax} = V_{CE} \cdot I_C = (10V) \times (3mA) = 30mVA = 30mW$$

① Doyma (Saturation) Bölgesi $V_{BE} \gg V_T, V_{CE} \approx 0.2V$

② Kesim (Cut off) Bölgesi $V_{BE} \leq V_T, i_B = 0, i_C \approx 0$

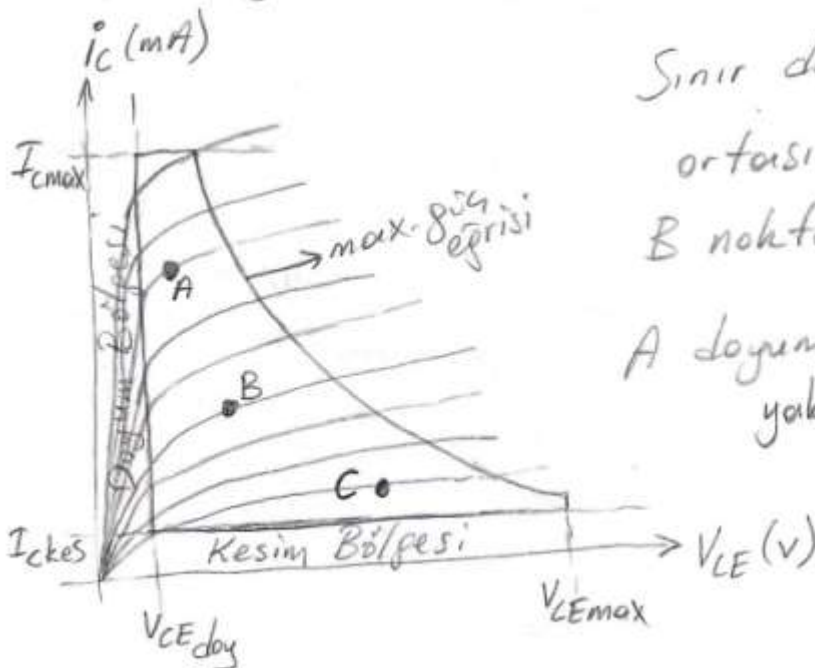
③ Aktif Bölge $i_C = \beta i_B > 0$

BJT'lerde DC Öngerilimleme

BJT'lerin akım veya gerilim yükseltme veya kontrol (açma-kapama) elemanı olarak kullanılması için önce öngerilimlenmesi lazımdır. Öngerilimleme transistörü açık duruma getirmek ve en doğrusal bölgede çalıştırmak için gereklidir. Öngerilimleme olmasaydı transistör daha baştan kapalı olurdu.

Öngerilimleme sabit bir akımı transistör üzerinden geçirmek ve transistör üzerinde istenilen sabit bir gerilim düşüsünü sağlamakla ilgili olduğundan statik bir işlemdir. Transistörün öngerilimlendiği noktayı çalışma noktası veya Q-noktası denir.

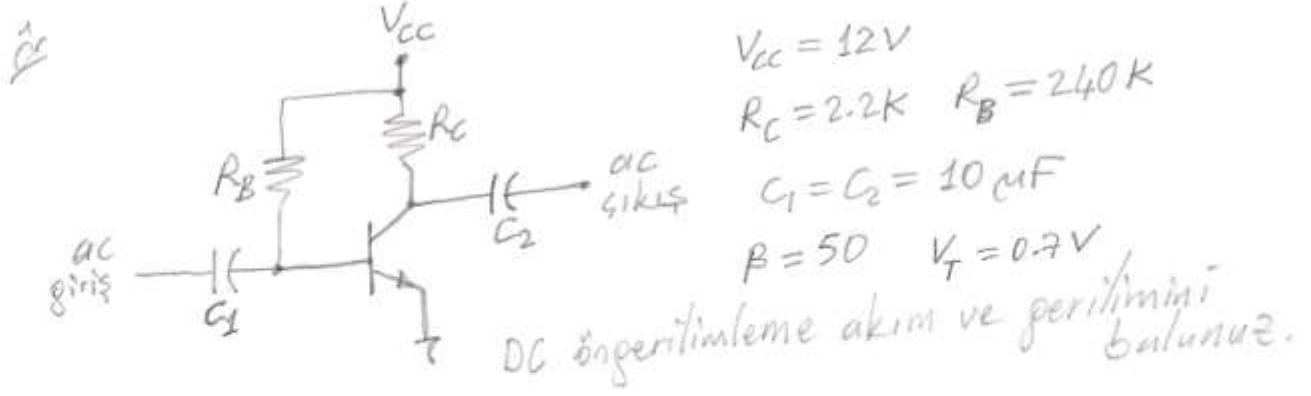
Öngerilimlemeye ek olarak devreye bir sinyal uygulan-
dıgında çalışma noktası kayar. Çalışma noktasındaki
kaymaların akım ve gerilim yönünden minimum-maksimum
sınırlar içerisinde kalması lazımdır ki transistör doğru
çalışabilsin. Transistörün düzgün çalışabildiği noktaların
oluşturduğu bölgeye çalışma bölgesi denir.



Sınır değerlerin tam
ortasında olduğundan
B noktası en uygun noktadır.

A doyuma yakın, C kesime
yakındır.

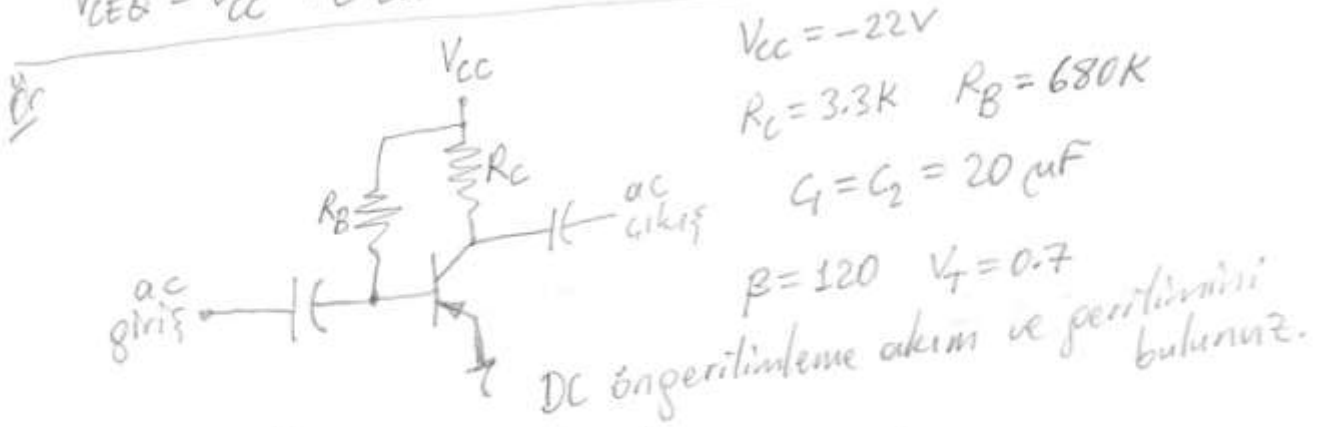
Max. güç eğrisi
dışındadır transistör
çalıştırılabilir. Ancak
ömrü kısalar veya bozulabilir.



$$I_{BQ} = \frac{V_{CC} - V_{BE}}{R_B} = \frac{12V - 0.7V}{240K} = 47.08 \mu A$$

$$I_{CQ} = \beta I_{BQ} = 50 \times (47.08 \mu A) = 2.35 mA$$

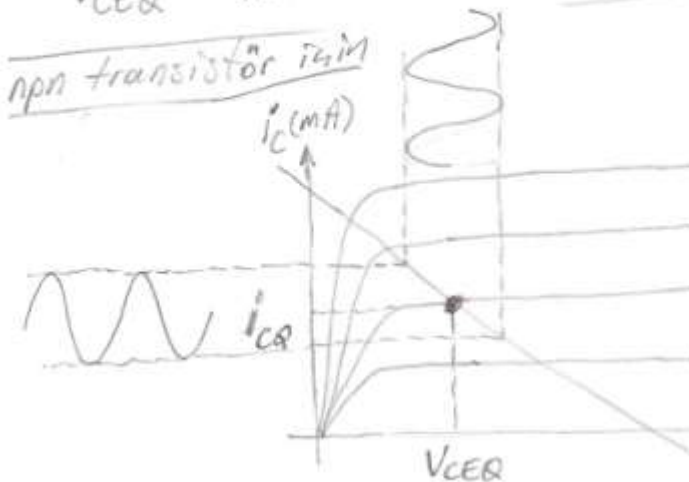
$$V_{CEQ} = V_{CC} - R_C I_{CQ} = 12V - (2.2K) \times (2.35 mA) = 6.83 V$$

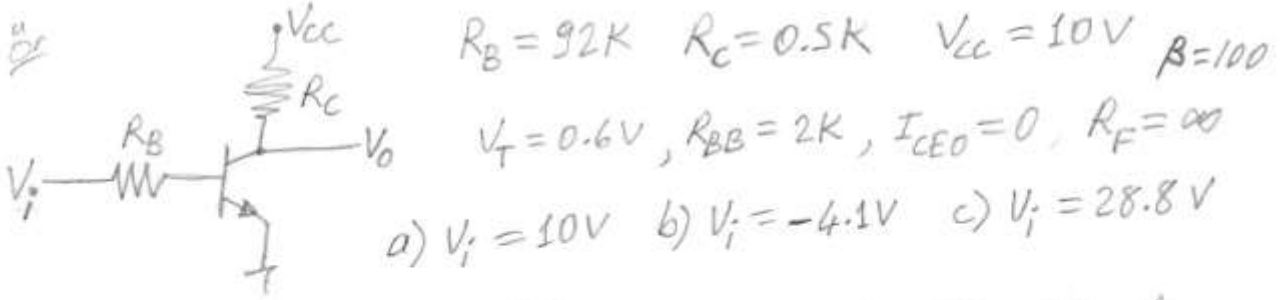


$$I_{BQ} = \frac{V_{BE} - V_{CC}}{R_B} = \frac{-0.7V - (-22V)}{680K} = 31.32 \mu A$$

$$I_{CQ} = \beta I_{BQ} = 120 \times (31.32 \mu A) = 3.76 mA$$

$$V_{CEQ} = V_{CC} + R_C I_{CQ} = -22V + (3.3K) \times (3.76 mA) = -9.6 V$$

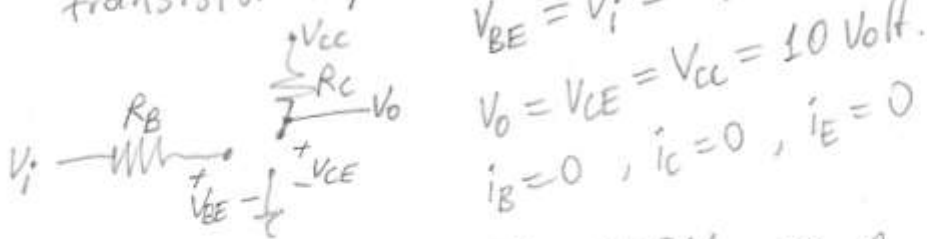




a) $i_B = \frac{V_i - V_T}{R_B + R_{BB}} = \frac{10V - 0.6V}{92K + 2K} = 0.1mA$ $i_C = \beta i_B = 10mA$

$V_o = V_{CC} - R_C i_C = 10V - (0.5K) \cdot (10mA) = 5V$ *çalışma noktası*

b) $i_B = \frac{V_i - V_T}{R_B + R_{BB}} = \frac{-4.1V - 0.6V}{92K + 2K} = \frac{-4.7V}{94K} = -0.05mA < 0$ olamaz.
transistör kapalı.

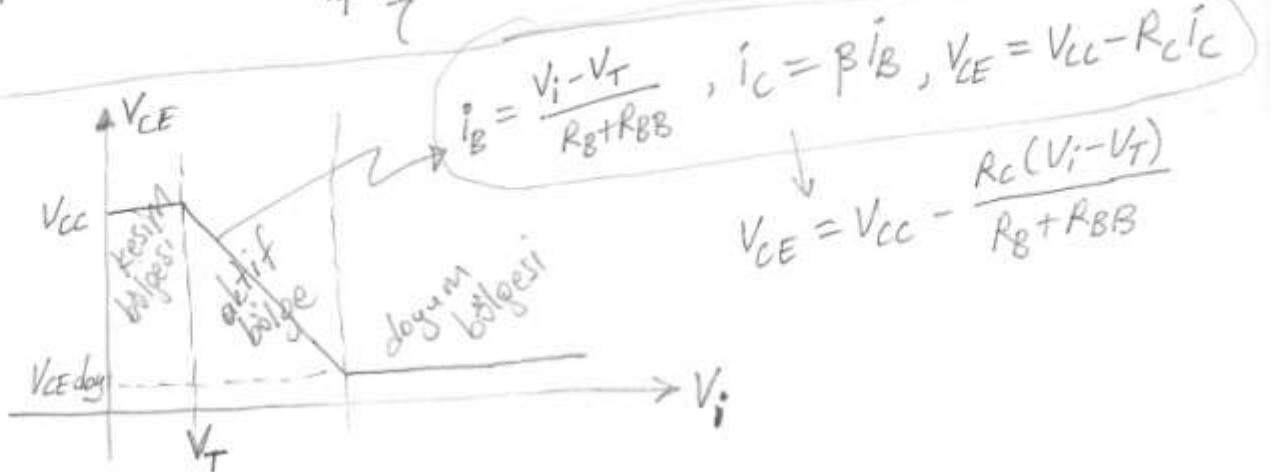
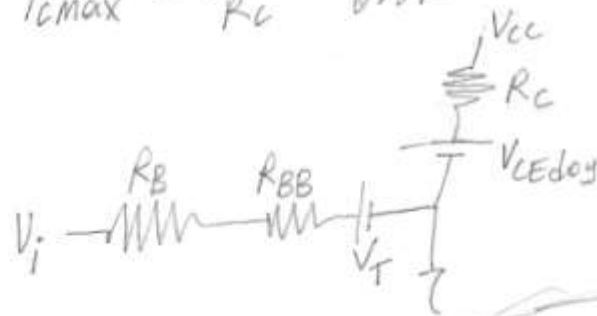


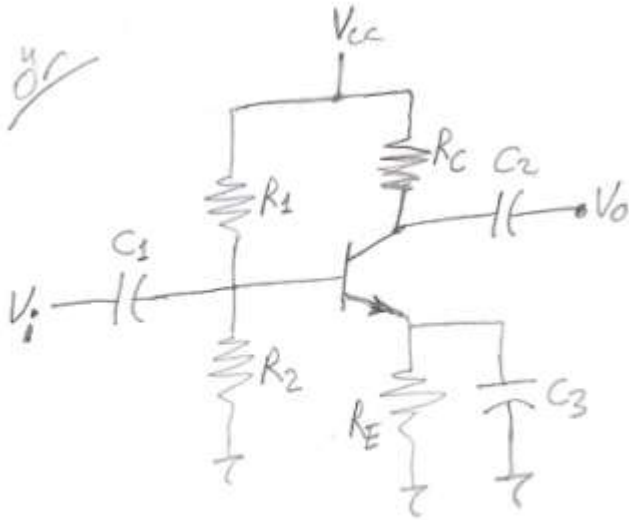
c) $i_B = \frac{V_i - V_T}{R_B + R_{BB}} = \frac{28.8V - 0.6V}{92K + 2K} = \frac{28.2V}{94K} = 0.3mA$

$i_{Cmax} = \frac{V_{CC}}{R_C} = \frac{10V}{0.5K} = 20mA$

$i_C = \beta i_B = 100 \cdot (0.3mA) = 30mA > i_{Cmax}$

transistör doyum noktasında





$$V_{CC} = 22V \quad \beta = 140$$

$$R_1 = 39K \quad R_2 = 3.9K \quad V_T = 0.7V$$

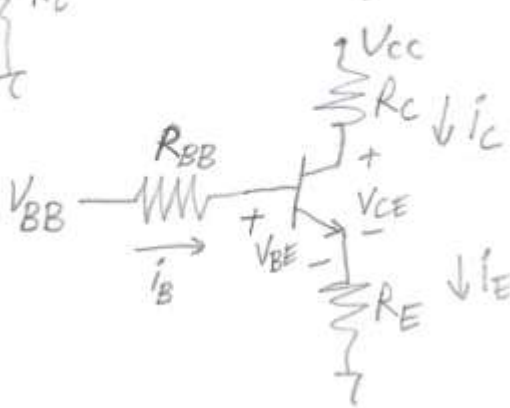
$$R_C = 10K \quad R_E = 1.5K$$

$$C_1 = C_2 = 10\mu F \quad C_3 = 50\mu F$$

DC biasing akımı ve voltajını bulunuz.

$$R_{BB} = R_1 \parallel R_2 = \frac{R_1 R_2}{R_1 + R_2} = \frac{39K \times 3.9K}{39K + 3.9K} = 3.55K$$

$$V_{BB} = \frac{R_2}{R_1 + R_2} V_{CC} = \frac{3.9K}{39K + 3.9K} \times 22V = 2V$$

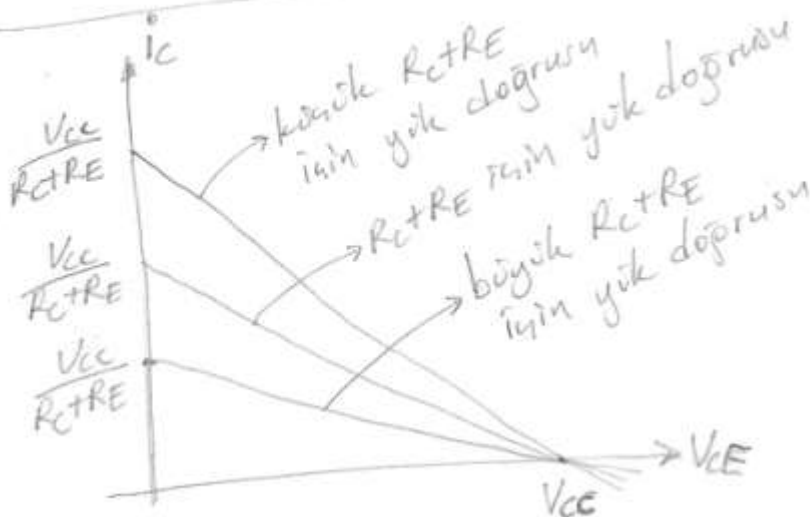


$$I_{BQ} = \frac{V_{BB} - V_{BE}}{R_{BB} + (\beta + 1)R_E}$$

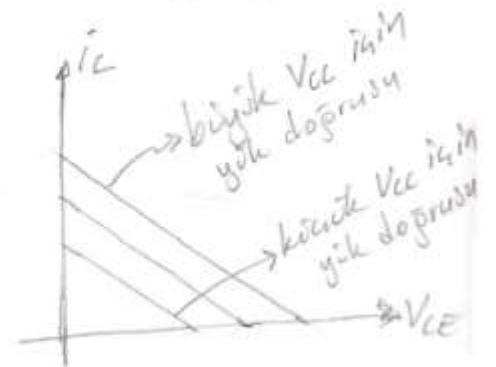
$$= \frac{2V - 0.7V}{3.55K + 141 \times (1.5K)} = 6.05 \mu A$$

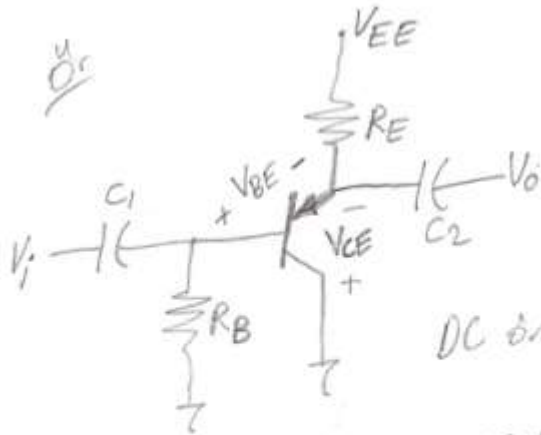
$$I_{CQ} = \beta I_{BQ} = 140 \times 6.05 \mu A = 0.85 mA \approx I_{EQ}$$

$$V_{CEQ} = V_{CC} - (R_C + R_E) I_{CQ} = 22V - (10K + 1.5K) \times (0.85 mA) = 12.2V$$



$$I_C = \frac{V_{CC} - V_{CE}}{R_C + R_E}$$





$$V_{EE} = 20V \quad \beta = 80$$

$$C_1 = C_2 = 10 \mu F \quad V_T = 0.7V$$

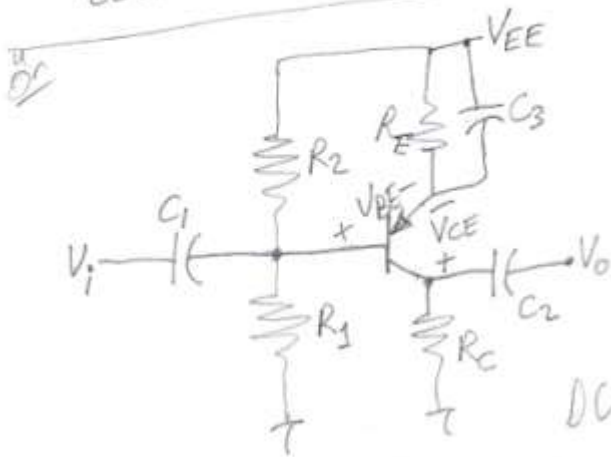
$$R_B = 240K \quad R_E = 2K$$

DC öngerilimleme akımı ve voltajını bulunuz.

$$I_{BQ} = \frac{V_{EE} + V_{BE}}{R_B + (\beta + 1)R_E} = \frac{20V - 0.7V}{240K + 81 \times (2K)} = 48.01 \mu A$$

$$I_{CQ} = \beta I_B = 80 \times (48.01 \mu A) = 3.84 mA \approx I_{EQ}$$

$$V_{CEQ} = R_E I_{EQ} - V_{EE} = (2K) \times (3.84 mA) - 20V = -12.32V$$



$$V_{EE} = 10V \quad \beta = 180 \quad V_T = 0.7V$$

$$C_1 = C_2 = 10 \mu F, \quad C_3 = 20 \mu F$$

$$R_1 = 43K \quad R_2 = 10K$$

$$R_C = 6.2K \quad R_E = 2K$$

DC öngerilimleme akımı ve voltajını bulunuz.

$$V_{BB} = \frac{R_1 V_{EE}}{R_1 + R_2} = \frac{43K \times 10V}{43K + 10K} = 8.11V$$

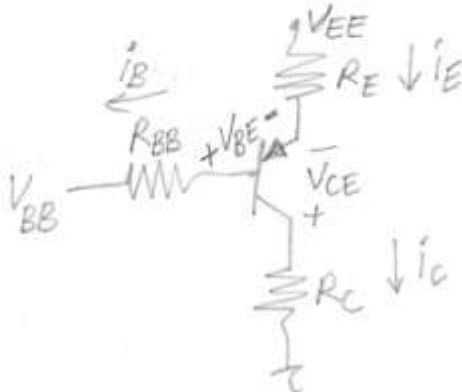
$$R_{BB} = R_1 || R_2 = \frac{R_1 R_2}{R_1 + R_2} = \frac{43K \times 10K}{43K + 10K} = 8.11K$$

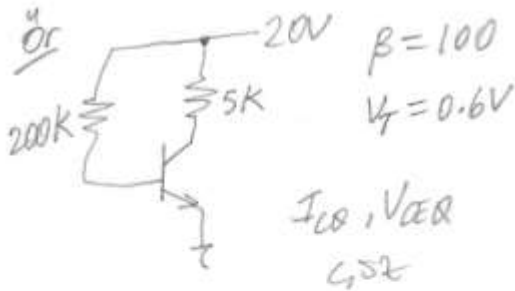
$$I_{BQ} = \frac{V_{EE} - V_{BB} + V_{BE}}{R_{BB} + (\beta + 1)R_E} = \frac{10V - 8.11V - 0.7V}{8.11K + 181 \times 2K}$$

$$= \frac{1.19V}{370.11K} = 3.215 \mu A$$

$$I_{CQ} = \beta I_{BQ} = 180 \times 3.215 \mu A \approx 0.579 mA \approx I_{EQ}$$

$$V_{CE} = (R_C + R_E) I_{CQ} - V_{EE} = 8.2K \times 0.579 mA - 10V \approx -5.25V$$



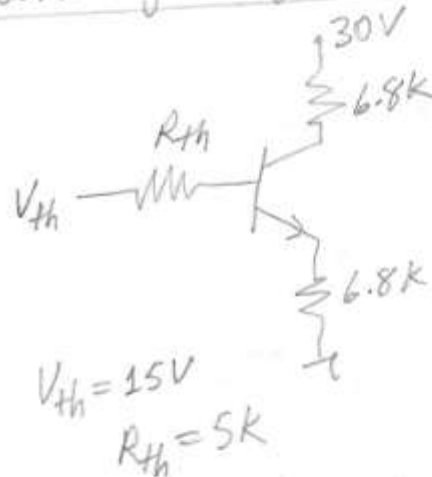
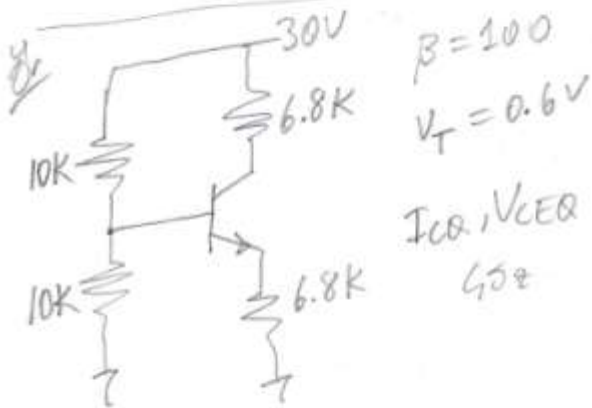


$$I_{BQ} = \frac{20V - 0.6V}{200k} = 0.097 \text{ mA}$$

$$I_{CQ} = \beta I_{BQ} = 9.7 \text{ mA}$$

$$V_{CEQ} = 20 - (5k) \times (9.7 \text{ mA}) = -28.5 < 0$$

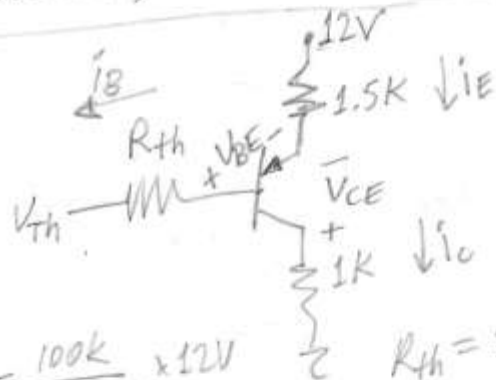
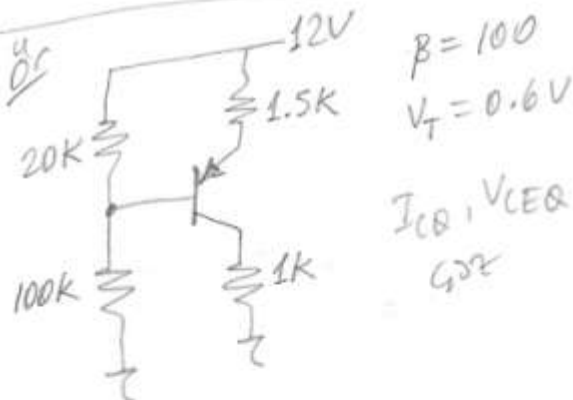
transistör doyum bölgesinde



$$I_{BQ} = \frac{V_{Th} - V_T}{R_{Th} + (\beta + 1)R_E} = \frac{15V - 0.6V}{5k + 101 \times 6.8k} \approx 20.815 \text{ } \mu\text{A}$$

$$I_{CQ} = \beta I_{BQ} = 2.0815 \text{ mA} \approx I_{EQ}$$

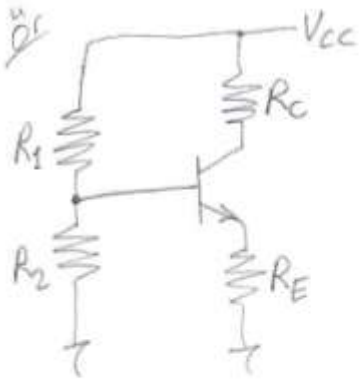
$$V_{CEQ} = 30 - (6.8k + 6.8k) \times (2.0815 \text{ mA}) \approx 1.69 \text{ V}$$



$$I_{BQ} = \frac{12 + V_{BE} - V_{Th}}{R_{Th} + (\beta + 1)R_E} = \frac{12 - 0.6 - 10}{16.67 + 101 \times 1.5} = \frac{1.4V}{168.17k} \approx 8.325 \text{ } \mu\text{A}$$

$$I_{CQ} = \beta I_{BQ} = 0.8325 \text{ mA}$$

$$V_{CEQ} = (R_C + R_E) I_{CQ} - 12V = 2.5k \times 0.8325 \text{ mA} - 12V \approx -9.92 \text{ V}$$

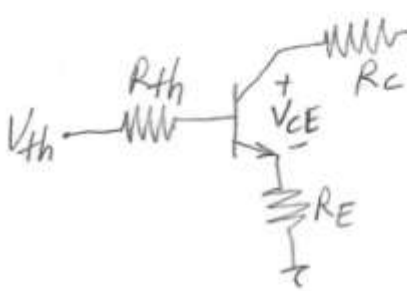


$$V_{CC} = 20V \quad R_2 = 50K \quad R_C = 1K \quad V_T = 0.7V$$

$$50 \leq \beta \leq 150 \text{ için}$$

$$3.9 \text{ mA} \leq I_C \leq 4.1 \text{ mA} \text{ oluyor ise}$$

R_1 ve R_E dirençlerini, V_{CE} aralığını bulunuz.



$$R_{Th} = R_1 \parallel R_2 = \frac{R_1 R_2}{R_1 + R_2} = \frac{50 R_1}{50 + R_1}$$

$$V_{Th} = \frac{R_2 V_{CC}}{R_1 + R_2} = \frac{1000}{50 + R_1}$$

$$I_C = \beta I_B = \frac{\beta (V_{Th} - V_T)}{R_{Th} + (\beta + 1) R_E}$$

$$\frac{619.1}{198.9} \text{ ile carp.}$$

$$3.9 = \frac{50 (V_{Th} - 0.7)}{R_{Th} + 51 R_E} \rightarrow 3.9 R_{Th} + 198.9 R_E = 50 V_{Th} - 35$$

$$4.1 = \frac{150 (V_{Th} - 0.7)}{R_{Th} + 151 R_E} \rightarrow 4.1 R_{Th} + 619.1 R_E = 150 V_{Th} - 105$$

$$8.039 R_{Th} = 5.631 V_{Th} - 3.942$$

$$\frac{402 R_1}{50 + R_1} = \frac{5631}{50 + R_1} - 3.942 \rightarrow R_1 \approx 13.386 K$$

$$V_{Th} = \frac{1000}{50 + R_1} \approx 15.78V, \quad R_{Th} = \frac{50 R_1}{50 + R_1} \approx 10.56 K$$

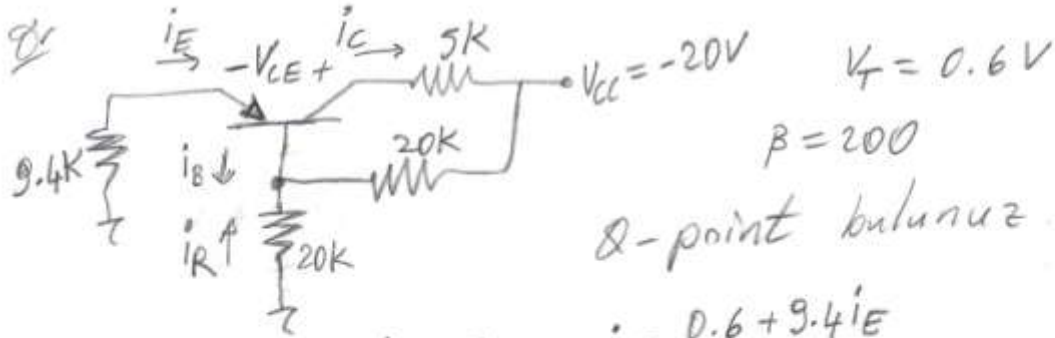
$$R_E = \frac{50 V_{Th} - 35 - 3.9 R_{Th}}{198.9} \approx 3.584 K$$

$$V_{CE} = V_{CC} - R_C I_C - R_E I_E \quad I_C \approx I_E$$

$$= V_{CC} - (R_C + R_E) I_C$$

$$I_C = 3.9 \text{ mA} \text{ için } V_{CE} = 20 - (1K + 3.584K) \times 3.9 \text{ mA} \approx 2.1224 V$$

$$I_C = 4.1 \text{ mA} \text{ için } V_{CE} = 20 - (1K + 3.584K) \times 4.1 \text{ mA} \approx 1.2056 V$$



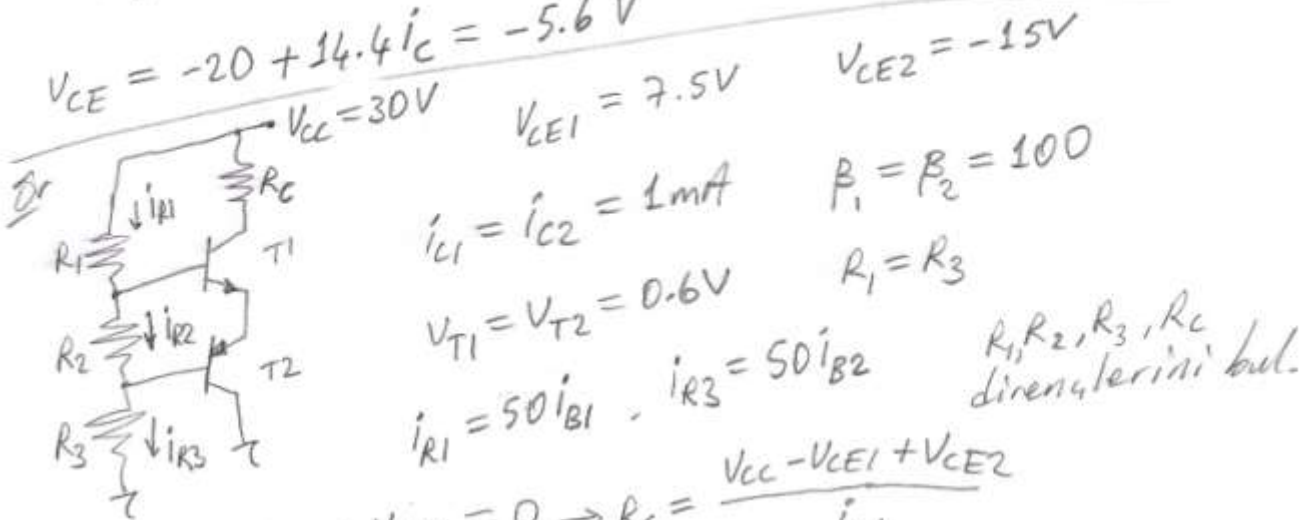
$$-9.4 i_E - V_T + 20 i_R = 0 \rightarrow i_R = \frac{0.6 + 9.4 i_E}{20}$$

$$V_{CC} + 20(i_B + i_R) + 20 i_R = 0 \rightarrow i_R = \frac{20 - 20 i_B}{40} = \frac{201 - i_E}{402}$$

$$i_R = i_R \rightarrow \frac{0.6 + 9.4 i_E}{20} = \frac{201 - i_E}{402} \rightarrow i_E \approx i_C \approx 1 \text{ mA}$$

$$-9.4 i_E + V_{CE} - 5 i_C = V_{CC} = -20 \quad i_E \approx i_C \text{ olduğundan}$$

$$V_{CE} = -20 + 14.4 i_C = -5.6 \text{ V}$$



$$V_{CC} - R_C i_{C1} - V_{CE1} + V_{CE2} = 0 \rightarrow R_C = \frac{V_{CC} - V_{CE1} + V_{CE2}}{i_{C1}}$$

$$R_C = \frac{30V - 7.5V - 15V}{1 \text{ mA}} = \frac{7.5V}{1 \text{ mA}} = 7.5 \text{ K}$$

$$i_{B1} = \frac{i_{C1}}{\beta_1} = 0.01 \text{ mA} \quad i_{B2} = \frac{i_{C2}}{\beta_2} = 0.01 \text{ mA}$$

$$i_{R1} = 50 i_{B1} = 0.5 \text{ mA}$$

$$i_{R3} = 50 i_{B2} = 0.5 \text{ mA}$$

$$R_1 i_{R1} + R_2 i_{R2} + R_3 i_{R3} = V_{CC}$$

$$R_1 i_{R1} + R_2 (i_{R1} - i_{B1}) + R_1 i_{R3} = V_{CC}$$

$$0.5 R_1 + 0.49 R_2 + 0.5 R_1 = 30 \Rightarrow R_1 = R_3 = 30 - 0.49 R_2$$

$$R_1 = R_3 \approx 28.8 \text{ K}$$

$$R_2 i_{R2} = V_{BE1} - V_{BE2}$$

$$R_2 = \frac{V_{BE1} - V_{BE2}}{i_{R1} - i_{B1}}$$

$$= \frac{0.6V + 0.6V}{0.49 \text{ mA}}$$

$$= 2.449 \text{ K}$$

Alan Etkili Transistörler (Field Effect Transistors - FET's)

n-p-n veya p-n-p tipli bir BJT (iki kutuplu jonksiyon transistörü) hem elektron hem de oyuk akımının kullanıldığı akım kontrollü bir transistördür. FET tek kutuplu bir transistördür. n kanallı bir FET elektron akımıyla, p kanallı bir FET ise oyuk akımla çalışan gerilim kontrollü bir transistördür.

FET'lerde giriş direnci $100\text{ M}\Omega$ civarındadır. BJT'lerde ise $2\text{ k}\Omega$ civarındadır.

FET'ler tek temel p-n jonksiyonuna sahip üç uçlu elemanlardır.

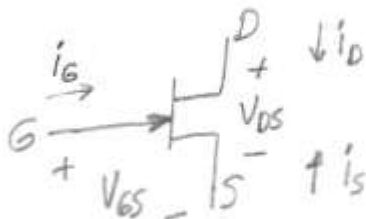
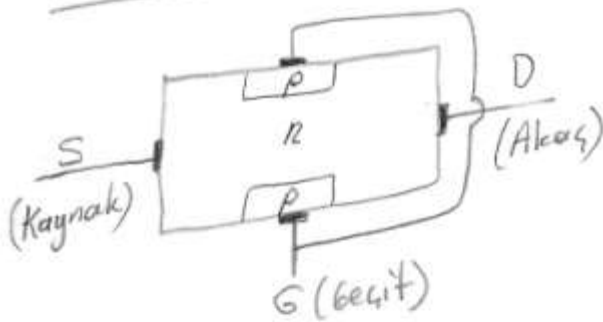
FET $\begin{cases} \text{JFET} \\ \text{MOSFET} \end{cases}$ $\begin{cases} \text{Kanal ayarlamalı MOSFET} \\ \text{Kanal oluşturmali MOSFET} \end{cases}$

JFET : Jonksiyon FET

MOSFET : Metaloksit yarıiletken FET

Büyük ölçekli entegre devreler öncelikle MOSFET'ler kullanılarak üretilirler.

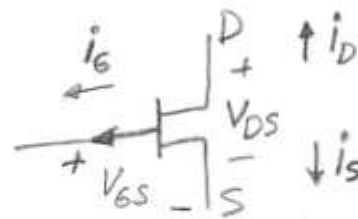
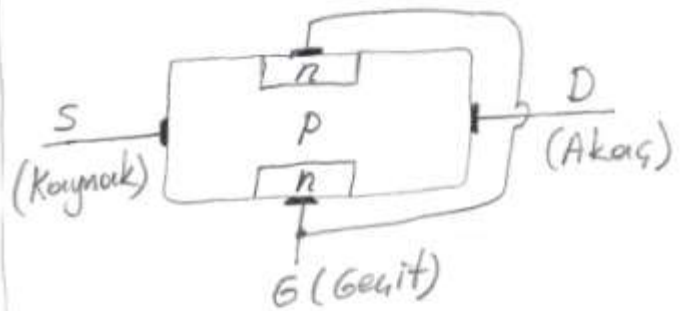
n kanallı JFET



$$i_G = 0, i_D = -i_S, i_D > 0$$

$$V_{DS} > 0, V_p < V_{GS} \leq 0$$

p kanallı JFET



$$i_G = 0, i_D = -i_S, i_D > 0$$

$$V_{DS} < 0, 0 \leq V_{GS} < V_p$$

I_{DSS} : Akar kaynak doyum akımı

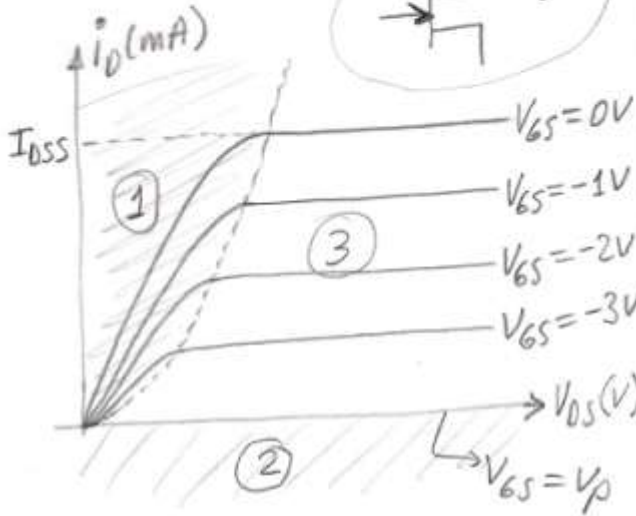
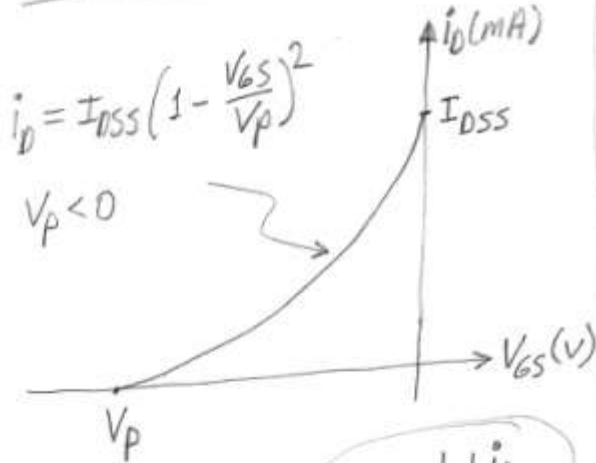
Sabit akım bölgesinde

$$i_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P}\right)^2$$

$$V_{DS} \geq V_{GS} - V_P > 0 \quad n \text{ kanallı}$$

$$V_{DS} \leq V_{GS} - V_P < 0 \quad p \text{ kanallı}$$

n kanallı JFET



① Direnç Bölgesi

$$V_{DS} \leq V_{GS} - V_P$$

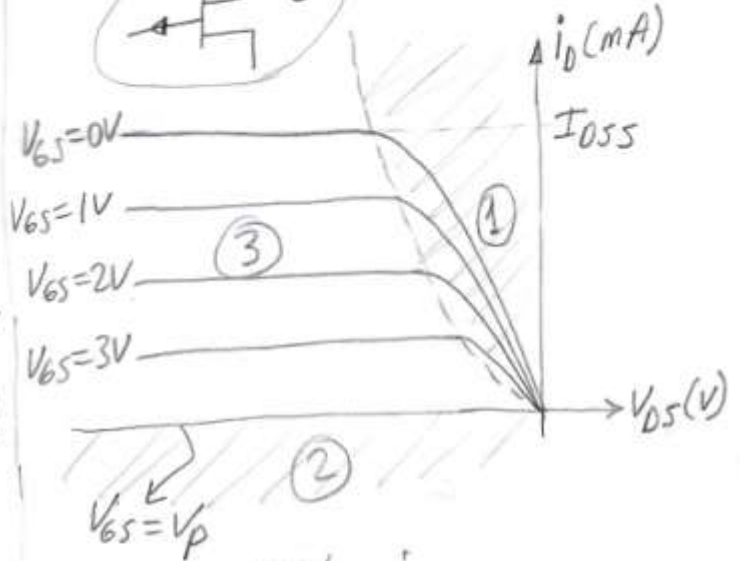
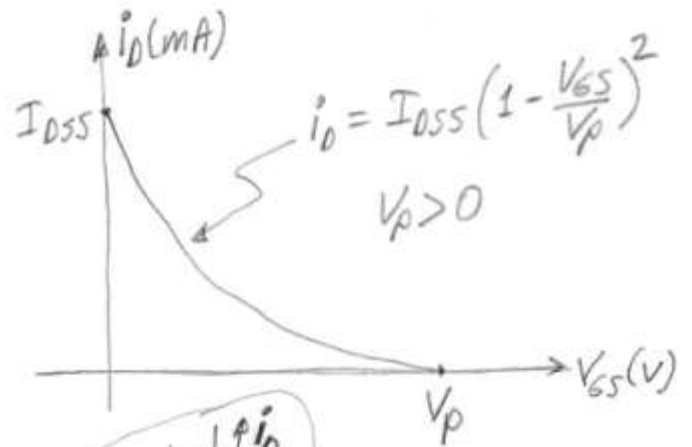
② Kapatlı Bölge $V_{GS} \leq V_P < 0$

③ Sabit akım bölgesi

$$V_{DS} \geq V_{GS} - V_P > 0$$

$$i_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P}\right)^2$$

p kanallı JFET



① Direnç Bölgesi

$$V_{DS} \geq V_{GS} - V_P$$

② Kapatlı Bölge $V_{GS} \geq V_P > 0$

③ Sabit Akım Bölgesi

$$V_{DS} \leq V_{GS} - V_P < 0$$

$$i_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P}\right)^2$$

Ör. Kısılma gerilimi $V_p = -4V$, akars-kaynak doyumu akımı $I_{DSS} = 12mA$ olan bir n kanallı JFET'in akars akımını aşağıdaki kapı-kaynak gerilimleri için bulunuz.

a) $V_{GS} = 0V$ b) $V_{GS} = -1.2V$ c) $V_{GS} = -2V$ d) $V_{GS} = -5V$ e) $V_{GS} = 1V$

$$I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_p}\right)^2 \text{ alırsak}$$

$$a) I_D = 12mA \left(1 - \frac{0}{-4}\right)^2 = 12mA$$

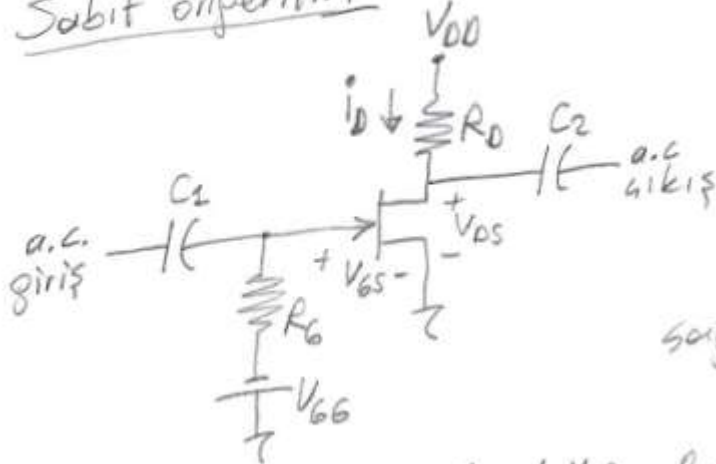
$$b) I_D = 12mA \left(1 - \frac{-1.2}{-4}\right)^2 = 5.88mA$$

$$c) I_D = 12mA \left(1 - \frac{-2}{-4}\right)^2 = 3mA$$

d) $V_{GS} = -5V < V_p = -4$
olduğundan JFET
kapalı bölgede

e) $V_{GS} = 1V > 0$ olamaz.
uygunsuz durum.

Sabit öngerilim



R_G direnci, C_1 kondansatörü
üzerinden uygulanacak
herhangi bir a.c. sinyalinin
 R_G üzerinde artırılmasını
saklamak için eklenmiştir.

$V_{DD} = 12V$ $V_{GG} = 1.5V$ $R_G = 1M\Omega$ $R_D = 1.2k\Omega$ $C_1 = 0.01\mu F$ $C_2 = 2\mu F$
 $I_{DSS} = 12mA$ $V_p = -4V$ ise Çalışma noktasını bulunuz

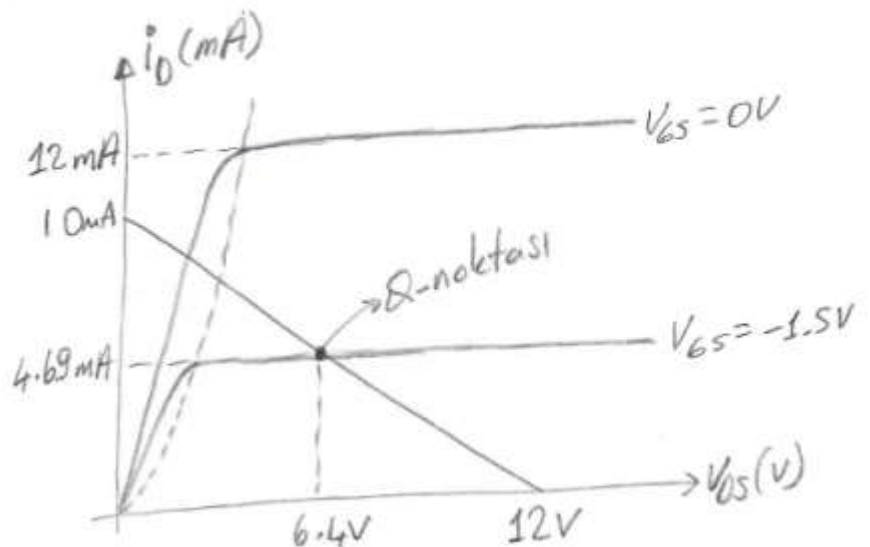
$$V_{GS} = -V_{GG} = -1.5V$$

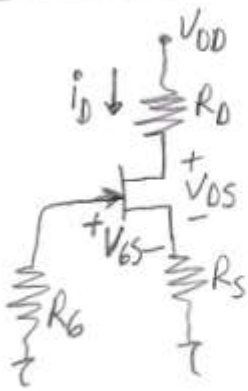
$$I_{DQ} = I_{DSS} \left(1 - \frac{V_{GS}}{V_p}\right)^2$$

$$= 12mA \cdot \left(1 - \frac{-1.5}{-4}\right)^2$$

$$= 4.69mA$$

$$V_{DSQ} = V_{DD} - R_D I_{DQ} = 6.4V$$



Kendinden Öngerilimli JFET

$$i_G = 0, V_G = 0, V_S = R_S i_D$$

$$V_{GS} = V_G - V_S = -R_S i_D$$

$$i_D = I_{OSS} \left(1 - \frac{V_{GS}}{V_P}\right)^2 = I_{OSS} \left(1 + \frac{R_S i_D}{V_P}\right)^2$$

$$V_{DS} = V_{DD} - (R_D + R_S) i_D$$

Dr Yukarıdaki şekli kullanarak soruyu çöz.

$$I_{OSS} = 10 \text{ mA} \quad V_P = -4 \text{ V} \quad R_D = 6.2 \text{ k}\Omega \quad R_S = 1.5 \text{ k}\Omega$$

$$R_G = 1 \text{ M}\Omega \quad V_{DD} = 24 \text{ V} \quad \text{çalışma noktası.}$$

$$V_{GS} = -R_S i_D$$

$$i_D = I_{OSS} \left(1 - \frac{V_{GS}}{V_P}\right)^2 = I_{OSS} \left(1 + \frac{R_S i_D}{V_P}\right)^2 = 10 \left(1 - \frac{1.5 i_D}{4}\right)^2$$

$$2.25 i_D^2 - 13.6 i_D + 16 = 0 \quad \begin{aligned} \rightarrow i_D &= \frac{20}{4.5} \text{ mA} = 4.44 \text{ mA} \\ \rightarrow i_D &= \frac{7.2}{4.5} \text{ mA} = 1.6 \text{ mA} \end{aligned}$$

$$V_{DS} = V_{DD} - (R_D + R_S) \cdot i_D$$

$$i_D = \frac{20}{4.5} \text{ mA} \text{ için } V_{DS} = 24 - (6.2 + 1.5) \times \frac{20}{4.5} = -10.22 \text{ V} \quad \times$$

$$i_D = 1.6 \text{ mA} \text{ için } V_{DS} = 24 - (6.2 + 1.5) \times 1.6 = 11.68 \text{ V} \quad \checkmark$$

$$i_{DQ} = 1.6 \text{ mA} \text{ ve } V_{DSQ} = 11.68 \text{ V} \text{ ve } V_{GSQ} = -2.4 \text{ V}$$

Dr $V_{DD} = 10 \text{ V}$, $R_D = 4 \text{ k}\Omega$, $R_S = 2 \text{ k}\Omega$, $I_{OSS} = 9 \text{ mA}$, $V_P = -3 \text{ V}$ olsa
idi çalışma noktası

$$V_{GS} = -R_S i_D = -2 i_D$$

$$i_D = I_{OSS} \left(1 - \frac{V_{GS}}{V_P}\right)^2$$

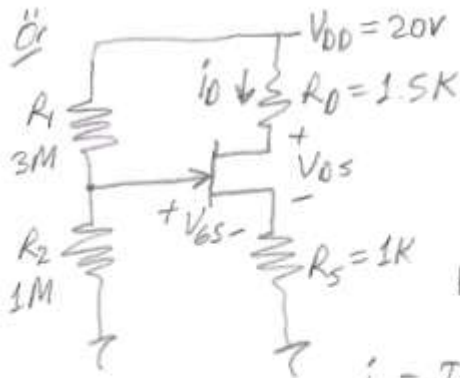
$$= 9 \left(1 - \frac{-2 i_D}{-3}\right)^2 = (3 - 2 i_D)^2$$

$$4 i_D^2 - 13 i_D + 9 = 0 \quad \begin{aligned} \rightarrow i_D &= 1 \text{ mA} \\ \rightarrow i_D &= 2.25 \text{ mA} \end{aligned}$$

$$i_D = 1 \text{ mA} \text{ için } V_{GS} = -2 i_D = -2 \text{ V} < -3 \text{ V} \quad \checkmark$$

$$V_{DS} > V_{GS} - V_P = 1 \text{ V}$$

$$V_{DS} = 10 - (4 + 2) \times 1 = 4 \text{ V} > 1 \text{ V} \quad \checkmark$$



$V_p = -5V$, $I_{DSS} = 8mA$ ise çalışma noktası?

$$V_G = \frac{R_2 V_{DD}}{R_1 + R_2} = \frac{1M \times 20V}{3M + 1M} = 5V$$

$$V_{GS} = V_G - V_S = V_G - R_S I_D = 5 - I_D$$

$$I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_p}\right)^2 = 8 \left(1 - \frac{5 - I_D}{-5}\right)^2 = 8 \left(\frac{I_D - 10}{5}\right)^2$$

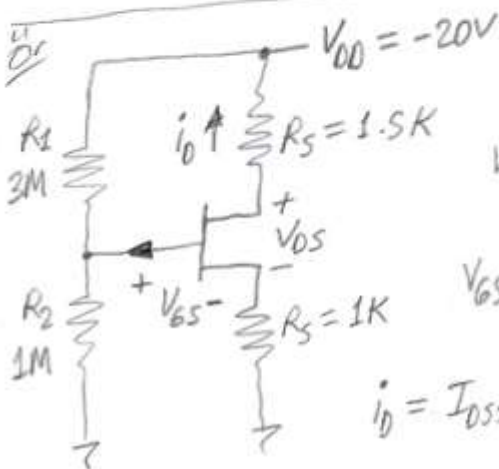
$$I_D^2 - 23.125 I_D + 100 = 0 \rightarrow I_D = 17.37 mA \quad X$$

$$I_D = 5.76 mA$$

$$I_{DQ} = 5.76 mA \text{ için } V_{GSQ} = 5 - I_{DQ} = -0.76V \quad (V_p < V_{GS} \leq 0) \quad \checkmark$$

$$V_{DSQ} \geq V_{GSQ} - V_p = -0.76V - (-5V) = 4.24V$$

$$V_{DSQ} = V_{DD} - (R_D + R_S) I_{DQ} = 20V - (1.5K + 1K) \times 5.76mA = 5.6V > 4.24V \quad \checkmark$$



$V_p = 5V$, $I_{DSS} = 8mA$ ise çalışma noktası?

$$V_G = \frac{R_2 V_{DD}}{R_1 + R_2} = \frac{1M \times (-20V)}{3M + 1M} = -5V$$

$$V_{GS} = V_G - V_S = V_G + R_S I_D = I_D - 5$$

$$I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_p}\right)^2 = 8 \left(1 - \frac{I_D - 5}{5}\right)^2 = 8 \left(\frac{I_D - 10}{5}\right)^2$$

$$I_D^2 - 23.125 I_D + 100 = 0 \rightarrow I_D = 17.37 mA \quad X$$

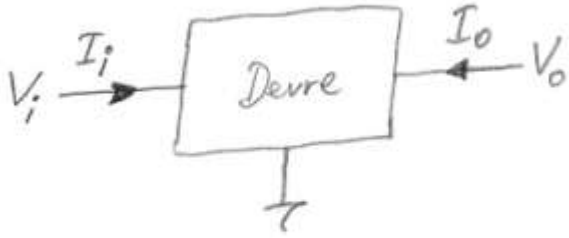
$$I_D = 5.76 mA$$

$$I_{DQ} = 5.76 mA \text{ için } V_{GSQ} = I_{DQ} - 5 = 0.76V \quad (0 \leq V_{GS} < V_p) \quad \checkmark$$

$$V_{DSQ} < V_{GSQ} - V_p = 0.76V - 5V = -4.24V$$

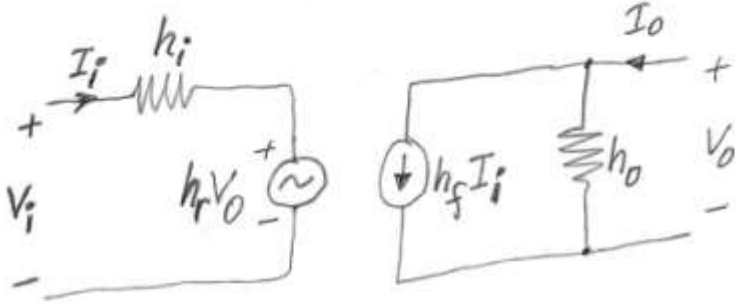
$$V_{DSQ} = V_{DD} + (R_S + R_D) I_{DQ}$$

$$= -20V + (1.5K + 1K) \times 5.76mA = -5.6V < -4.24V \quad \checkmark$$

Karma Eşdeğer Devre

$$V_i = h_{11} I_i + h_{12} V_o$$

$$I_o = h_{21} I_i + h_{22} V_o$$



Tam karma eşdeğer devre

$$h_{11} = \left. \frac{V_i}{I_i} \right|_{V_o=0} \quad (\Omega) \text{ ohm}$$

$h_{11} (h_i)$: Giriş direnci (input)

$h_{12} (h_r)$: Ters transfer gerilim oranı (reverse)

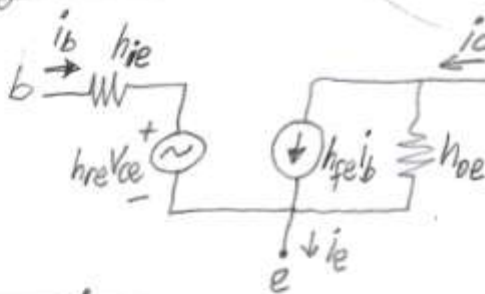
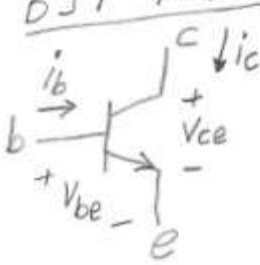
$$h_{12} = \left. \frac{V_i}{V_o} \right|_{I_i=0} \quad (\text{birimsiz})$$

$h_{21} (h_f)$: İleri transfer akım oranı (forward)

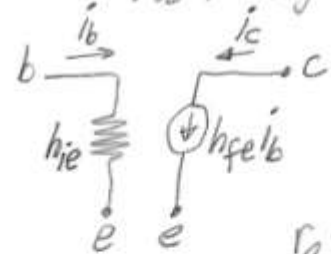
$$h_{21} = \left. \frac{I_o}{I_i} \right|_{V_o=0} \quad (\text{birimsiz})$$

$h_{22} (h_o)$: Çıkış iletkenliği (output)

$$h_{22} = \left. \frac{I_o}{V_o} \right|_{I_i=0} \quad (\text{mho}) \text{ siemens}$$

BJT Küçük Sinyal Analizi

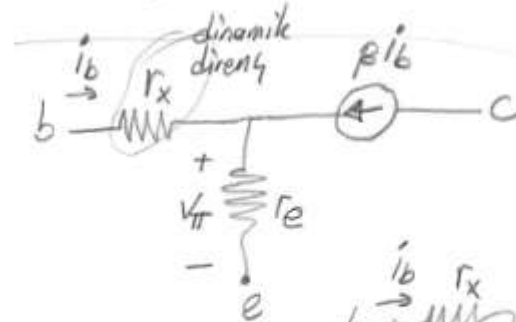
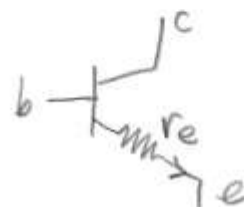
h_{re} çok küçük ve h_{oe} çok büyük ise



$$h_{fe} = \beta$$

$$r_e = \frac{26 \text{ mV}}{I_{EQ}}$$

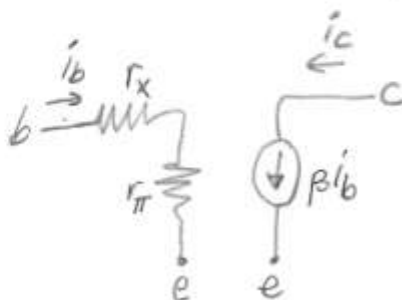
$$h_{ie} = (\beta + 1) r_e = r_{ac} = \frac{26 \text{ mV}}{I_{BQ}}$$

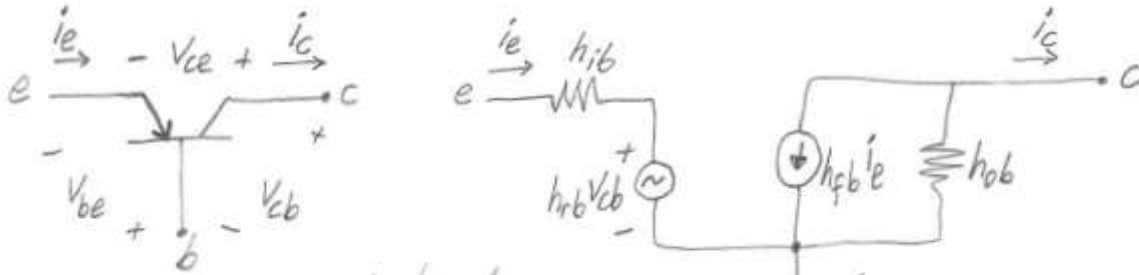


$$V_{\pi} = r_e I_e$$

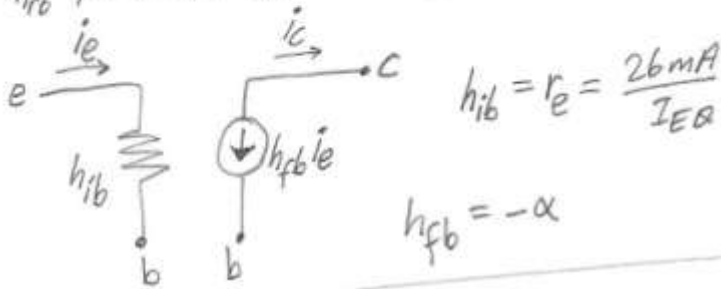
$$= (\beta + 1) r_e I_b$$

$$r_{\pi}$$



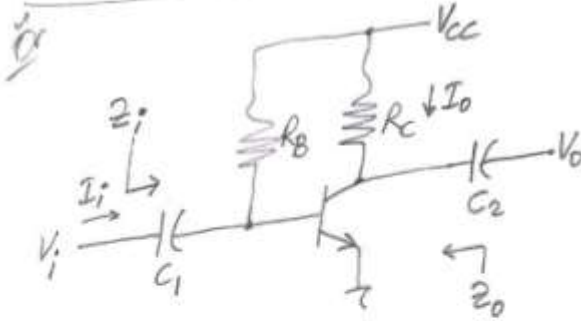


h_{rb} çok küçük, h_{ob} çok büyük ise



$$h_{ib} = r_e = \frac{26 \text{ mV}}{I_{EQ}}$$

$$h_{fb} = -\alpha$$



$$C_1 = C_2 = 0.1 \mu\text{F}$$

$$R_B = 560 \text{ K} \quad R_C = 3 \text{ k}\Omega$$

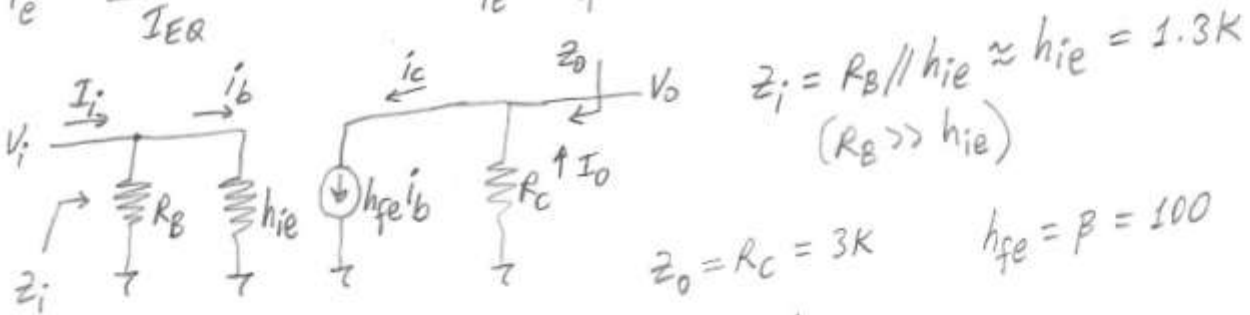
$$\beta = 100, V_{CC} = 12 \text{ V} \text{ ise}$$

Z_i, Z_o, A_v, A_o değerlerini bulunuz.

ortak emittörlü sabit öngerilimli düzenlemesi

$$I_{BQ} = \frac{V_{CC} - V_{BE}}{R_B} = \frac{12 \text{ V} - 0.7 \text{ V}}{560 \text{ K}} \approx 20 \mu\text{A} \quad I_{CQ} \approx I_{EQ} = \beta I_{BQ} = 100 \times 20 \mu\text{A} = 2 \text{ mA}$$

$$r_e = \frac{26 \text{ mV}}{I_{EQ}} = 13 \Omega \quad h_{ie} = (\beta + 1) \cdot r_e \approx 1300$$



$$Z_i = R_B // h_{ie} \approx h_{ie} = 1.3 \text{ K} \quad (R_B \gg h_{ie})$$

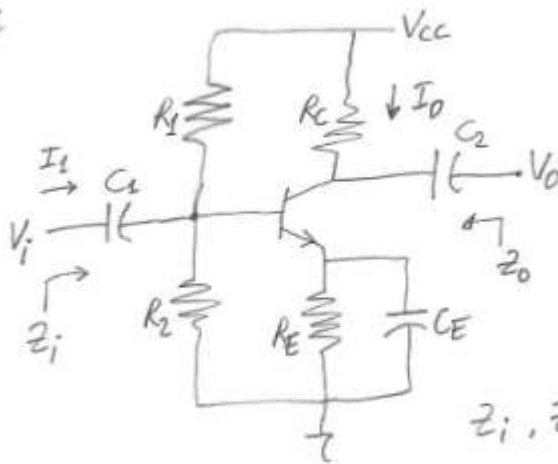
$$Z_o = R_C = 3 \text{ K} \quad h_{fe} = \beta = 100$$

$$V_o = -R_C I_o = -R_C i_c = -R_C h_{fe} i_b = -R_C h_{fe} \frac{V_i}{h_{ie}}$$

$$A_v = \frac{V_o}{V_i} = -R_C \frac{h_{fe}}{h_{ie}} = -3 \text{ K} \cdot \frac{100}{1.3 \text{ K}} = -230.77$$

$$A_i = \frac{I_o}{I_i} = \frac{i_c}{i_b} = h_{fe} = 100$$

ör

Gerilim Bölücü ile İmpedanslar

$$C_1 = C_2 = 1 \mu F \quad C_E = 0.1 \mu F$$

$$R_1 = 56 K \quad R_2 = 5.6 K \quad \beta = 90$$

$$R_C = 10 K \quad R_E = 1.5 K \quad V_{CC} = 22 V$$

 z_i, z_o, A_i, A_o değerleri?

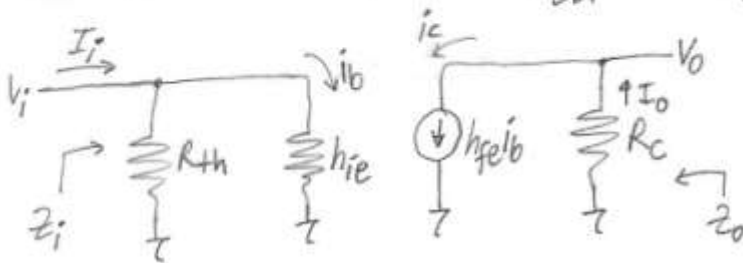
$$V_{th} = \frac{R_2 V_{CC}}{R_1 + R_2} = \frac{5.6 K \times 22 V}{56 K + 5.6 K} = 2 V \quad R_{th} = R_1 \parallel R_2 = \frac{R_1 R_2}{R_1 + R_2} = 5.09 K$$

$$I_{BQ} = \frac{V_{th} - V_{BE}}{R_{th} + (\beta + 1) R_E} = \frac{2 V - 0.7 V}{5.09 K + 91 \times 1.5 K} = 9.18 \mu A$$

$$h_{fe} = \beta = 90$$

$$I_{CQ} = \beta I_{BQ} = 90 \times 9.18 \mu A = 0.826 mA \approx I_{EQ}$$

$$h_{ie} = (\beta + 1) r_e = (\beta + 1) \cdot \frac{26 mV}{I_{EQ}} = \frac{26 mV}{I_{BQ}} = \frac{26 mV}{9.18 \mu A} = 2.835 K$$



$$z_i = R_{th} \parallel h_{ie} = 5.09 K \parallel 2.835 K = 1.821 K$$

$$z_o = R_C = 10 K$$

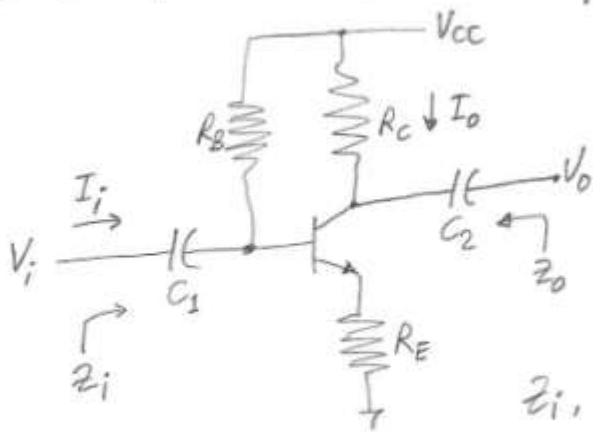
$$V_o = -R_C I_o = -R_C h_{fe} i_b = -R_C h_{fe} \frac{V_i}{h_{ie}}$$

$$A_v = \frac{V_o}{V_i} = -R_C \frac{h_{fe}}{h_{ie}} = -10 K \frac{90}{2.835 K} = -317.5$$

$$A_i = \frac{I_o}{I_i} = \frac{h_{fe} i_b}{V_i / z_i} = \frac{z_i h_{fe} i_b}{V_i} = \frac{(R_{th} \parallel h_{ie}) \cdot h_{fe} i_b}{h_{ie} i_b} = \frac{R_{th} h_{fe}}{R_{th} + h_{ie}}$$

$$= \frac{5.09 \times 90}{5.09 + 2.835} = 57.8$$

Ör CE Köprülenmemiş emittör önperilimli düzenleme



$$C_1 = C_2 = 0.1 \mu F$$

$$V_{CC} = 20V \quad \beta = 120 \quad V_T = 0.7V$$

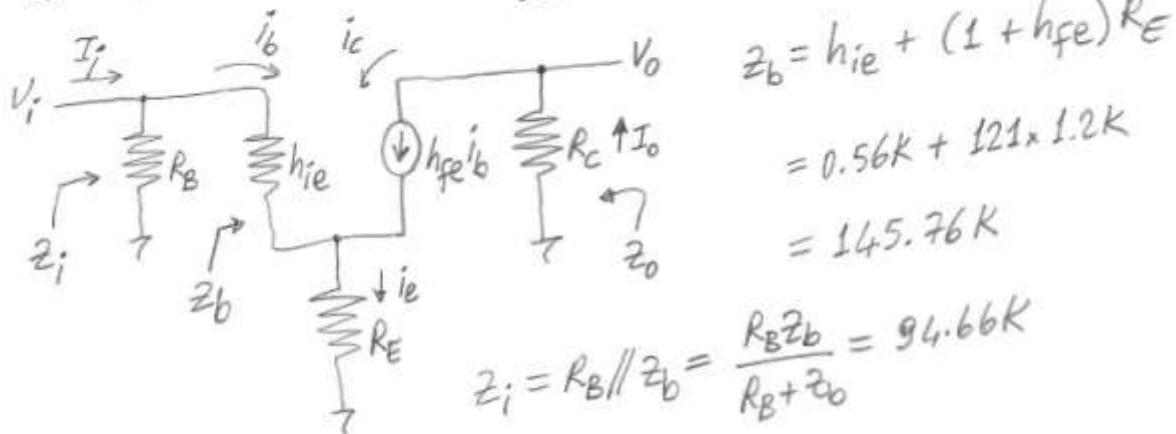
$$R_B = 270K \quad R_C = 5.6K \quad R_E = 1.2K$$

z_i, z_o, A_v, A_i değerlerini bulunuz.

$$I_{BQ} = \frac{V_{CC} - V_{BE}}{R_B + (\beta + 1)R_E} = \frac{20V - 0.7V}{270K + 121 \times 1.2K} = \frac{19.3V}{415.2K} = 46.48 \mu A$$

$$I_{EQ} = (\beta + 1)I_{BQ} = 5.624 \approx I_{CQ}$$

$$h_{ie} = (\beta + 1)r_e = (\beta + 1) \frac{26mV}{I_{EQ}} = \frac{26mV}{I_{BQ}} = 0.56K$$



$$z_b = h_{ie} + (1 + h_{fe})R_E$$

$$= 0.56K + 121 \times 1.2K$$

$$= 145.76K$$

$$z_i = R_B \parallel z_b = \frac{R_B z_b}{R_B + z_b} = 94.66K$$

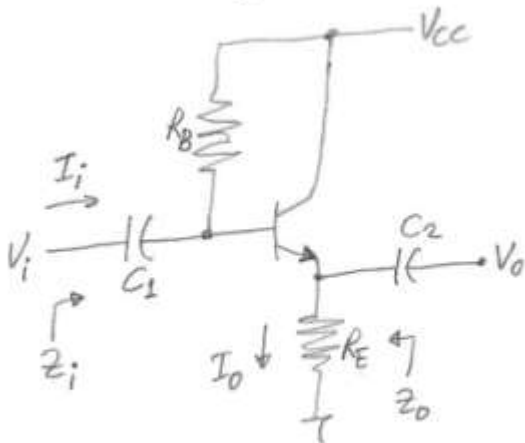
$$z_o = R_C = 5.6K$$

$$V_o = -R_C I_o = -R_C h_{fe} i_b = -R_C h_{fe} \frac{V_i}{z_b}$$

$$A_v = \frac{V_o}{V_i} = -R_C \frac{h_{fe}}{z_b} = -5.6K \times \frac{120}{145.76K} = -4.61$$

$$A_i = \frac{I_o}{I_i} = \frac{V_o / z_o}{V_i / z_i} = \frac{V_o}{V_i} \frac{z_i}{z_o} = A_v \frac{z_i}{z_o} = -4.61 \frac{94.66K}{5.6K} = -77.93$$

Emitör izleyici devresi



$$V_{CC} = 12V \quad V_T = 0.7V \quad \beta = 98$$

$$C_1 = C_2 = 0.1 \mu F$$

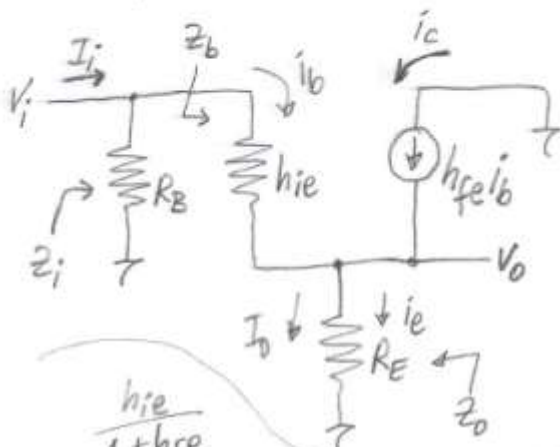
$$R_B = 220K \quad R_E = 3.3K \text{ ise}$$

Z_i, Z_o, A_v, A_i değerlerini bulunuz.

$$I_{BQ} = \frac{V_{CC} - V_T}{R_B + (\beta + 1)R_E} = \frac{12V - 0.7V}{220K + 99 \times 3.3K} = \frac{11.3V}{546.7K} = 20.67 \mu A$$

$$I_{EQ} = (\beta + 1)I_{BQ} = 2.05 \text{ mA} \approx I_{CQ}$$

$$h_{ie} = (\beta + 1)r_e = (\beta + 1) \frac{26 \text{ mV}}{I_{EQ}} = \frac{26 \text{ mV}}{I_{BQ}} \quad h_{fe} = \beta = 98$$



$$Z_b = h_{ie} + (1 + h_{fe})R_E$$

$$= 1.26K + 99 \times 3.3K = 327.96K$$

$$Z_i = R_B \parallel Z_b = \frac{R_B Z_b}{R_B + Z_b} = 131.67K$$

Z_o 'ı bulmak için V_i sıfır yapılırsa

$$Z_o = R_E \parallel \frac{h_{ie}}{1 + h_{fe}} = (3.3K) \parallel (12.7\Omega) \approx 12.7\Omega$$

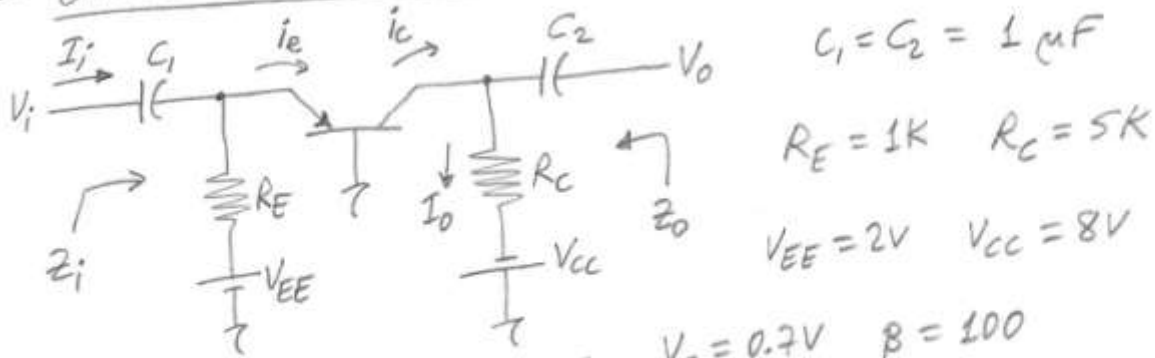
$$V_o = \frac{R_E V_i}{R_E + h_{ie}/(1 + h_{fe})} \rightarrow A_v = \frac{V_o}{V_i} = \frac{R_E}{R_E + h_{ie}/(1 + h_{fe})} \approx \frac{3.3K}{3.3K + 12.7\Omega} \approx 1$$

$$V_i = R_B(I_i - i_b) = Z_b i_b \rightarrow i_b = \frac{R_B I_i}{R_B + Z_b}$$

$$I_o = i_e = (1 + h_{fe})i_b = \frac{R_B(1 + h_{fe})I_i}{R_B + Z_b}$$

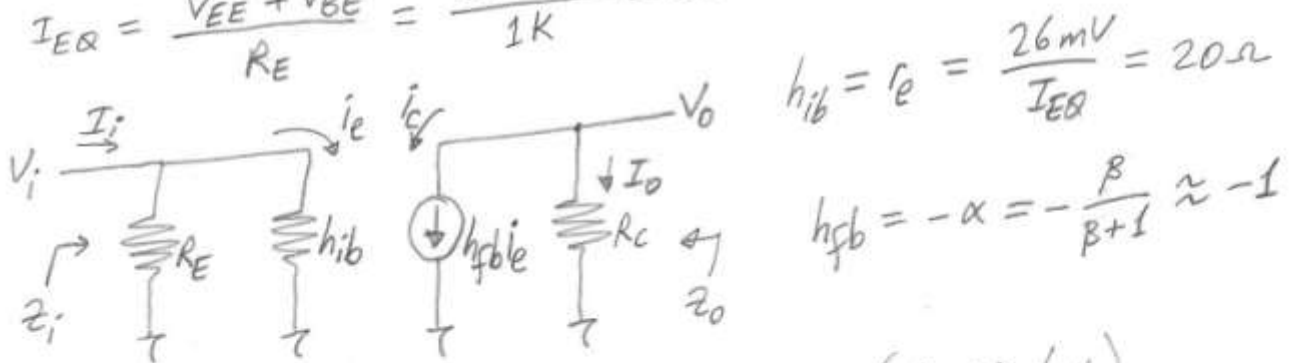
$$A_i = \frac{I_o}{I_i} = \frac{R_B(1 + h_{fe})}{R_B + Z_b} = \frac{220K \times 99}{220K + 327.96K} \approx 39.75$$

Ör Ortak Bazlı Düzenleme



z_i, z_o, A_v, A_i değerleri?

$$I_{EQ} = \frac{V_{EE} + V_{BE}}{R_E} = \frac{2V - 0.7V}{1K} = 1.3 \text{ mA}$$



$$z_i = R_E \parallel h_{ib} = (1K) \parallel (20 \Omega) = 19.6 \Omega \quad (R_E \gg h_{ib})$$

$$z_o = R_C = 5K$$

$$V_o = R_C I_o = -R_C i_c = -R_C h_{fb} i_e = -R_C h_{fb} \frac{V_i}{h_{ib}}$$

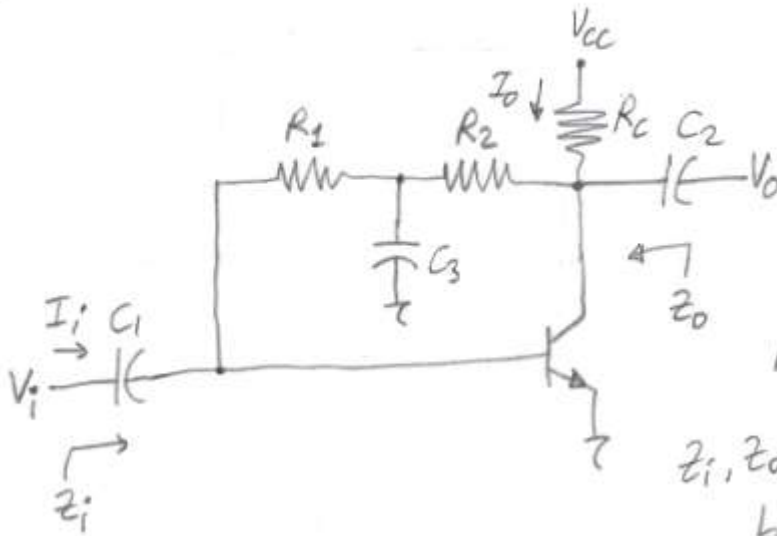
$$A_v = \frac{V_o}{V_i} = -R_C \frac{h_{fb}}{h_{ib}} = -5K \frac{-1}{20 \Omega} = 250$$

$R_E \gg h_{ib}$ olduğundan $I_i \approx i_e$ olur.

$$I_o = +i_c = -h_{fb} i_e \approx -h_{fb} I_i$$

$$A_i = \frac{I_o}{I_i} = -h_{fb} = 1$$

Ör Kollectör DC peribesleme ve fark yükseltici



$$V_{cc} = 12V \quad V_T = 0.7V$$

$$R_1 = 120K \quad R_2 = 68K$$

$$C_1 = C_2 = 0.1 \mu F$$

$$C_3 = 0.01 \mu F$$

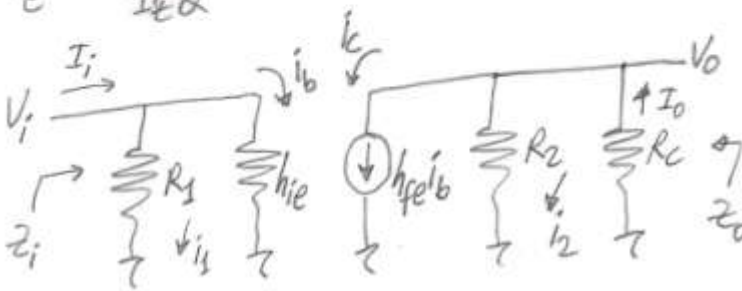
$$R_c = 3K \quad \beta = 140$$

z_i, z_o, A_v, A_i degerlerini bulunuz.

$$I_{BQ} = \frac{V_{cc} - V_{BE}}{R_1 + R_2 + (\beta + 1)R_c} = \frac{12V - 0.7V}{120K + 68K + 141 \times 3K} = \frac{11.3V}{611K} = 18.5 \mu A$$

$$I_{EQ} = (\beta + 1)I_{BQ} = 2.6 \text{ mA} \approx I_{CQ}$$

$$r_e = \frac{26 \text{ mV}}{I_{EQ}} = 10 \Omega \quad h_{ie} = (\beta + 1)r_e = 1.41K \quad h_{fe} = \beta = 140$$



$$z_o = R_c \parallel R_2 = (3K) \parallel (68K) \approx 2.87K$$

$$z_i = R_1 \parallel h_{ie} = (120K) \parallel (1.41K) \approx 1.38K$$

$$V_o = -R_c I_o = -R_c (i_c + i_2) = -R_c (h_{fe} i_b + \frac{V_o}{R_2})$$

$$= -R_c h_{fe} i_b - \frac{R_c}{R_2} V_o = -R_c h_{fe} \frac{V_i}{h_{ie}} - \frac{R_c}{R_2} V_o$$

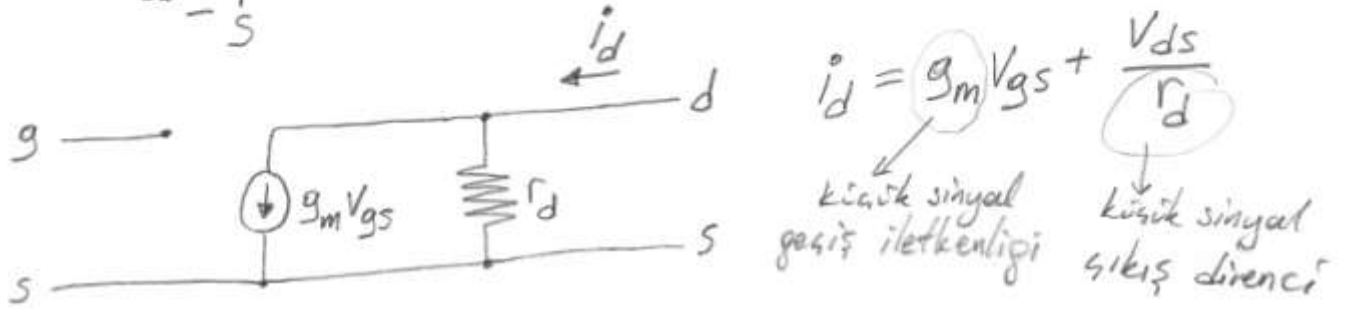
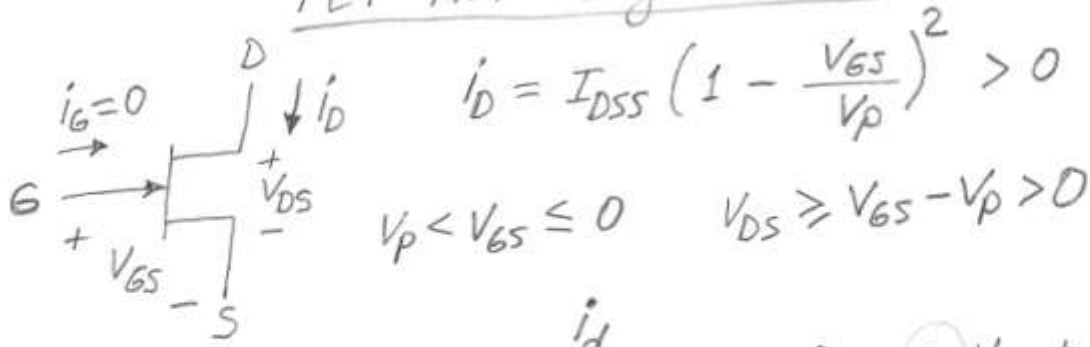
$$A_v = \frac{V_o}{V_i} = \frac{-R_c h_{fe}}{h_{ie}} \frac{R_2}{R_2 + R_c} = \frac{-3K \times 140}{1.41K} \cdot \frac{68K}{68K + 3K} = -285.29$$

$$V_i = R_1 i_1 = h_{ie} i_b \rightarrow i_1 = \frac{h_{ie}}{R_1} i_b \rightarrow I_i = i_1 + i_b = (1 + \frac{h_{ie}}{R_1}) i_b$$

$$V_o = R_2 i_2 = -R_c I_o \rightarrow i_2 = -\frac{R_c}{R_2} I_o \rightarrow I_o = i_c + i_2 = h_{fe} i_b - \frac{R_c}{R_2} I_o \rightarrow I_o = \frac{R_2 h_{fe} i_b}{R_2 + R_c}$$

$$A_i = \frac{I_o}{I_i} = \frac{R_1 R_2 h_{fe}}{(R_1 + h_{ie})(R_2 + R_c)} = \frac{120K \times 68K \times 140}{(120K + 1.41K)(68K + 3K)} \approx 132.54$$

FET Küçük Sinyal Analizi



$$g_m = \left. \frac{\partial I_D}{\partial V_{GS}} \right|_Q = g_{m0} \left(1 - \frac{V_{GS}}{V_P}\right)$$

$$r_d = \frac{1}{y_{os}} \rightarrow \text{kiçik sinyal çıkış iletkenliği}$$

$$y_{os} = \left. \frac{\partial I_D}{\partial V_{DS}} \right|_Q \quad g_{m0} = \frac{2 I_{DSS}}{|V_P|}$$

$$r_d = r_{ds} \text{ (10K ile 100K arası)}$$

$V_{GS} = 0$ ise $g_m = g_{m0}$ olur.

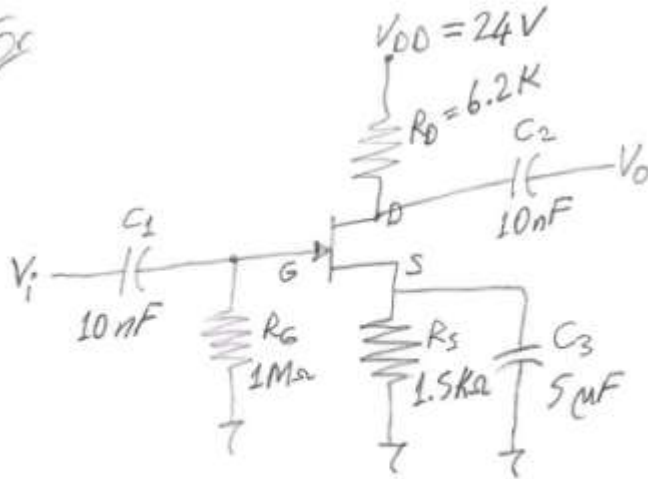
Fet elemanları çok yüksek giriş direncinde gerilim kazancı sağlayan küçük sinyal yükselteçlerinin kurulması için kullanılır. Hem JFET hem de kanal ayarlanabilir MOSFET, aynı gerilim kazancını sağlayan benzer dc öngerilim koşullarında çalışabilir. Bununla beraber MOSFET transistörleri çok daha yüksek giriş empedansı sağlar.

En iyi gerilim kazancı sağlamak için, ortak kaynak yükselteci düzenlemesi sağlar. Kapıya bir giriş sinyali uygulanır. Çıkış sinyali kanaldan alınır ve kaynak ucu referans ve ortak uc olarak kullanılır.

Ör $I_{DSS} = 12 \text{ mA}$, $V_P = -3 \text{ V}$, $V_{GS} = -1 \text{ V}$ ise $g_m = ?$

$$g_{m0} = \frac{2 I_{DSS}}{|V_P|} = \frac{2 \times 12 \text{ mA}}{3 \text{ V}} = 8 \text{ mS} \quad g_m = g_{m0} \left(1 - \frac{V_{GS}}{V_P}\right) = 8 \text{ mS} \left(1 - \frac{-1}{-3}\right) = \frac{16}{3} \text{ mS}$$

Ex



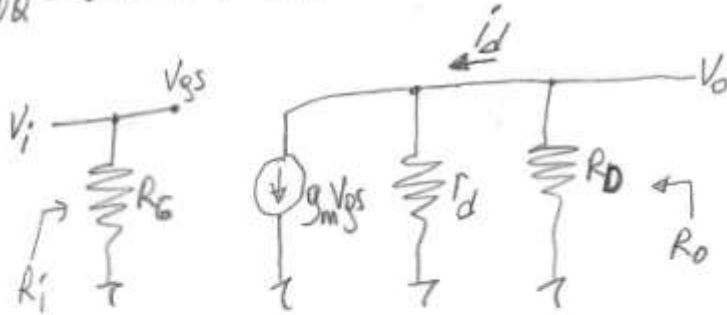
$$I_{DSS} = 10 \text{ mA}, V_p = -4 \text{ V}$$

$$r_d = 50 \text{ K}$$

transistörün çalışma noktasını ve R_i, R_o, A_v değerlerini bulunuz.

Daha önce bulduk.

$$i_{DQ} = 1.6 \text{ mA}, V_{DSQ} = 11.68 \text{ V}, V_{GSQ} = -2.4 \text{ V}$$



$$R_o = R_D // r_d = \frac{6.2 \text{ K} \times 50 \text{ K}}{6.2 \text{ K} + 50 \text{ K}} = 5.52 \text{ K}\Omega$$

$$R_i = R_G = 1 \text{ M}\Omega$$

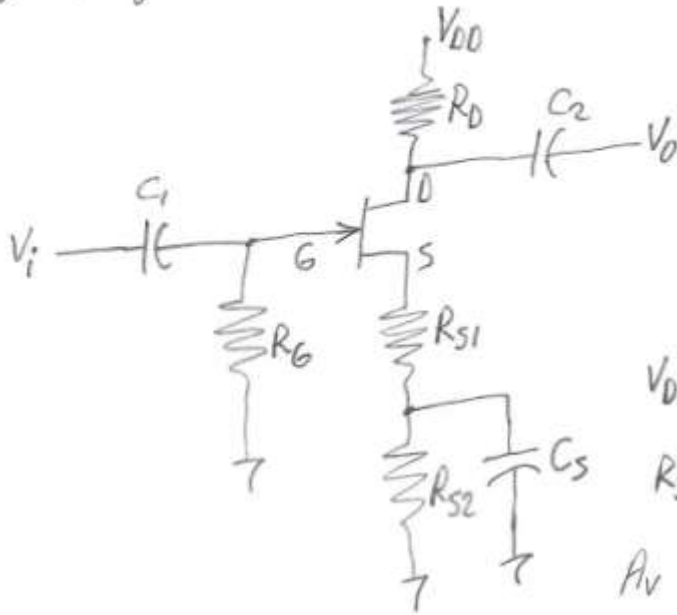
$$g_{m0} = \frac{2I_{DSS}}{|V_p|} = \frac{2 \times 10 \text{ mA}}{4 \text{ V}} = 5 \text{ mS}$$

$$g_m = g_{m0} \left(1 - \frac{V_{GSQ}}{V_p} \right) = 5 \text{ mS} \times \left(1 - \frac{-2.4 \text{ V}}{-4} \right) = 2 \text{ mS}$$

$$V_{GS} = V_i, \quad i_d = g_m V_{GS} + \frac{V_o}{r_d} = 2V_i + \frac{V_o}{50}$$

$$V_o = -R_D i_d = -12.4 V_i - 0.124 V_o \Rightarrow A_v = \frac{V_o}{V_i} = -11.03$$

Dr Kaynak Dirençli Yükselteç



$$V_P = -6V$$

$$I_{DSS} = 10 \text{ mA}, r_d = 50K$$

$$C_1 = C_2 = 0.05 \mu F$$

$$C_S = 5 \mu F$$

$$V_{DD} = 24V, R_D = 4.3K$$

$$R_{S1} = 0.25K, R_{S2} = 1.75K$$

A_v değerini bulunuz.

$$R_S = R_{S1} + R_{S2} = 2K$$

$$V_{GS} = -R_S i_D$$

$$i_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P}\right)^2 = I_{DSS} \left(1 + \frac{R_S i_D}{V_P}\right)^2 = 10 \left(1 + \frac{2i_D}{-6}\right)^2$$

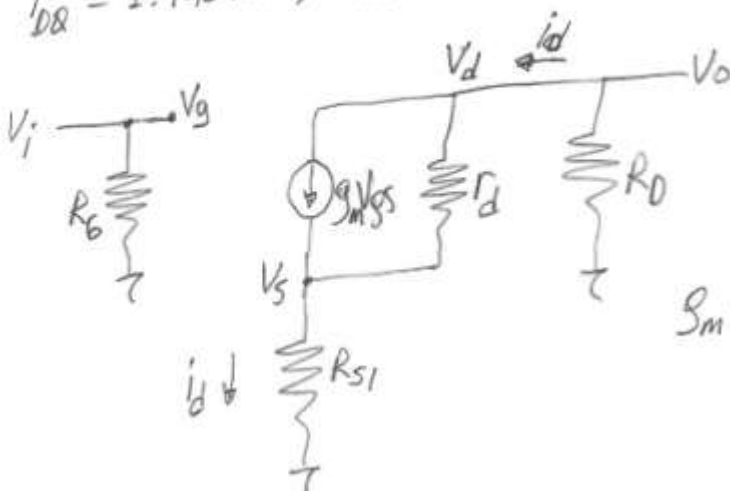
$$i_D^2 - 6.9i_D + 9 = 0 \rightarrow \begin{cases} i_D = 5.155 \text{ mA} \\ i_D = 1.745 \text{ mA} \end{cases}$$

$$V_{DS} = V_{DD} - (R_D + R_S) i_D$$

$$i_D = 5.155 \text{ mA} \rightarrow V_{DS} = 24 - (4.3 + 2) \times 5.155 = -8.48V \quad \times$$

$$i_D = 1.745 \text{ mA} \rightarrow V_{DS} = 24 - (4.3 + 2) \times 1.745 = 13V \quad \checkmark$$

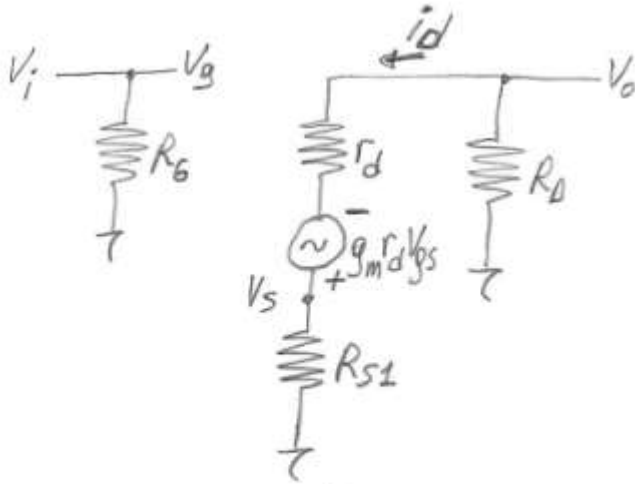
$$i_{DQ} = 1.745 \text{ mA}, V_{DSQ} = 13V, V_{GSQ} = -3.49V$$



$$g_{m0} = \frac{2I_{DSS}}{|V_P|} = \frac{2 \times 10 \text{ mA}}{6V} = \frac{10}{3} \text{ mS}$$

$$g_m = g_{m0} \left(1 - \frac{V_{GS}}{V_P}\right) ?$$

$$= \frac{10}{3} \left(1 - \frac{-3.49}{-6}\right) = 5.27 \text{ mS}$$

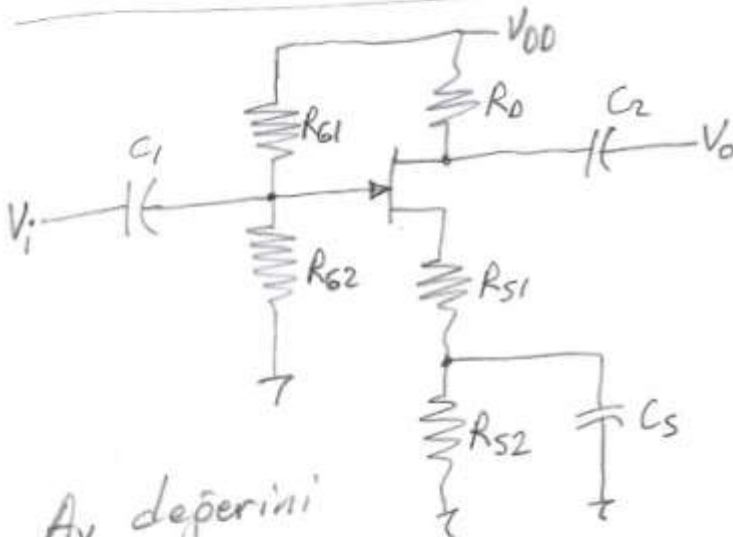


$$\begin{aligned}
 V_{gs} &= V_g - V_s = V_i - V_s \\
 &= V_i - R_{S1} i_o = V_i - R_{S1} \left(-\frac{V_o}{R_D} \right) \\
 &= V_i + \frac{R_{S1}}{R_D} V_o
 \end{aligned}$$

$$V_o = - \frac{R_D}{r_d + R_{S1} + R_D} g_m r_d V_{gs} = - \frac{R_D}{r_d + R_{S1} + R_D} g_m r_d \left(V_i + \frac{R_{S1}}{R_D} V_o \right)$$

$$A_v = \frac{V_o}{V_i} = \frac{-g_m R_D}{1 + g_m R_{S1} + \frac{R_D + R_{S1}}{r_d}}$$

$$= \frac{-5.27 \times 4.3}{1 + 5.27 \times 0.25 + \frac{4.3 + 0.25}{50}} = \frac{-22.661}{2.4085} = -9.41$$



$$R_{G1} = 3M \quad R_{G2} = 1M$$

$$R_D = 1.5K \quad R_{S1} = 0.25K$$

$$R_{S2} = 0.75K$$

$$C_1 = C_2 = 0.05 \mu F$$

$$C_S = 5 \mu F$$

$$V_{DD} = 20V \quad I_{DSS} = 8mA$$

$$V_P = -5V \quad r_d = 50K$$

A_v değerini bulunuz.

Daha önce bulmuştuk.

$$i_{DQ} = 5.76 mA$$

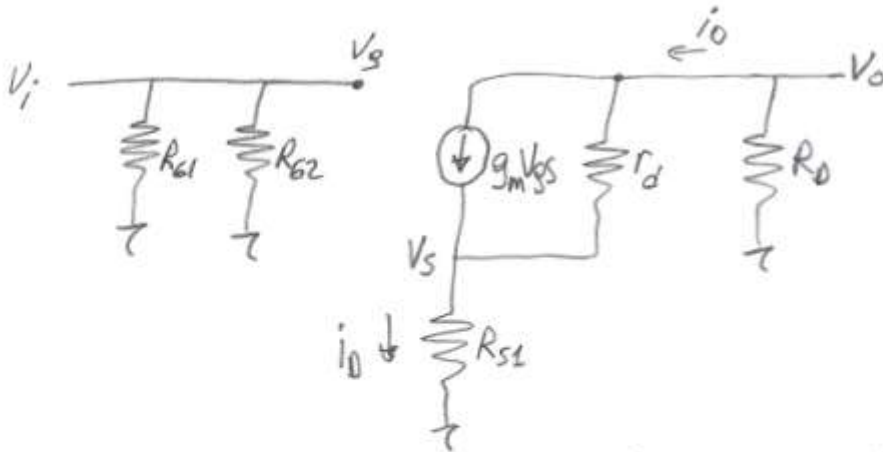
$$V_{GS} = -0.76V$$

$$V_{DSQ} = 5.6V$$

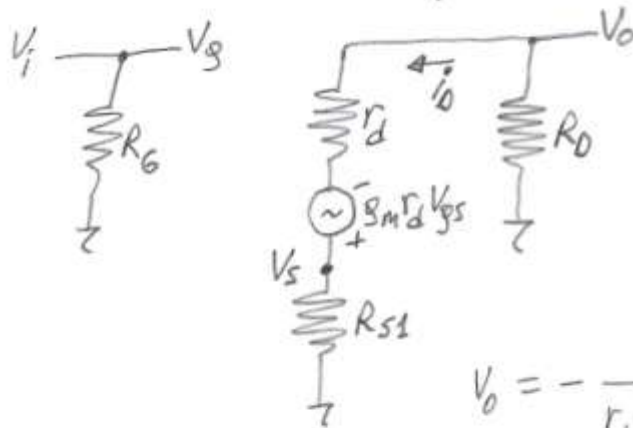
$$R_S = R_{S1} + R_{S2} = 1K$$

$$g_{m0} = \frac{2I_{DSS}}{|V_P|} = \frac{2 \times 8mA}{5V} = 3.2 mS$$

$$g_m = g_{m0} \left(1 - \frac{V_{GS}}{V_P} \right) = 3.2 mS \cdot \left(1 - \frac{-0.76}{-5} \right) = 2.71 mS$$



$$R_G = R_{G1} \parallel R_{G2}$$



$$\begin{aligned} V_{GS} &= V_G - V_S = V_i - V_S \\ &= V_i - R_{S1} i_o = V_i - R_{S1} \left(-\frac{V_o}{R_o} \right) \\ &= V_i + \frac{R_{S1}}{R_o} V_o \end{aligned}$$

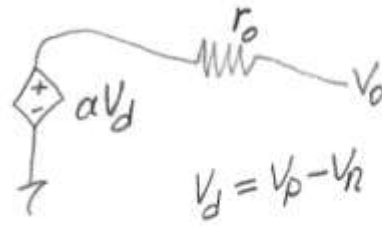
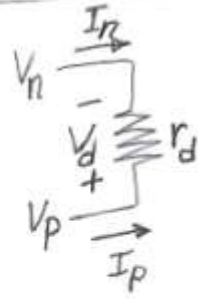
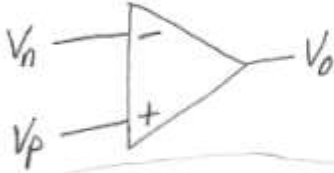
$$V_o = - \frac{R_o}{r_d + R_{S1} + R_o} g_m r_d V_{GS}$$

$$V_o = - \frac{R_o}{r_d + R_{S1} + R_o} g_m r_d \left(V_i + \frac{R_{S1}}{R_o} V_o \right)$$

$$A_v = \frac{V_o}{V_i} = \frac{-g_m R_o}{1 + g_m R_{S1} + \frac{R_o + R_{S1}}{r_d}} = \frac{-2.71 \times 1.5}{1 + 2.71 \times 0.25 + \frac{1.5 + 0.25}{50}} = -2.37$$

İşlemsel Kuvvetlendiriciler - The Operational Amplifier

Opamp



ideal Opamp

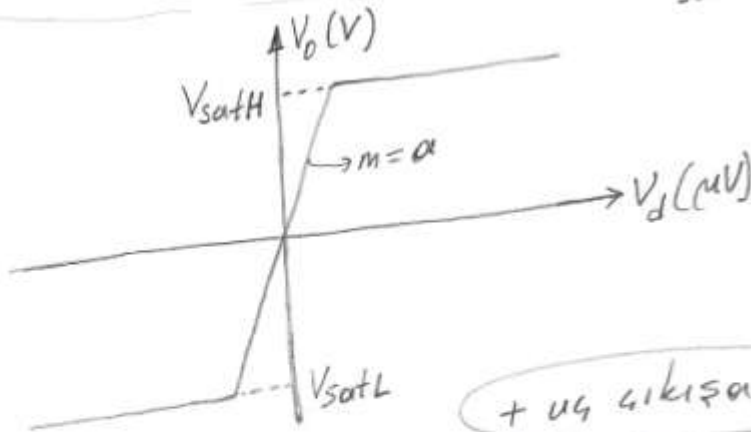
$r_d \rightarrow \infty$, $I_p = I_n = 0$, $r_o = 0$
 $a \rightarrow \infty$ yani $V_d = \frac{V_o}{a} = 0$

Opamp $\pm 15V$ ile beslenir ise

$$V_{satH} \approx 15 - 2 = 13V$$

$$V_{satL} \approx -15 + 2 = -13V$$

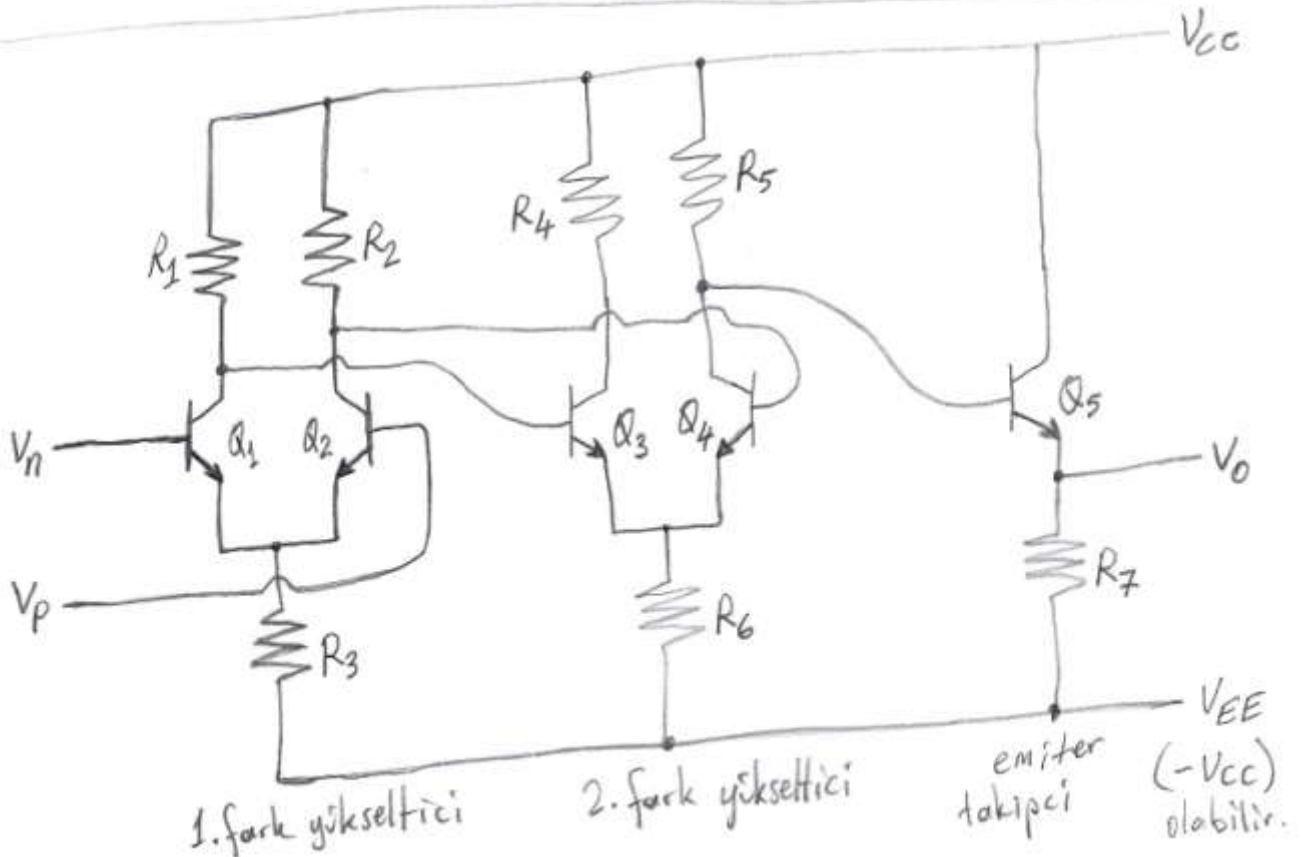
$$a = 200.000$$

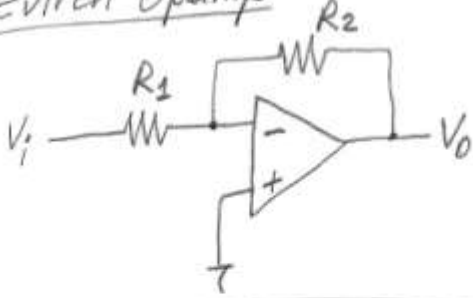


$$\frac{13V}{a} \approx 65 \mu V$$

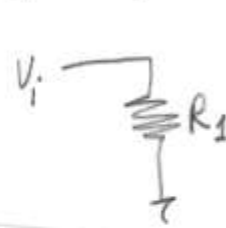
$$-65 \mu V < V_d < +65 \mu V$$

+ u_g çıkışa verilmez → kararsız osilasyon yapar



Eviren Opamp

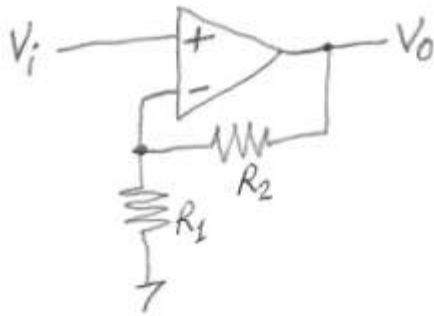
$$\frac{V_i}{R_1} + \frac{V_o}{R_2} = 0 \rightarrow V_o = -\frac{R_2}{R_1} V_i$$



$$R_i = R_1$$

$$R_o = 0$$

$$A = -R_2/R_1$$

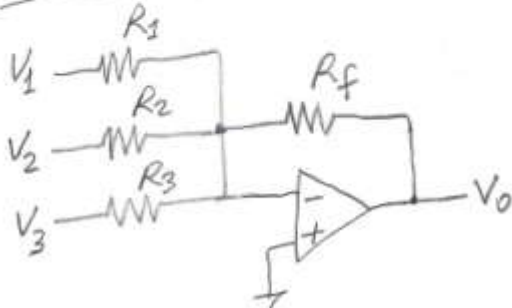
Evirmeyen Opamp

$$\frac{V_i}{R_1} = \frac{V_o}{R_1 + R_2} \rightarrow V_o = \left(1 + \frac{R_2}{R_1}\right) V_i$$

$$A = 1 + \frac{R_2}{R_1}$$

$$R_i = \infty$$

$$R_o = 0$$

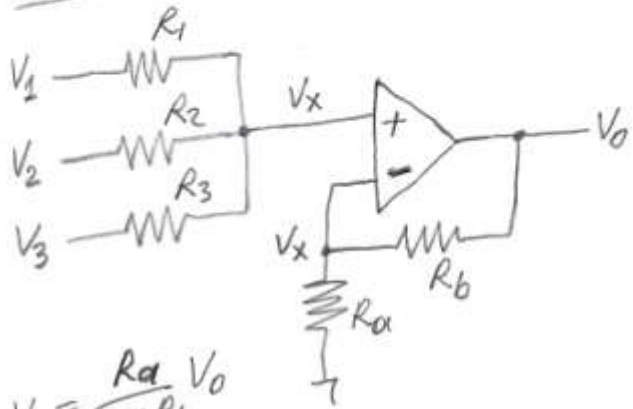
Eviren toplayıcı opamp

$$\frac{V_1}{R_1} + \frac{V_2}{R_2} + \frac{V_3}{R_3} + \frac{V_o}{R_f} = 0$$

$$V_o = -R_f \left(\frac{V_1}{R_1} + \frac{V_2}{R_2} + \frac{V_3}{R_3} \right)$$

$$R_1 = R_2 = R_3 = R \text{ olursa}$$

$$V_o = -\frac{R_f}{R} (V_1 + V_2 + V_3)$$

Evirmeyen toplayıcı opamp

$$V_x = \frac{R_a}{R_a + R_b} V_o$$

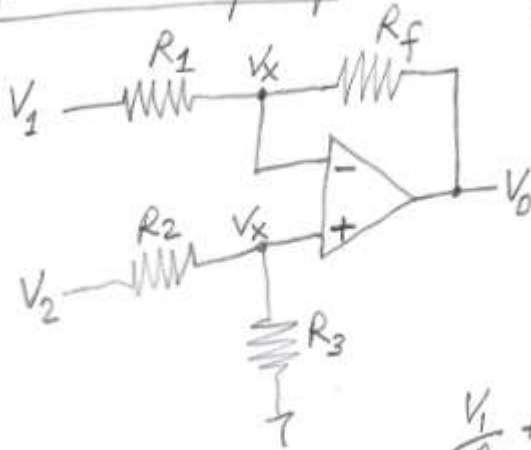
$$\frac{V_1 - V_x}{R_1} + \frac{V_2 - V_x}{R_2} + \frac{V_3 - V_x}{R_3} = 0$$

$$\frac{V_1}{R_1} + \frac{V_2}{R_2} + \frac{V_3}{R_3} = V_x \left(\frac{1}{R_1} + \frac{1}{R_2} + \frac{1}{R_3} \right)$$

$$V_x = \frac{R_1 R_2 R_3}{R_1 R_2 + R_1 R_3 + R_2 R_3} \left(\frac{V_1}{R_1} + \frac{V_2}{R_2} + \frac{V_3}{R_3} \right)$$

$$R_1 = R_2 = R_3 = R \text{ olursa}$$

$$V_o = \frac{1}{3} \left(1 + \frac{R_b}{R_a} \right) \cdot (V_1 + V_2 + V_3)$$

Gıkıkarıcı Opamp

$$R_{i1} = R_1, R_{i2} = R_2 + R_3, R_o = 0$$

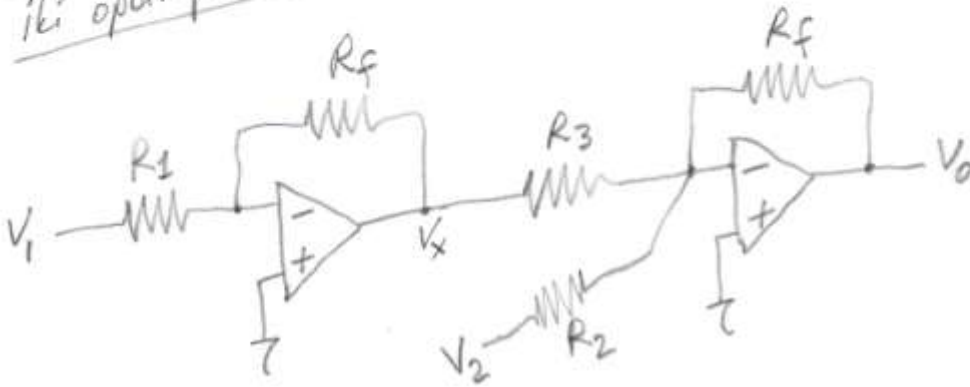
$$V_x = \frac{R_3}{R_2 + R_3} V_2$$

$$\frac{V_1 - V_x}{R_1} + \frac{V_0 - V_x}{R_f} = 0$$

$$\frac{V_1}{R_1} + \frac{V_0}{R_f} = \left(\frac{1}{R_1} + \frac{1}{R_f} \right) V_x$$

$$V_0 = \left(1 + \frac{R_f}{R_1} \right) \frac{R_3}{R_2 + R_3} V_2 - \frac{R_f}{R_1} V_1$$

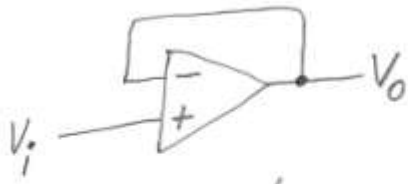
$$\frac{R_f}{R_1} = \frac{R_3}{R_2} = k \text{ alınırsa } V_0 = \frac{R_f}{R_1} (V_2 - V_1)$$

İki opamplı gıkıkarıcı

$$\frac{V_1}{R_1} + \frac{V_x}{R_f} = 0 \rightarrow V_x = -\frac{R_f}{R_1} V_1$$

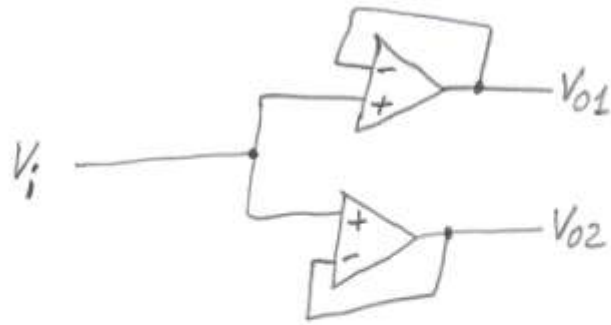
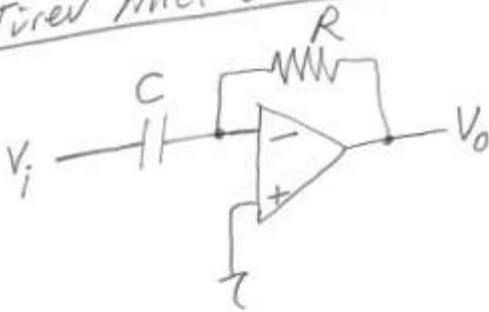
$$\frac{V_x}{R_3} + \frac{V_2}{R_2} + \frac{V_0}{R_f} = 0 \rightarrow V_0 = -\frac{R_f}{R_3} V_x - \frac{R_f}{R_2} V_2$$

$$V_0 = \left(-\frac{R_f}{R_3} \right) \left(-\frac{R_f}{R_1} \right) V_1 + \left(-\frac{R_f}{R_2} \right) V_2 = \frac{R_f^2}{R_1 R_3} V_1 - \frac{R_f}{R_2} V_2$$

Voltaj Takip Edici

$$V_o = V_i \text{ olur.}$$

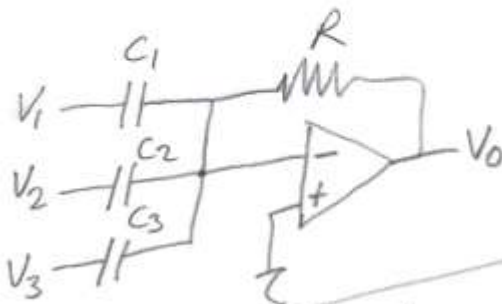
$$A=1, R_i=\infty, R_o=0$$

Türev Alıcı Devre

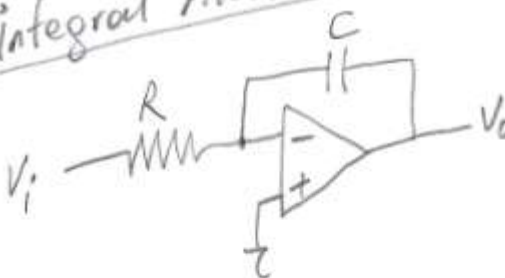
$$C \frac{dV_i}{dt} + \frac{V_o}{R} = 0$$

$$V_o = -RC \frac{dV_i}{dt}$$

$$C_1 \frac{dV_1}{dt} + C_2 \frac{dV_2}{dt} + C_3 \frac{dV_3}{dt} + \frac{V_o}{R} = 0$$

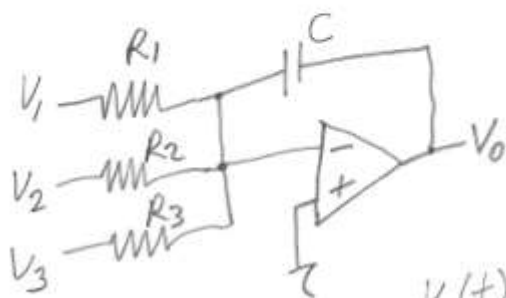


$$V_o = -RC_1 \frac{dV_1}{dt} - RC_2 \frac{dV_2}{dt} - RC_3 \frac{dV_3}{dt}$$

Integral Alıcı Devre

$$\frac{V_i}{R} + C \frac{dV_o}{dt} = 0 \Rightarrow \frac{dV_o}{dt} = -\frac{1}{RC} V_i$$

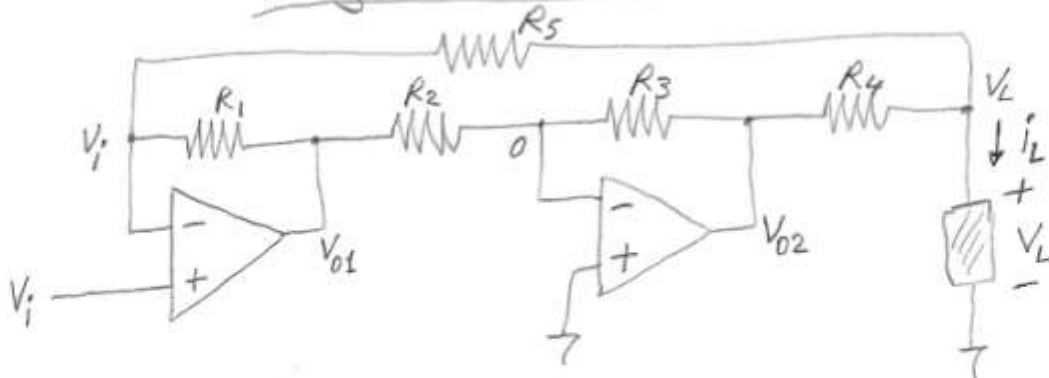
$$V_o(t) = V_o(0) - \frac{1}{RC} \int_0^t V_i(\tau) d\tau$$



$$\frac{V_1}{R_1} + \frac{V_2}{R_2} + \frac{V_3}{R_3} + C \frac{dV_o}{dt} = 0$$

$$\frac{dV_o}{dt} = -\frac{V_1}{R_1 C} - \frac{V_2}{R_2 C} - \frac{V_3}{R_3 C}$$

$$V_o(t) = V_o(0) - \frac{1}{R_1 C} \int_0^t V_1(\tau) d\tau - \frac{1}{R_2 C} \int_0^t V_2(\tau) d\tau - \frac{1}{R_3 C} \int_0^t V_3(\tau) d\tau$$

Voltaj-Akım Dönüştürücü

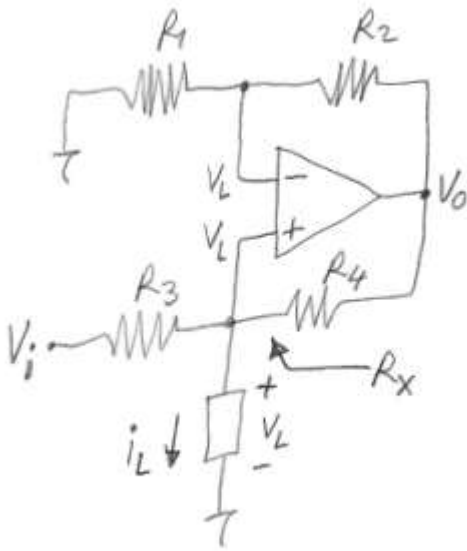
$$\frac{V_L - V_i}{R_5} + \frac{V_{01} - V_i}{R_1} = 0 \rightarrow V_{01} = \left(1 + \frac{R_1}{R_5}\right) V_i - \frac{R_1}{R_5} V_L$$

$$\frac{V_{01}}{R_2} + \frac{V_{02}}{R_3} = 0 \rightarrow V_{02} = -\frac{R_3}{R_2} V_{01} = \frac{R_1 R_3}{R_2 R_5} V_L - \left(1 + \frac{R_1}{R_5}\right) \frac{R_3}{R_2} V_i$$

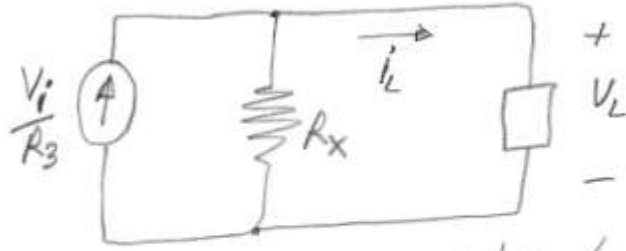
$$\begin{aligned} i_L &= \frac{V_{02} - V_L}{R_4} + \frac{V_i - V_L}{R_5} = \frac{V_i}{R_5} + \frac{V_{02}}{R_4} - \frac{V_L}{R_4} - \frac{V_L}{R_5} \\ &= \frac{V_i}{R_5} + \frac{R_1 R_3}{R_2 R_4 R_5} V_L - \left(1 + \frac{R_1}{R_5}\right) \frac{R_3}{R_2 R_4} V_i - \frac{V_L}{R_4} - \frac{V_L}{R_5} \\ &= \left(\frac{1}{R_5} - \left(1 + \frac{R_1}{R_5}\right) \frac{R_3}{R_2 R_4}\right) V_i + \left(\frac{R_1 R_3}{R_2 R_4 R_5} - \frac{1}{R_4} - \frac{1}{R_5}\right) V_L \\ &= \left(\frac{R_2 R_4 - R_3 R_5 - R_1 R_3}{R_2 R_4 R_5}\right) V_i - \left(\frac{R_1 R_3 - R_2 R_5 - R_2 R_4}{R_2 R_4 R_5}\right) V_L \end{aligned}$$

$$R_1 = R_2 = R_3 = R_4 + R_5 = R \text{ olsun}$$

$$\begin{aligned} i_L &= \left(\frac{R R_4 - R R_5 - R \cdot R}{R R_4 R_5}\right) V_i - \left(\frac{R \cdot R - R R_5 - R R_4}{R R_4 R_5}\right) V_L \\ &= \frac{R_4 - R_5 - R}{R_4 R_5} V_i - \frac{R - (R_4 + R_5)}{R_4 R_5} V_L \rightarrow 0 \\ &= \frac{R - R_5 - R_5 - R}{R_4 R_5} V_i = -\frac{2}{R_4} V_i \quad (\text{sabit akım}) \end{aligned}$$



Norton eşdeğer devresi



$i_L = \frac{V_i}{R_3} - \frac{V_L}{R_x}$ Aşağıdaki denklem bu şekle getirilip R_x bulunur.

$$\frac{V_L}{R_1} + \frac{V_L - V_0}{R_2} = 0 \rightarrow V_0 = \left(1 + \frac{R_2}{R_1}\right) \cdot V_L$$

$$i_L = \frac{V_i - V_L}{R_3} + \frac{V_0 - V_L}{R_4} = \frac{V_i - V_L}{R_3} + \frac{\left(1 + \frac{R_2}{R_1}\right) V_L - V_L}{R_4}$$

$$= \frac{V_i}{R_3} - \frac{V_L}{R_3} + \frac{R_2}{R_1 R_4} V_L = \frac{V_i}{R_3} - \left(\frac{1}{R_3} - \frac{R_2}{R_1 R_4}\right) V_L$$

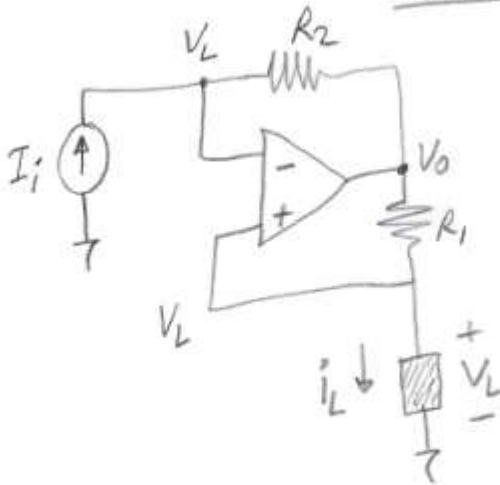
$$= \frac{V_i}{R_3} - \left(\frac{R_1 R_4 - R_2 R_3}{R_1 R_3 R_4}\right) V_L = \frac{V_i}{R_3} - \frac{V_L}{\frac{R_1 R_3 R_4}{R_1 R_4 - R_2 R_3}}$$

$$R_x = \frac{R_1 R_3 R_4}{R_1 R_4 - R_2 R_3} = \frac{R_4}{\frac{R_4}{R_3} - \frac{R_2}{R_1}}$$

$$\frac{R_4}{R_3} = \frac{R_2}{R_1} = k \text{ ise } R_x = \frac{R_4}{k - k} = \frac{R_4}{0} = \infty$$

Bu durumda $\rightarrow 0$ olur

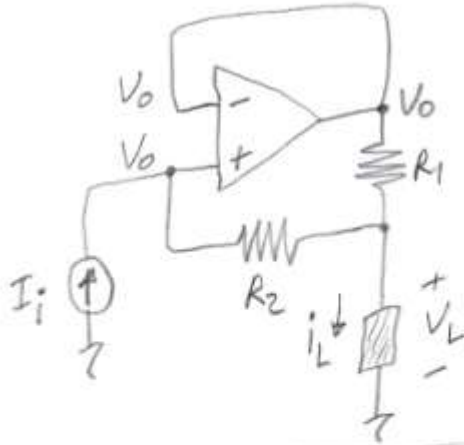
$$i_L = \frac{V_i}{R_3} - \frac{V_L}{R_x} \Rightarrow i_L = \frac{V_i}{R_3}$$

Akım Yükleli

$$I_i = \frac{V_L - V_o}{R_2} \Rightarrow V_o - V_L = -R_2 I_i$$

$$i_L = \frac{V_o - V_L}{R_1} = -\frac{R_2}{R_1} I_i$$

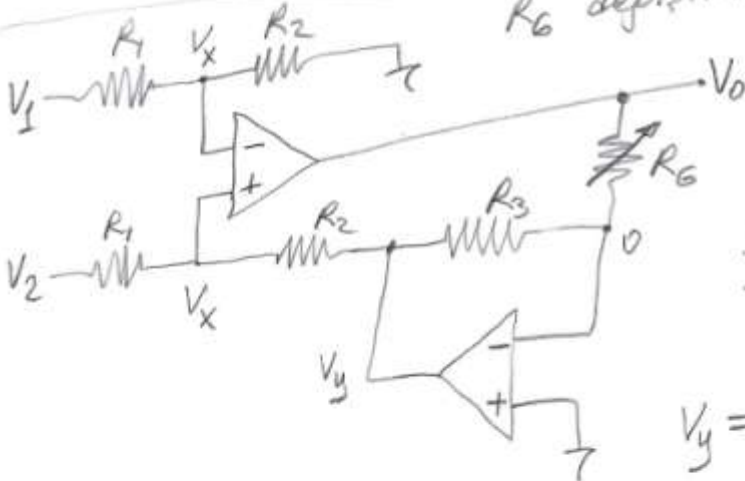
$$I_i = \frac{V_o - V_L}{R_2} \Rightarrow V_o - V_L = R_2 I_i$$



$$i_L = I_i + \frac{V_o - V_L}{R_1} = I_i + \frac{R_2 I_i}{R_1}$$

$$= \left(1 + \frac{R_2}{R_1}\right) I_i$$

R_6 değiştirilerek kazanç değiştirilebilir.



$$V_x = \frac{R_2}{R_1 + R_2} V_1$$

$$\frac{V_2 - V_x}{R_1} + \frac{V_y - V_x}{R_2} = 0$$

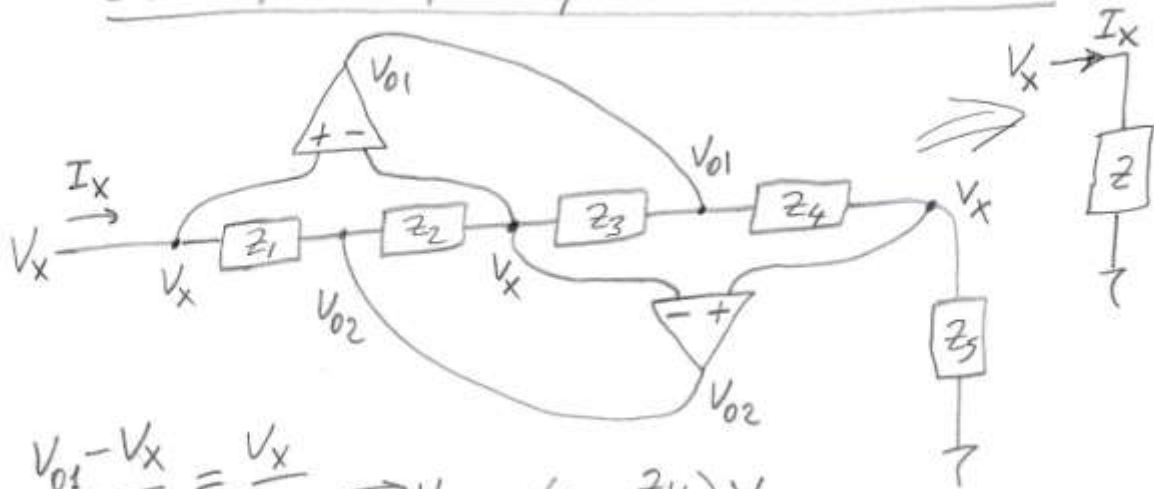
$$V_y = \left(1 + \frac{R_2}{R_1}\right) V_x - \frac{R_2}{R_1} V_2$$

$$= \frac{R_2}{R_1} (V_1 - V_2)$$

$$\frac{V_y}{R_3} + \frac{V_o}{R_6} = 0$$

$$V_o = -\frac{R_6}{R_3} V_y = +\frac{R_2 R_6}{R_1 R_3} (V_2 - V_1)$$

Genelleştirilmiş Empedans Dönüştürücü

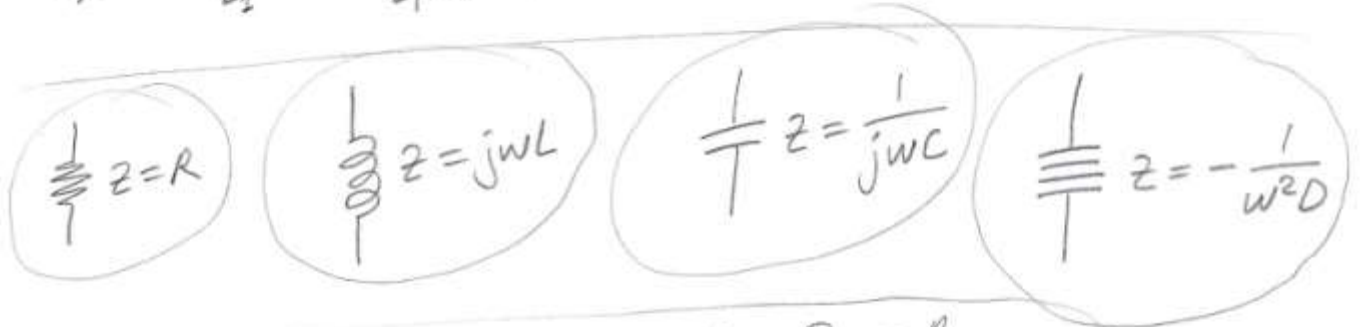


$$\frac{V_{01} - V_x}{Z_4} = \frac{V_x}{Z_5} \Rightarrow V_{01} = \left(1 + \frac{Z_4}{Z_5}\right) V_x$$

$$\frac{V_{02} - V_x}{Z_2} = \frac{V_x - V_{01}}{Z_3} \Rightarrow V_{02} = \left(1 + \frac{Z_2}{Z_3}\right) V_x - \frac{Z_2}{Z_3} V_{01}$$

$$V_{02} = \left(1 + \frac{Z_2}{Z_3}\right) V_x - \frac{Z_2}{Z_3} \left(1 + \frac{Z_4}{Z_5}\right) V_x = \left(1 - \frac{Z_2 Z_4}{Z_3 Z_5}\right) V_x$$

$$I_x = \frac{V_x - V_{02}}{Z_1} = \frac{Z_2 Z_4}{Z_1 Z_3 Z_5} V_x \Rightarrow Z_x = \frac{V_x}{I_x} = \frac{Z_1 Z_3 Z_5}{Z_2 Z_4}$$



$$Z_1 = R_1, Z_2 = \frac{1}{j\omega C_2}, Z_3 = R_3, Z_4 = R_4, Z_5 = R_5$$

$$Z = \frac{Z_1 Z_3 Z_5}{Z_2 Z_4} = \frac{R_1 R_3 R_5}{\frac{1}{j\omega C_2} \cdot R_4} = j\omega \frac{R_1 R_3 R_5 C_2}{R_4} \rightarrow L = \frac{R_1 R_3 R_5 C_2}{R_4}$$

$$Z_1 = \frac{1}{j\omega C_1}, Z_2 = R_2, Z_3 = R_3, Z_4 = R_4, Z_5 = \frac{1}{j\omega C_5}$$

$$Z = \frac{Z_1 Z_3 Z_5}{Z_2 Z_4} = \frac{\frac{1}{j\omega C_1} R_3 \frac{1}{j\omega C_5}}{R_2 R_4} = -\frac{R_3}{\omega^2 C_1 C_5 R_2 R_4} \rightarrow D = \frac{R_2 R_4 C_1 C_5}{R_3}$$